

X-ray analysis
Mauro Sardela Jr.
AMC2024

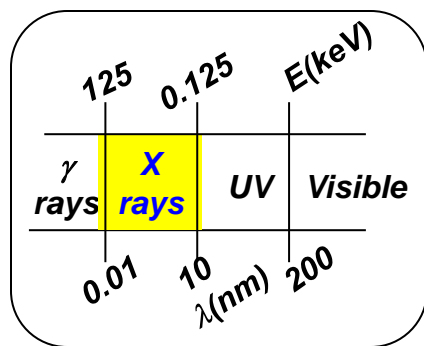
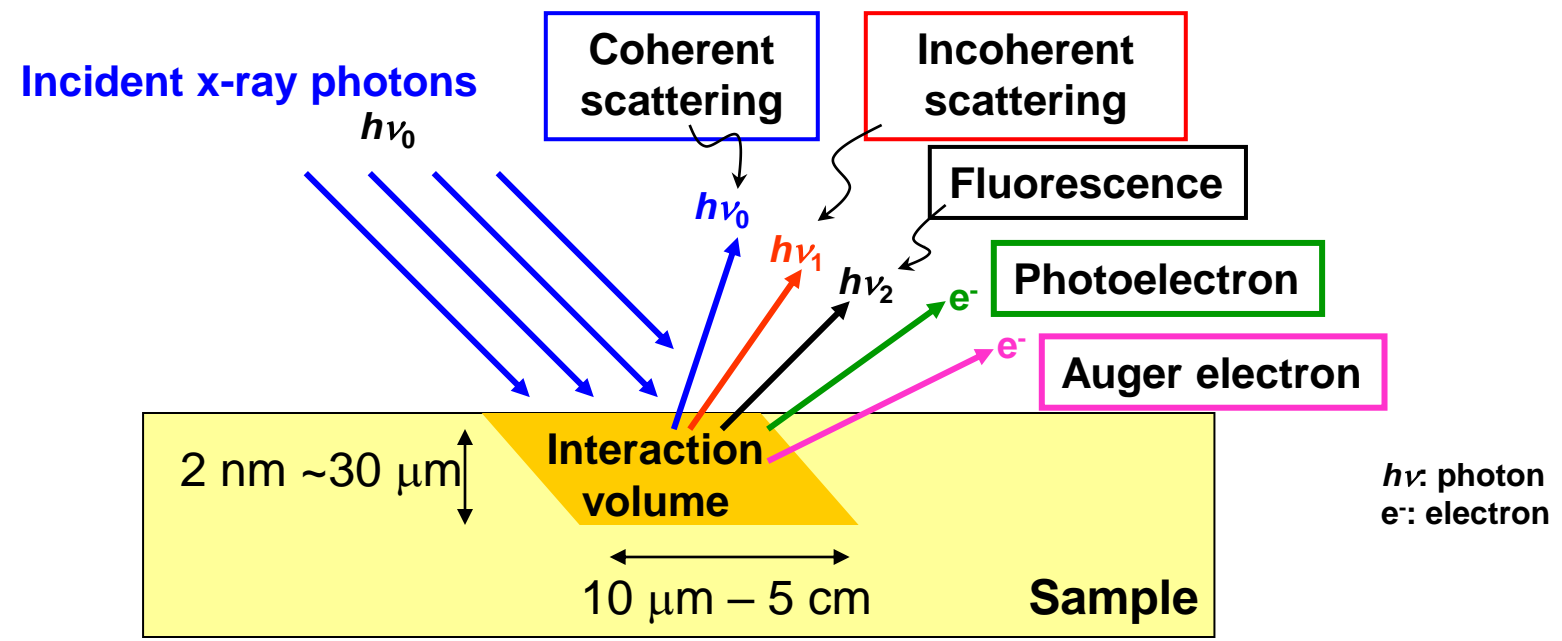
Platinum sponsors:



Sponsors:



X-ray interactions with matter



X-ray radiation mostly used in lab instruments:
Cu radiation

- **Cu K α** : $\lambda = 0.15418 \text{ nm}$
 (8.05 keV, conventional resolution)
- **Cu K α 1**: ($\lambda = 0.15056 \text{ nm}$ (high resolution))

Anode	Cr	Fe	Co	Cu	Mo	Ag
K α (nm)	0.229	0.194	0.179	0.154	0.071	0.056
Energy (keV)	5.41	6.39	6.93	8.05	17.46	22.14

X-ray interactions with matter

Coherent scattering

(Diffraction, Thompson or Rayleigh scattering)

(1) Incoming photon
 (2) Oscillating electron
 (3) Scattered photon
 No loss of energy.

Incoherent scattering

(Compton scattering)

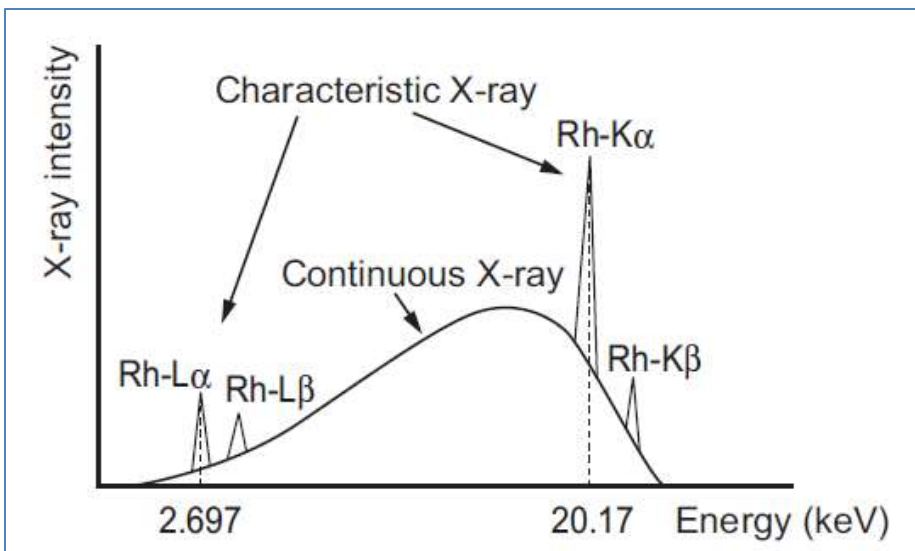
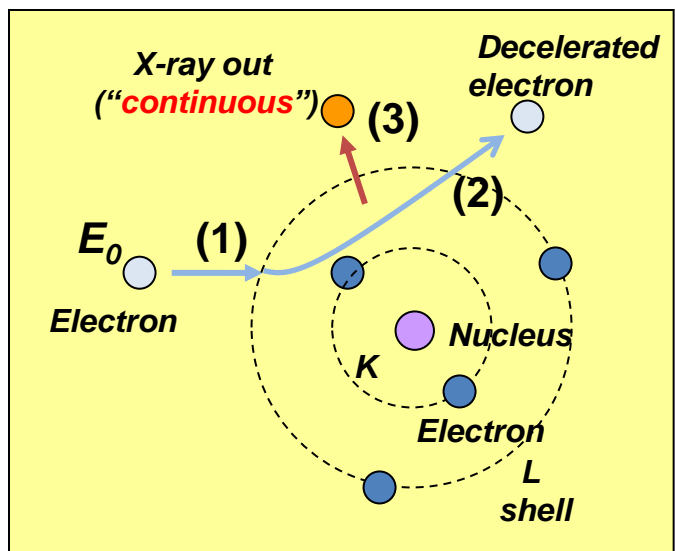
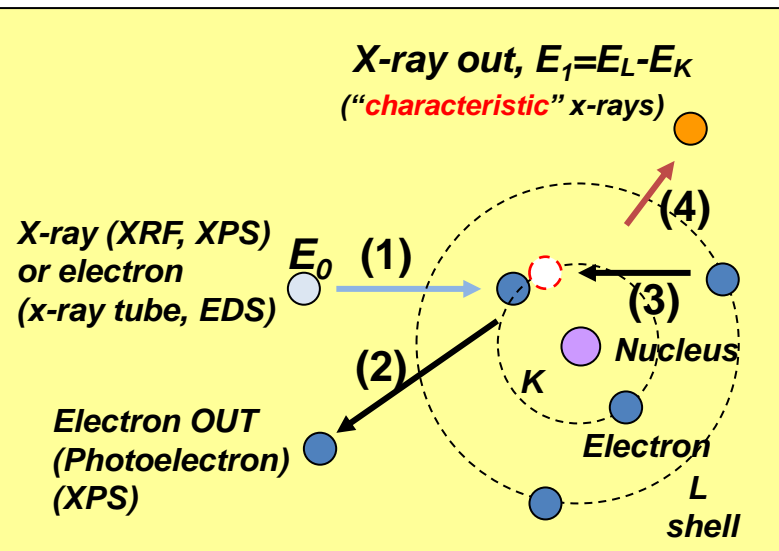
(1) Incoming photon
 (2) Energy is partially transferred to electron
 (3) Scattered photon (energy loss).

Fluorescence

(1) Incoming photon
 (2) Expelled electron (photoelectron)
 (3) Hole is created in the shell
 (4) Outer shell electron moves to the inner shell hole
 (5) Energy excess emitted as *characteristic photon*.

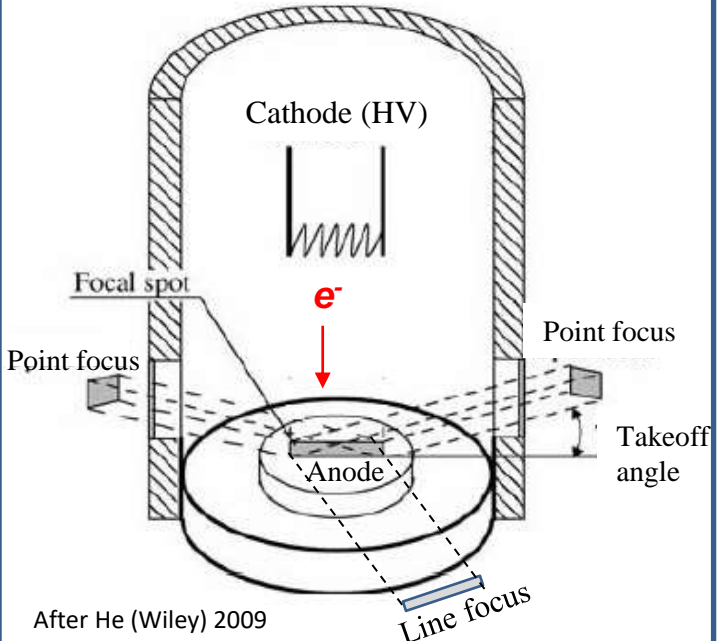
Auger electron

(1-4) Hole created (3) after photoelectron emission (2) is occupied by outer electron (4).
 (5) Excitation energy is transferred to electron
 (6) Electron ejected from atom (Auger electron)



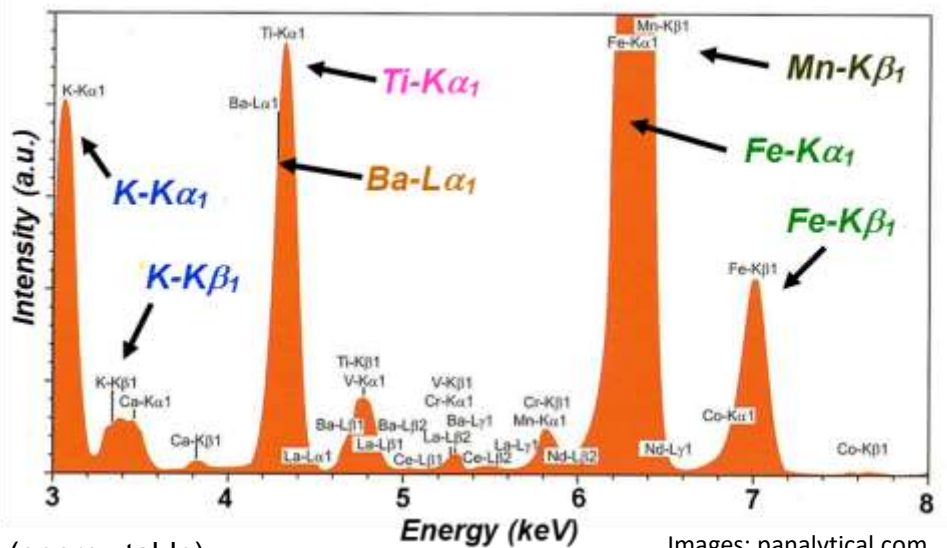
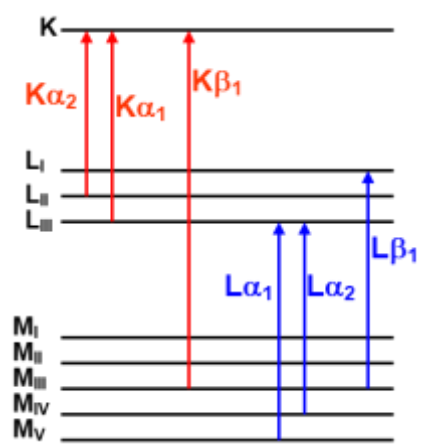
X-ray generation from sealed tubes:

electrons from W filament accelerate under HV and hit a metal target (Cu, Mo, ...) generating continuous and characteristic x-ray lines used in X-ray analytical instruments (Cu $K\alpha$, ...)



After He (Wiley) 2009

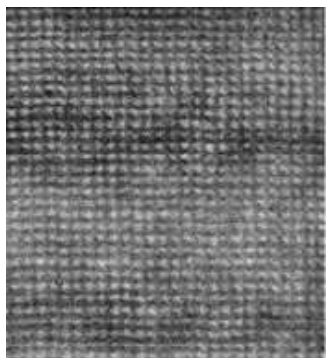
X-ray characteristic lines x-ray fluorescence (XRF) for quantitative elemental chemical analysis



Images: panalytical.com

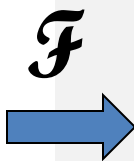
- $E \sim Z^2$ chemical fingerprinting
- Energy is known for each element transition (energy table)
- Energy resolution: 150-300 eV (EDXRF), 5-20 eV (WDXRF)
- Detection limits: 10% C, 0.5% O, 100 ppm F, 10 ppm Si, 0.1 ppm Pt – U
- Solids, liquids – non destructible technique, some tools are handheld.
- Use reference samples for calibration, or fundamental parameters method.

Fundamentals of diffraction



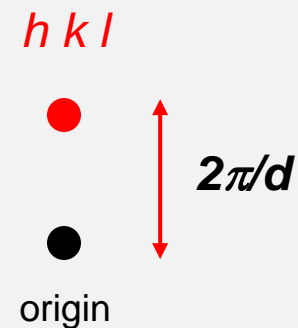
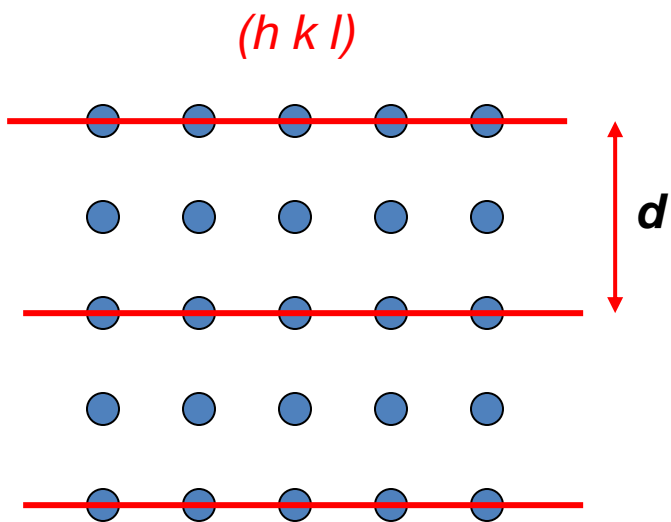
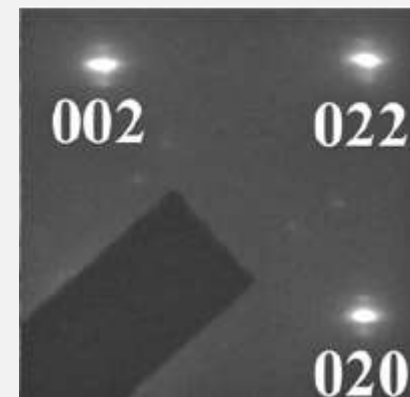
“Real” space

Set of planes

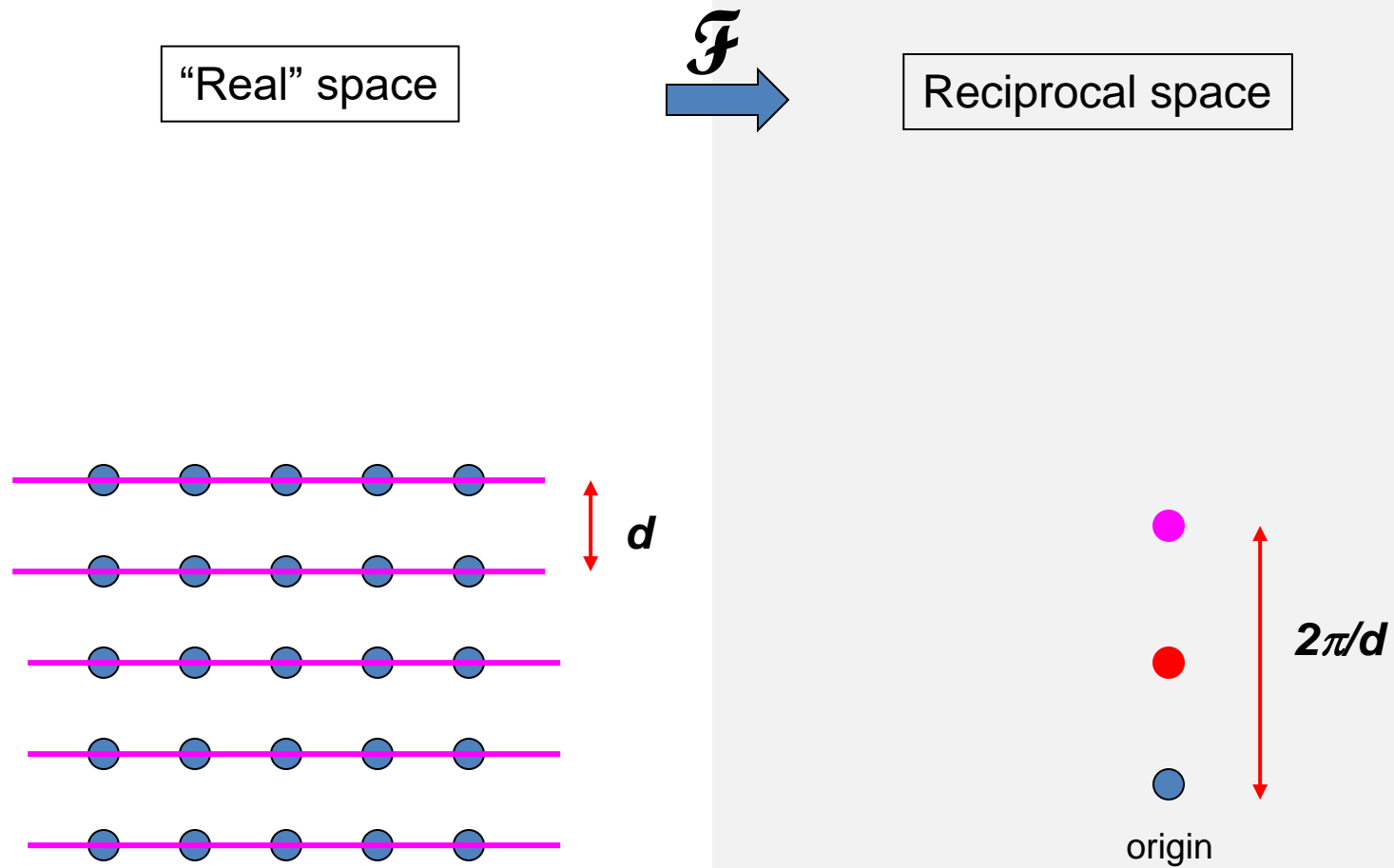


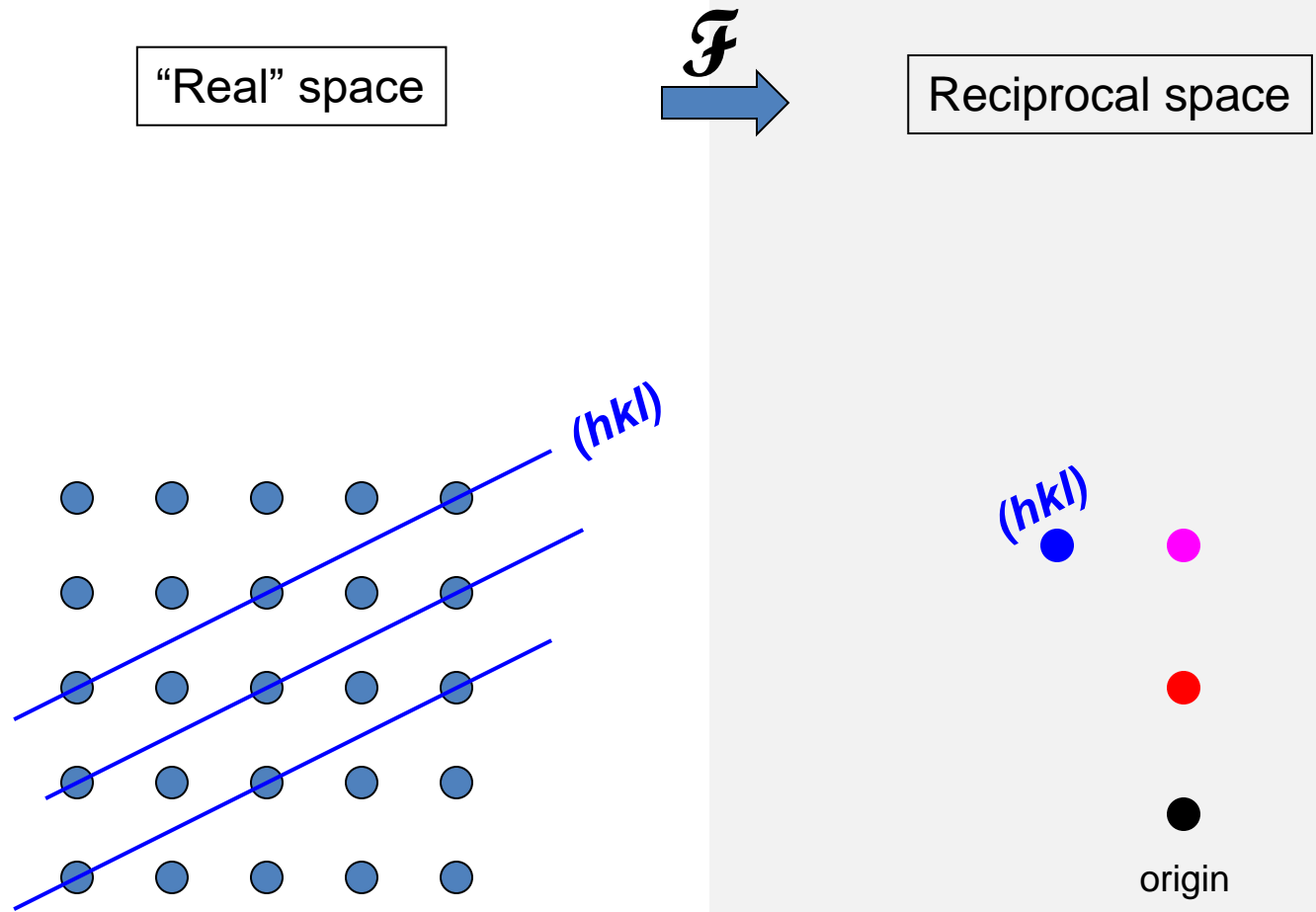
Reciprocal space

Point

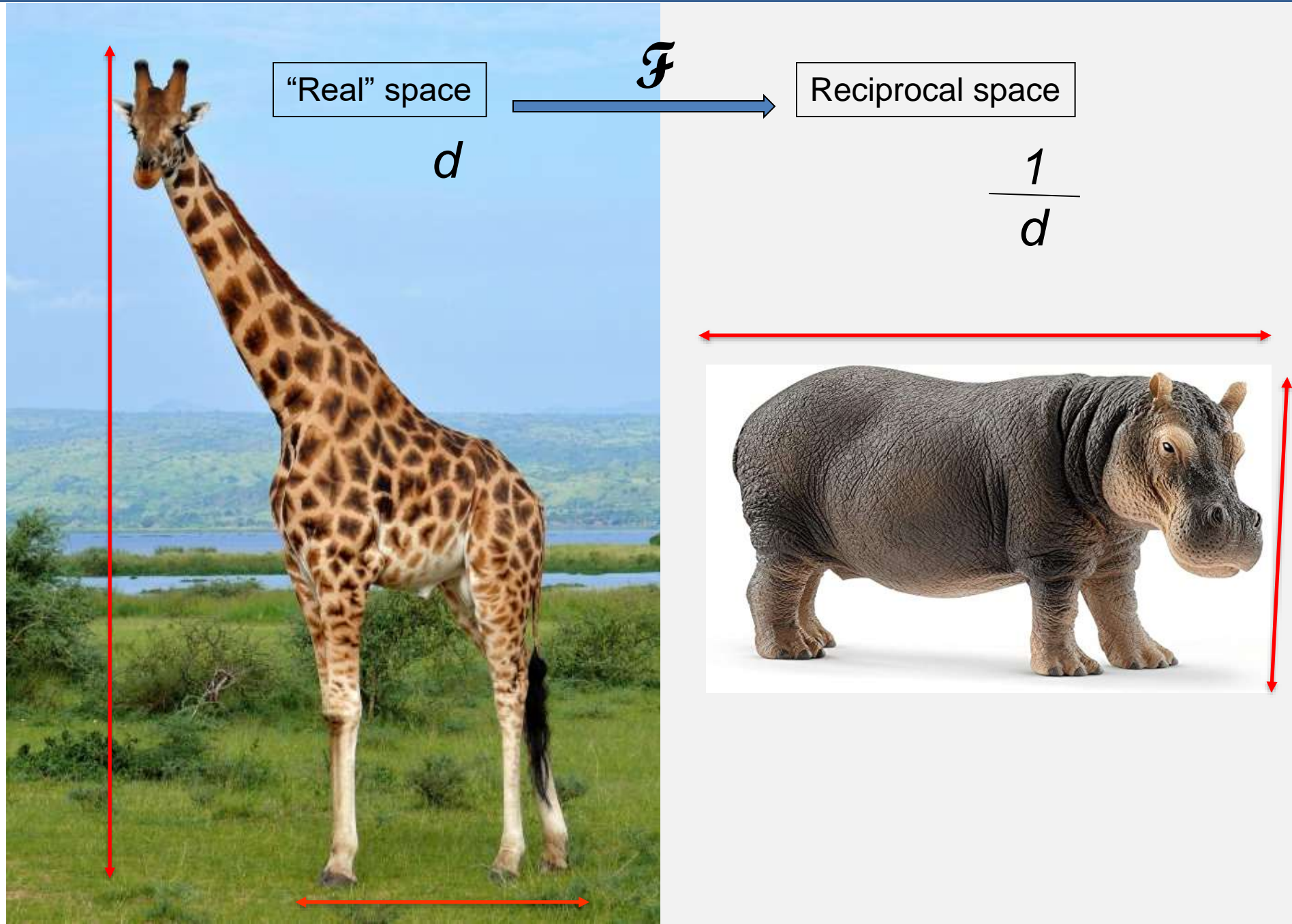


M. von Laue 1879-1960
X-rays from crystals, 1912.

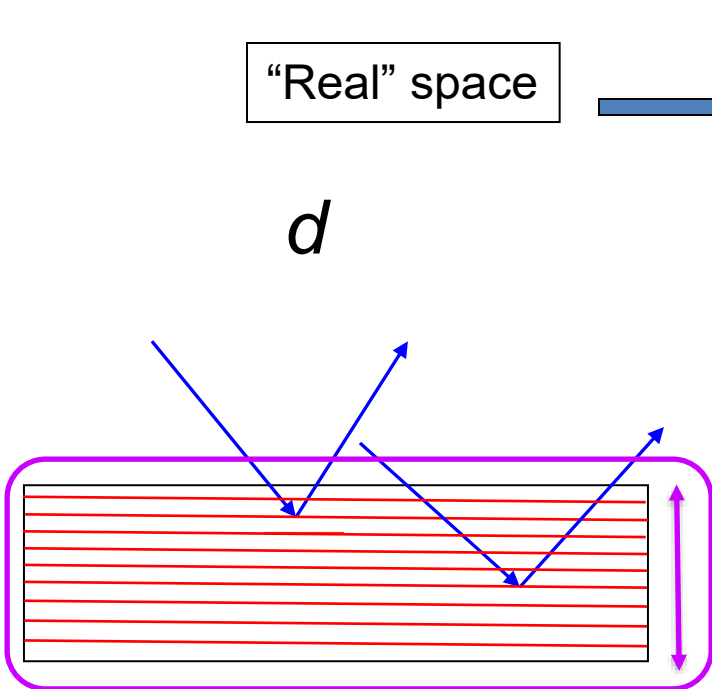
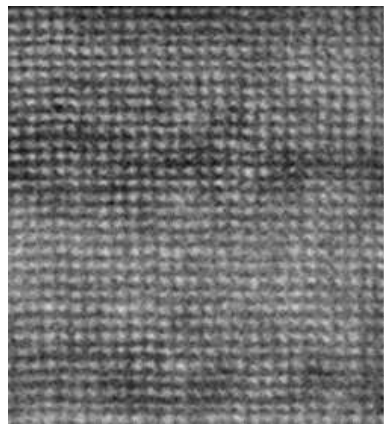




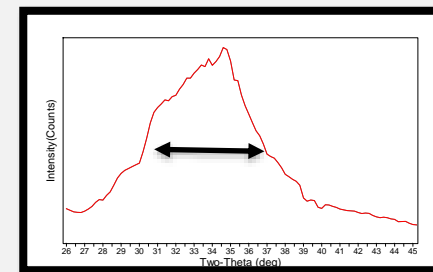
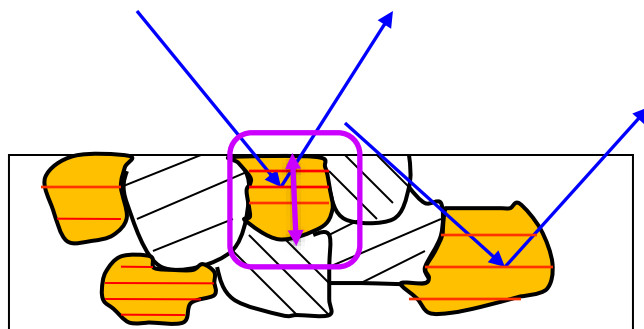
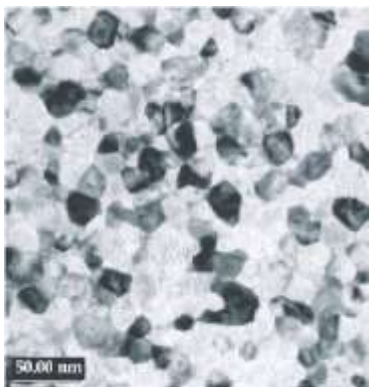
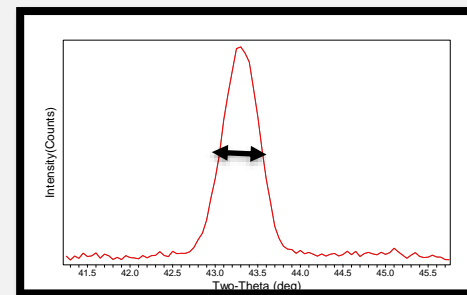
Fundamentals of diffraction



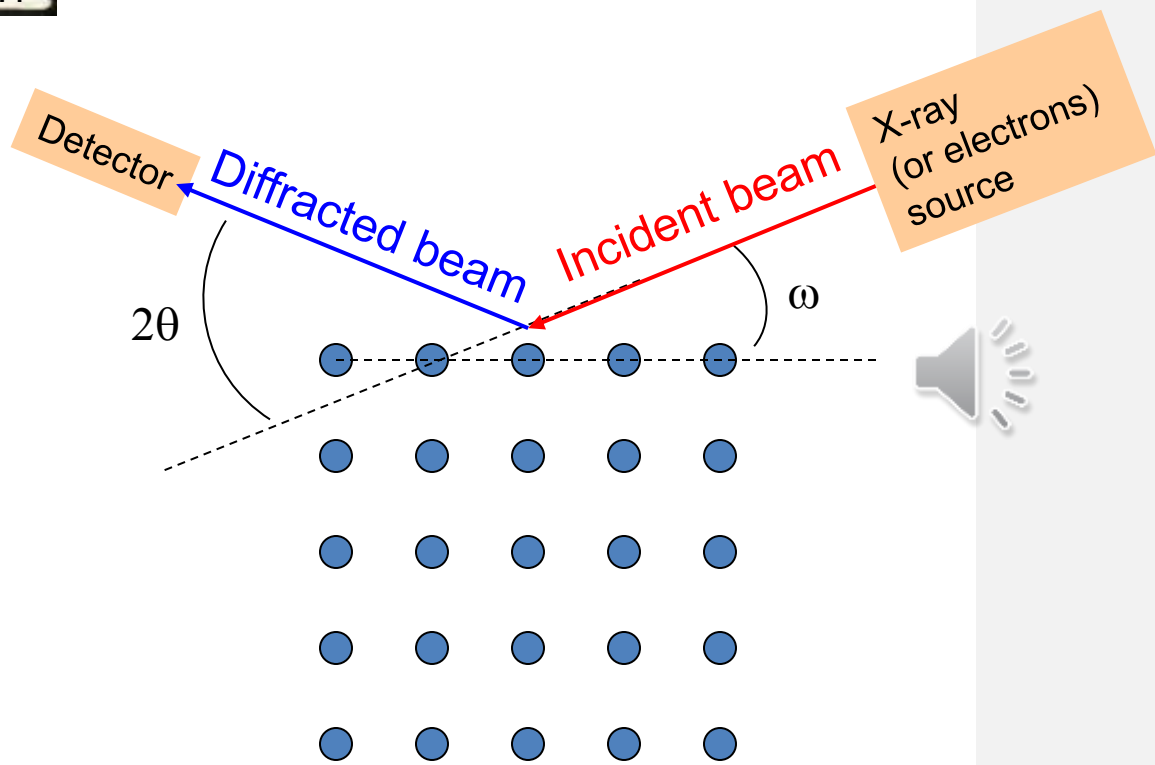
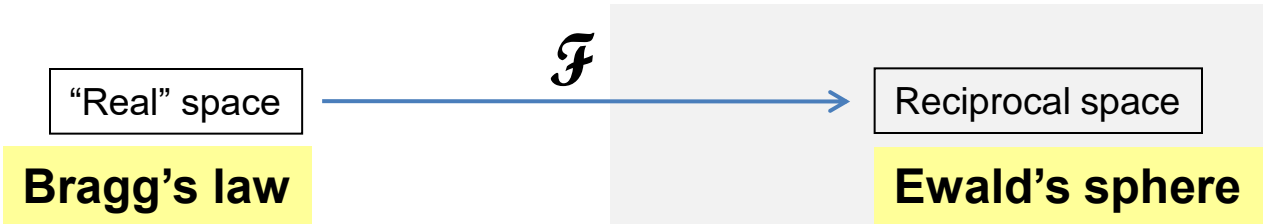
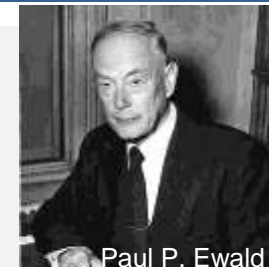
Fundamentals of diffraction

 \mathcal{F}

Reciprocal space

 $\frac{1}{d}$ 

Bragg's law and Ewald's sphere

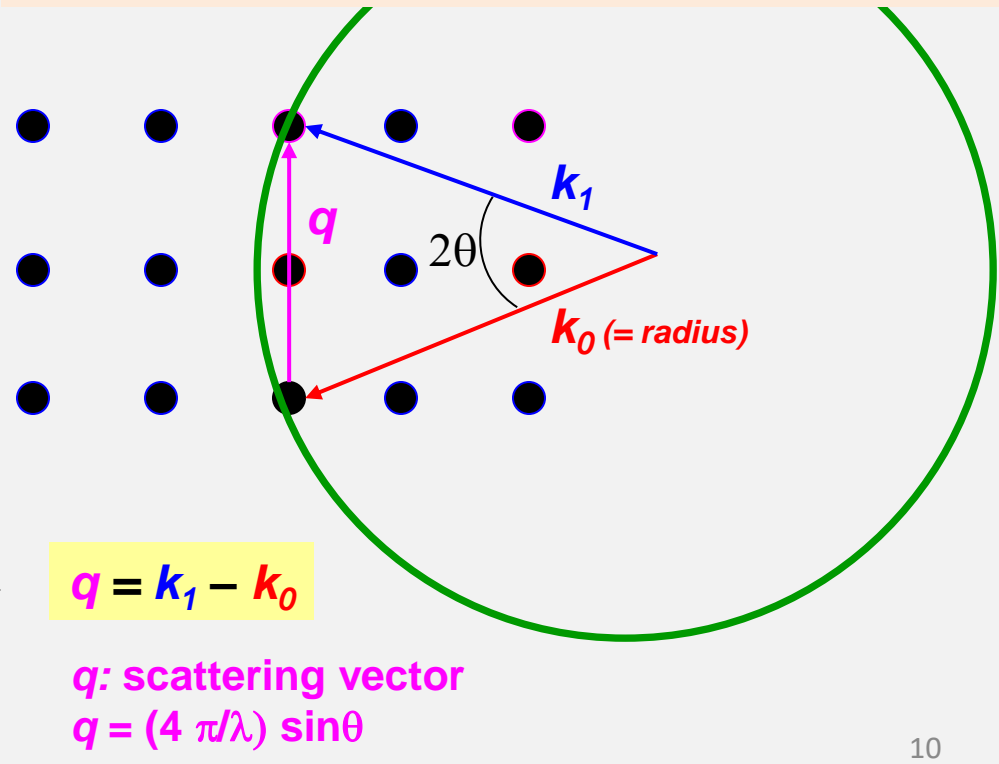


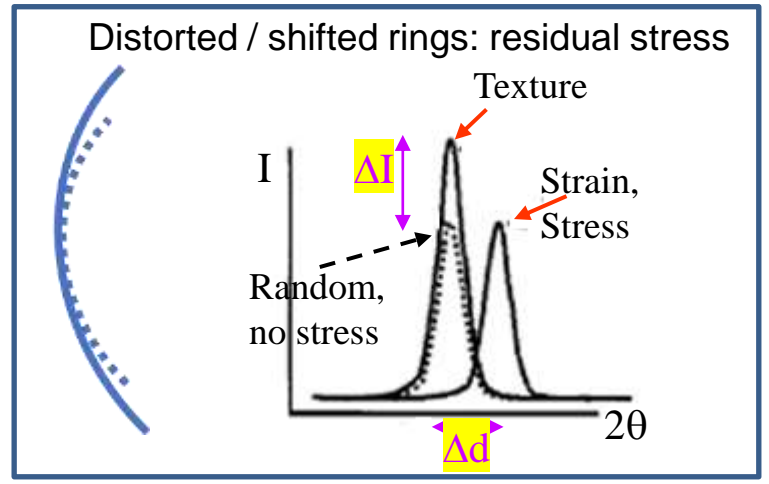
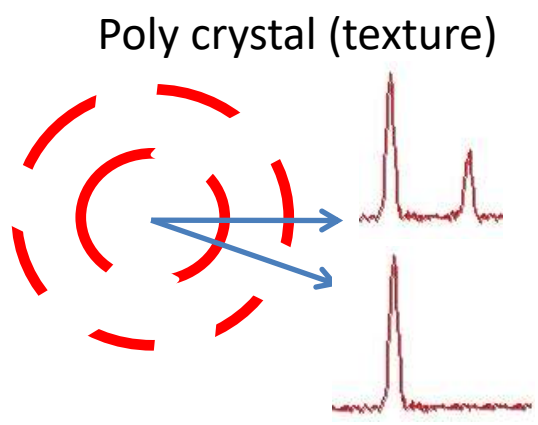
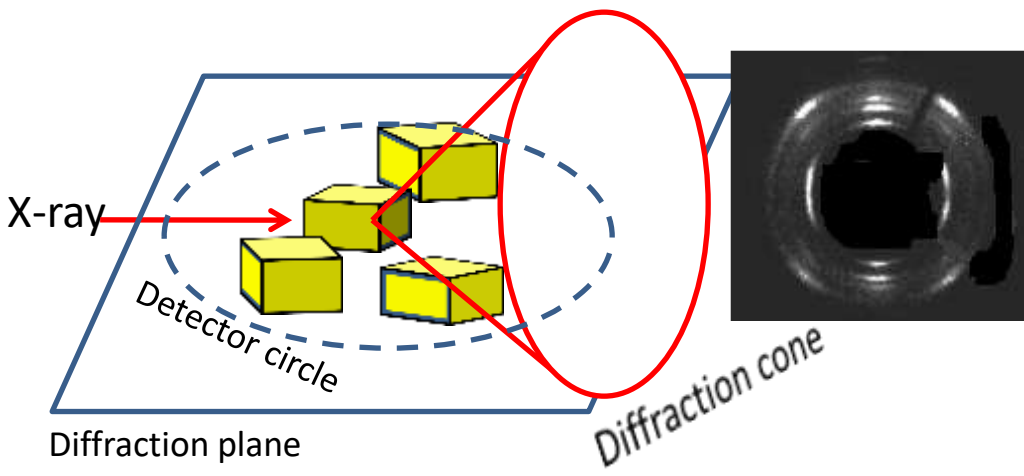
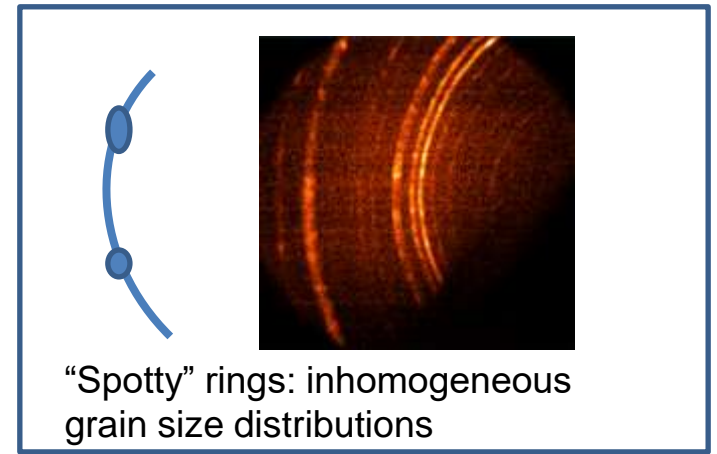
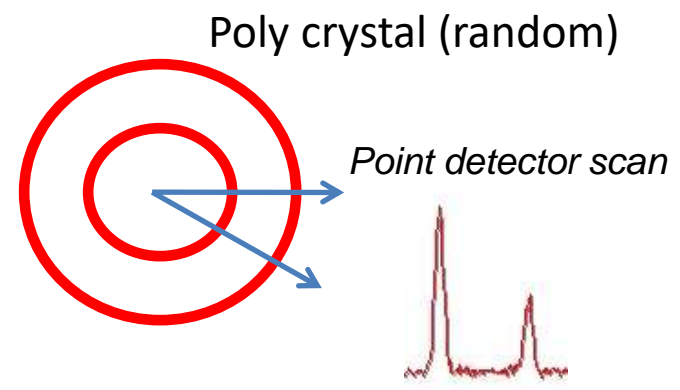
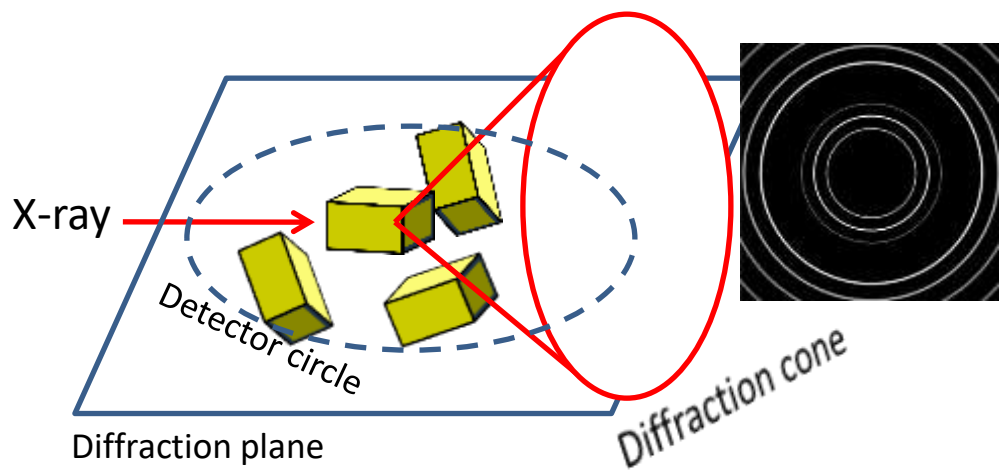
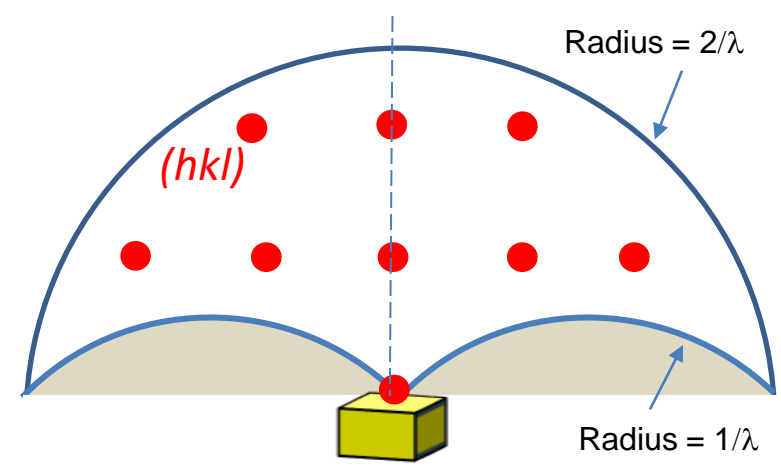
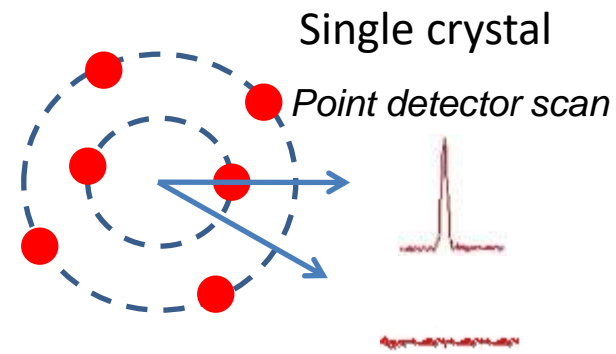
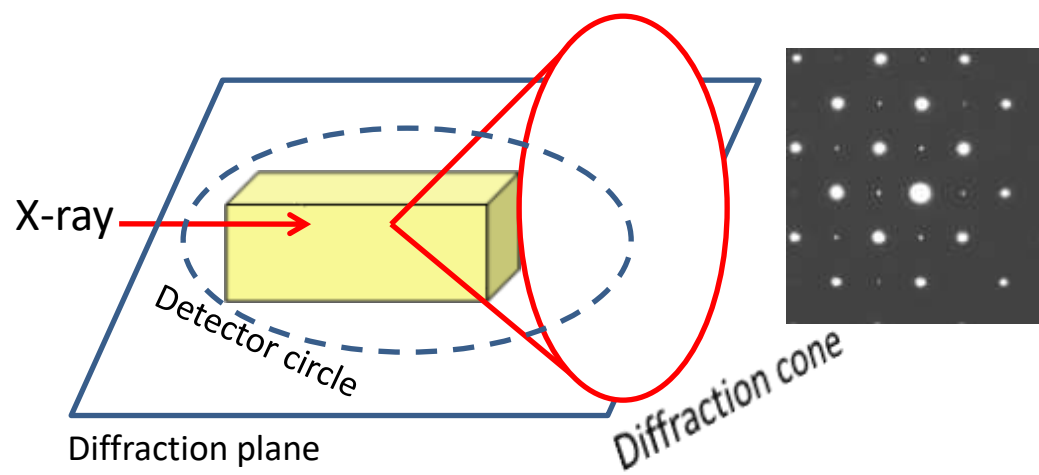
$k_0 \sim 6.5 \text{ nm}^{-1}$ (Cu α x-rays)
 $k_0 \sim 398 \text{ nm}^{-1}$ (200 kV e-)
 $1/d \sim 2.78 \text{ nm}^{-1}$ (d ~ 0.36 nm, example for a metal)
 e- k_0 much larger: e- diffraction from multiple planes
 X-rays $k_0 \sim 1/d$: XRD sensitive to changes in crystal structure

$2 d \sin \theta = n \lambda$

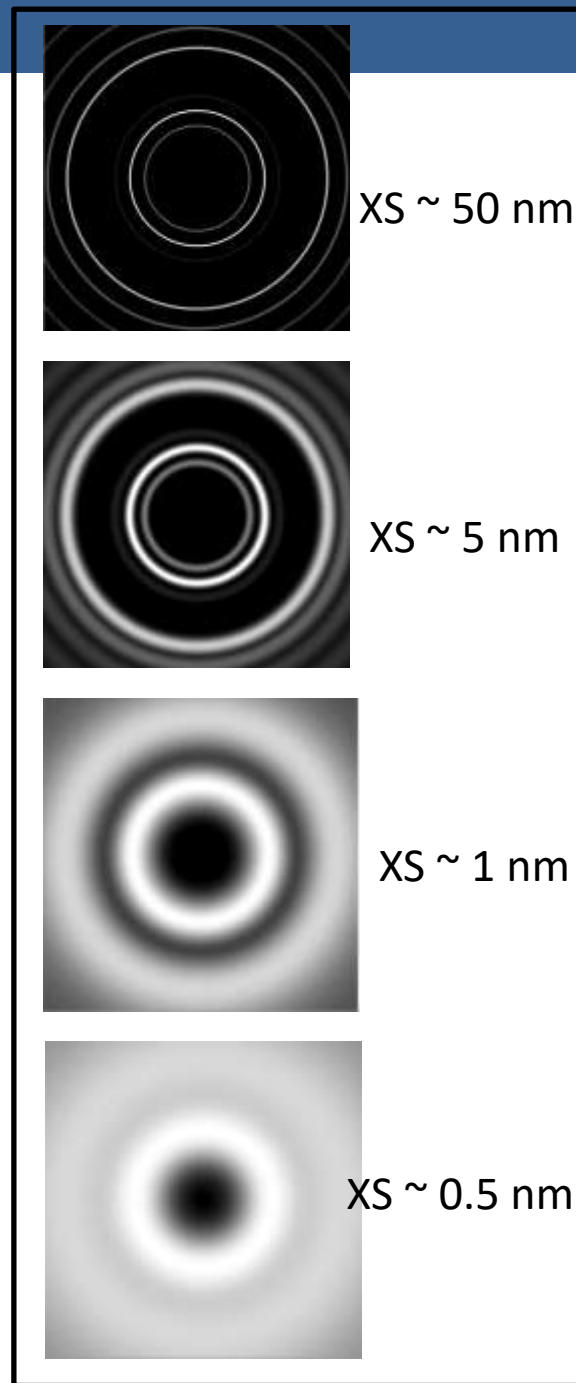
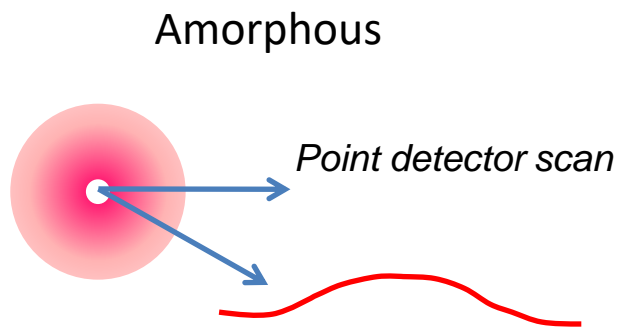
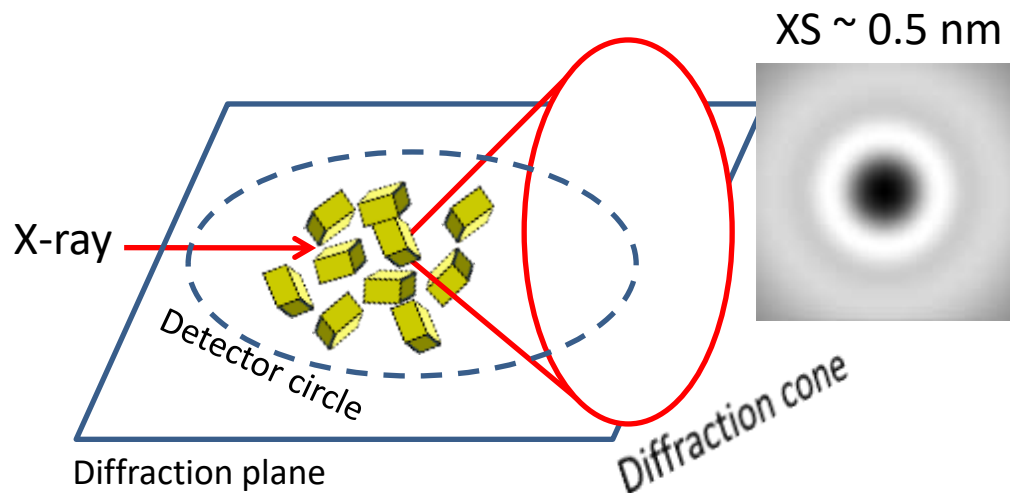
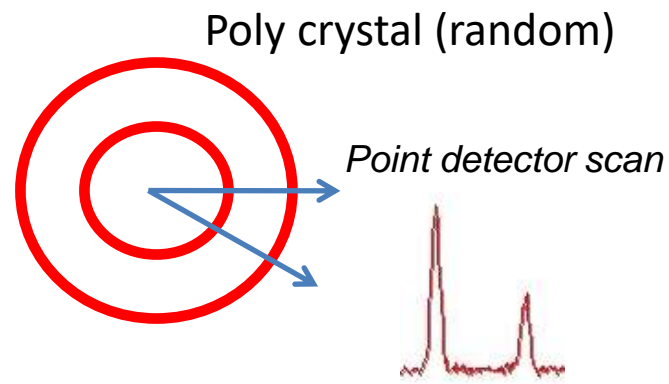
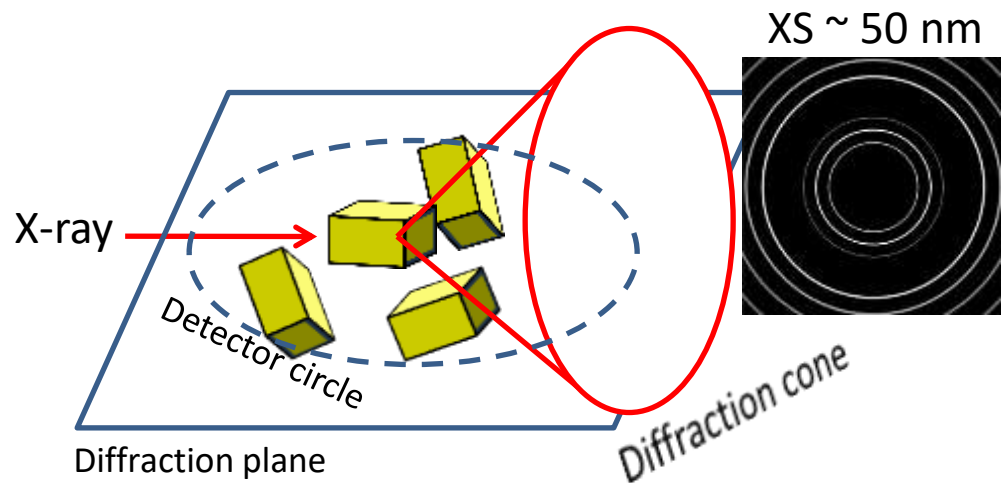
Measure $2\theta \rightarrow d$
 $d \sim 1/\sin\theta$

← Elastic scattering →



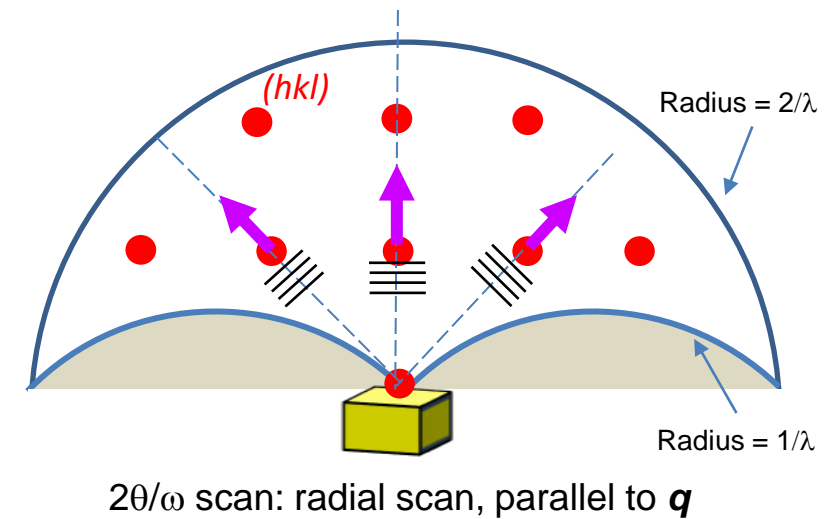
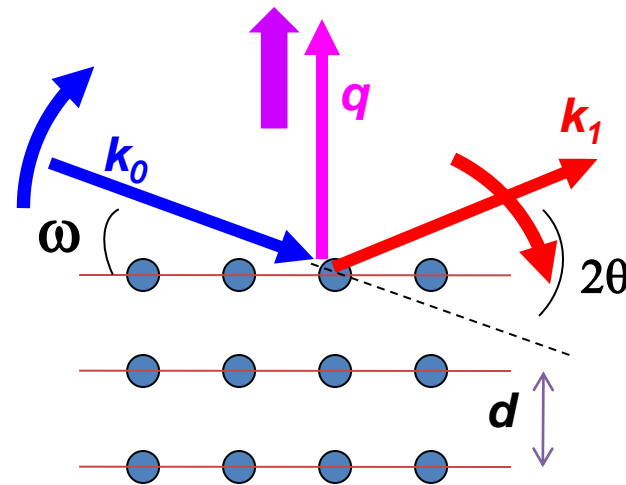
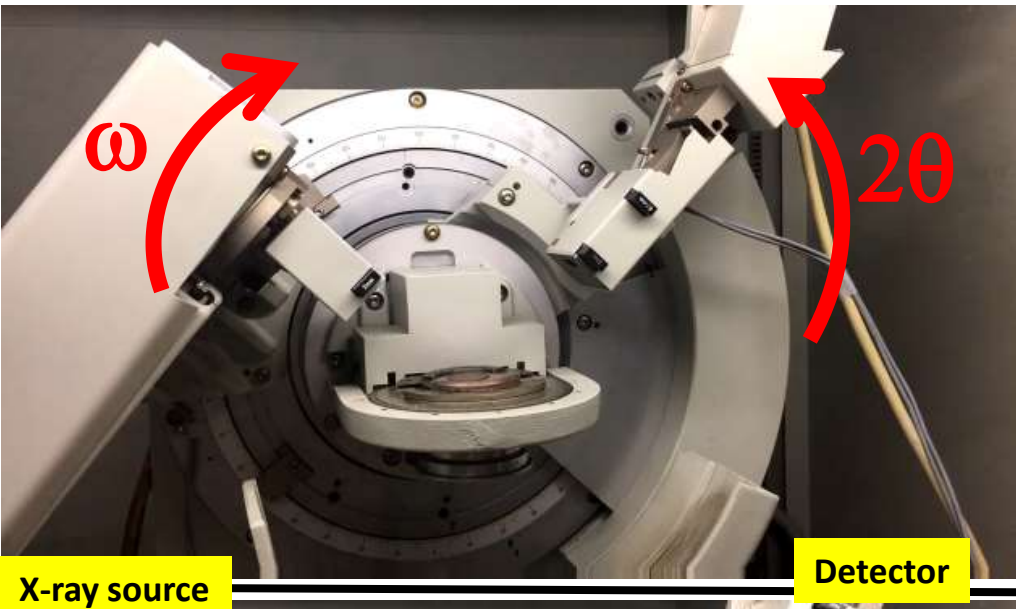


Amorphous and polycrystalline phases



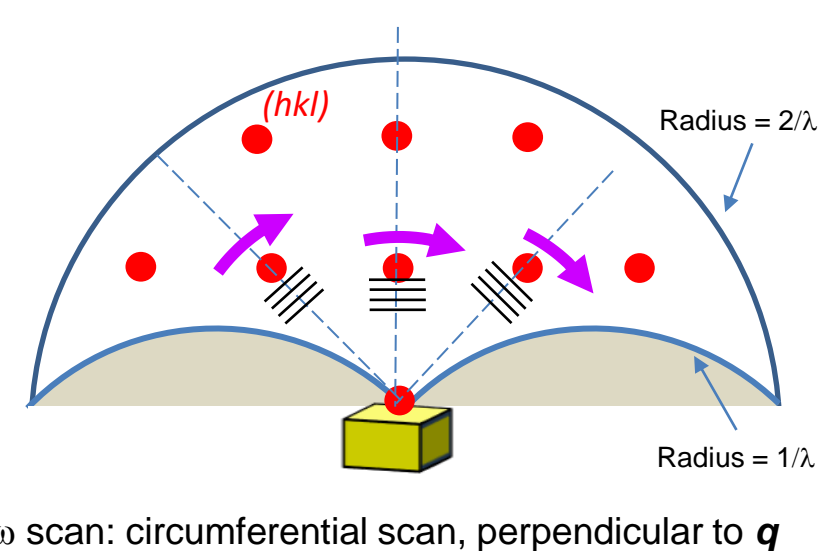
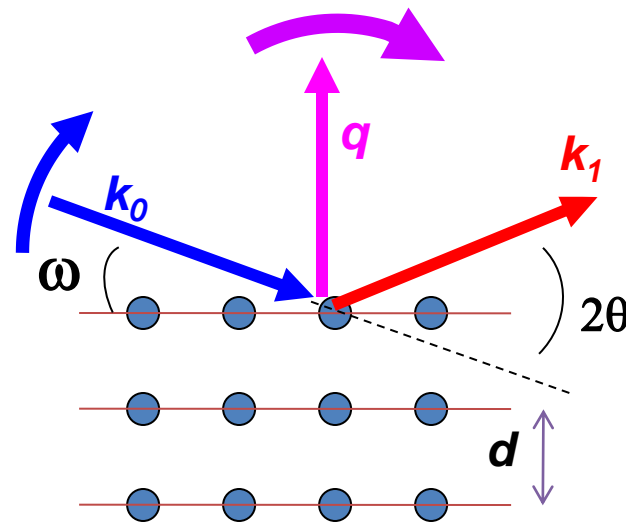
XS : crystallite size

2theta/omega scan

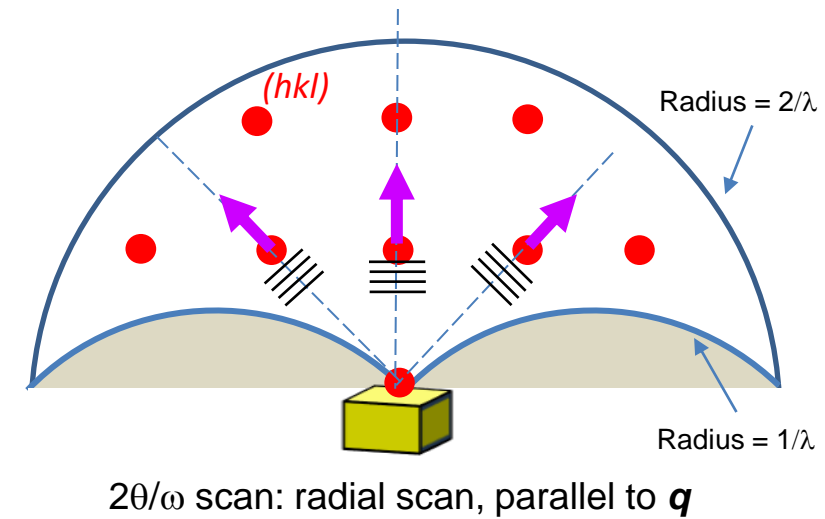
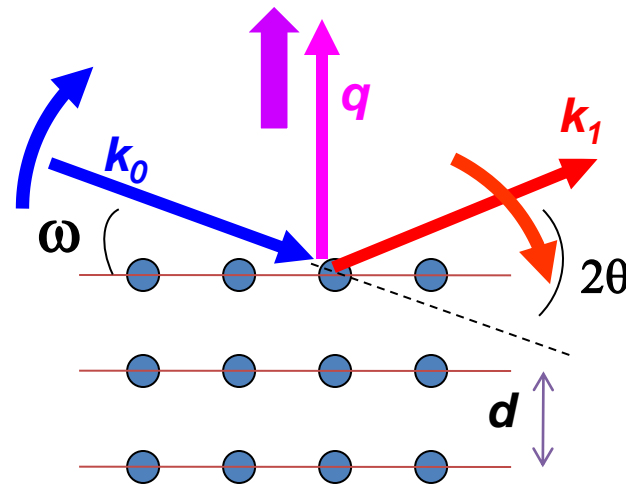
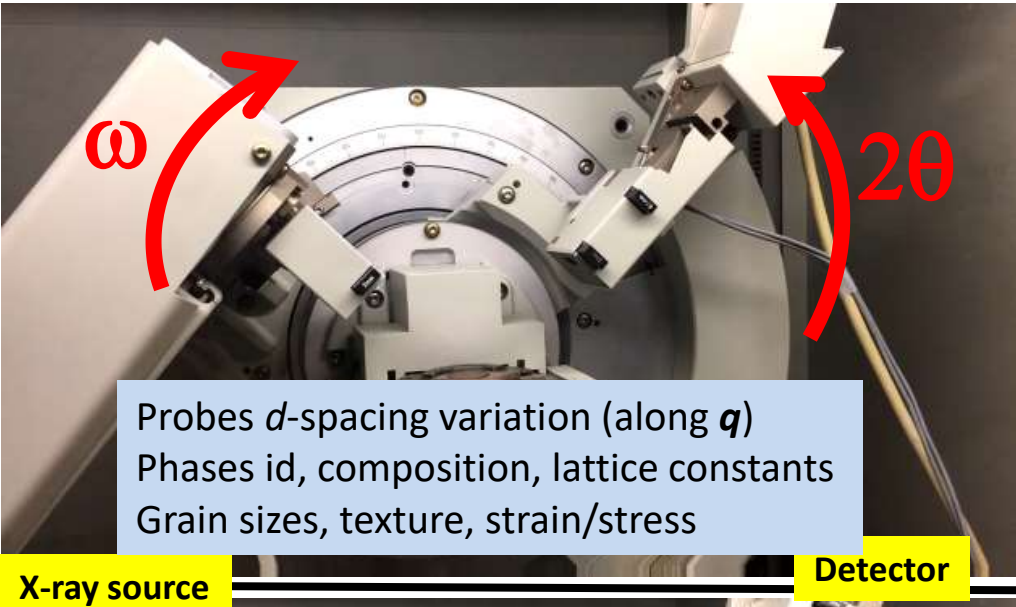


omega scan

(rocking curve)

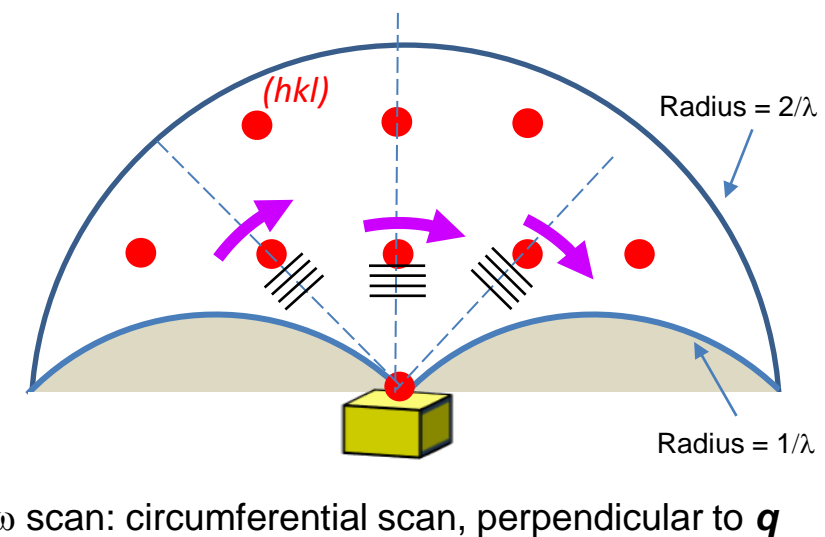
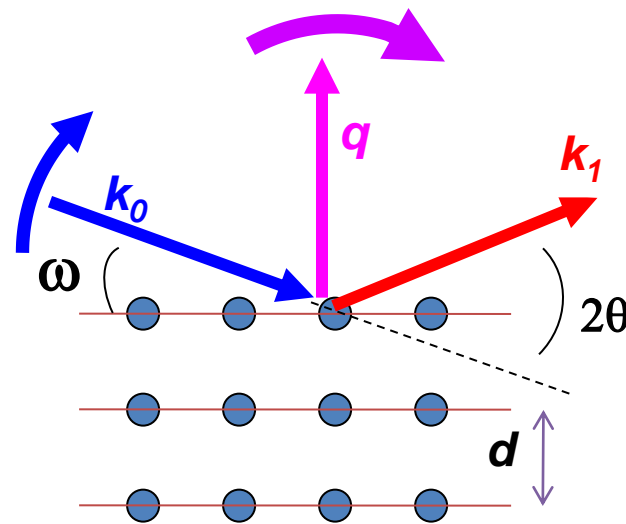


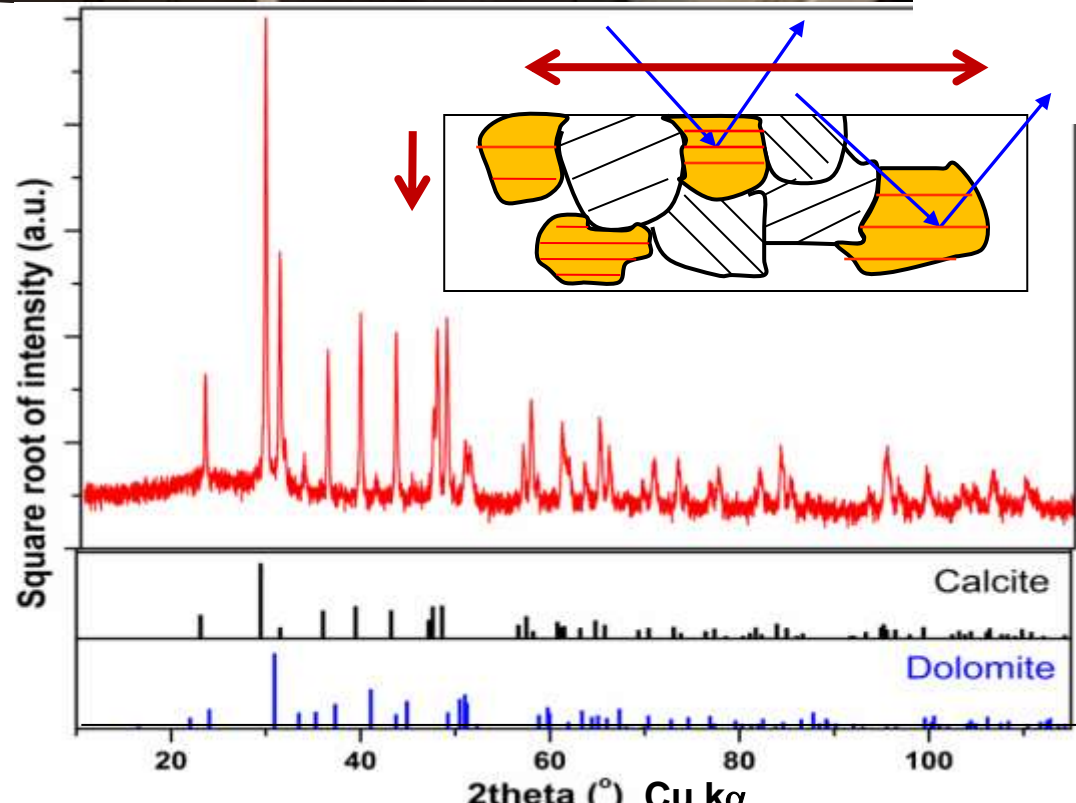
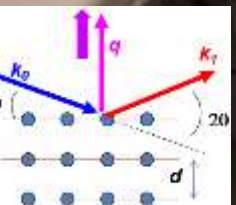
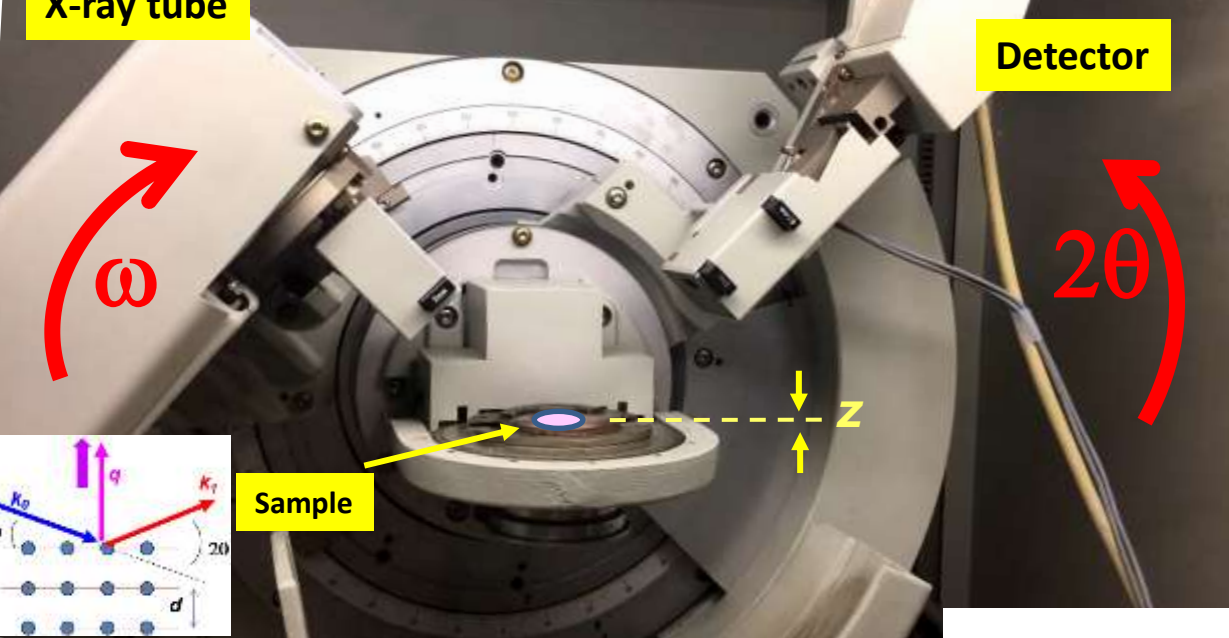
2theta/omega scan



omega scan

(rocking curve)





Information from typical XRD data

Grain orientations for planes parallel to surface (**directional**)
 Not all grain orientations are seen in this scan

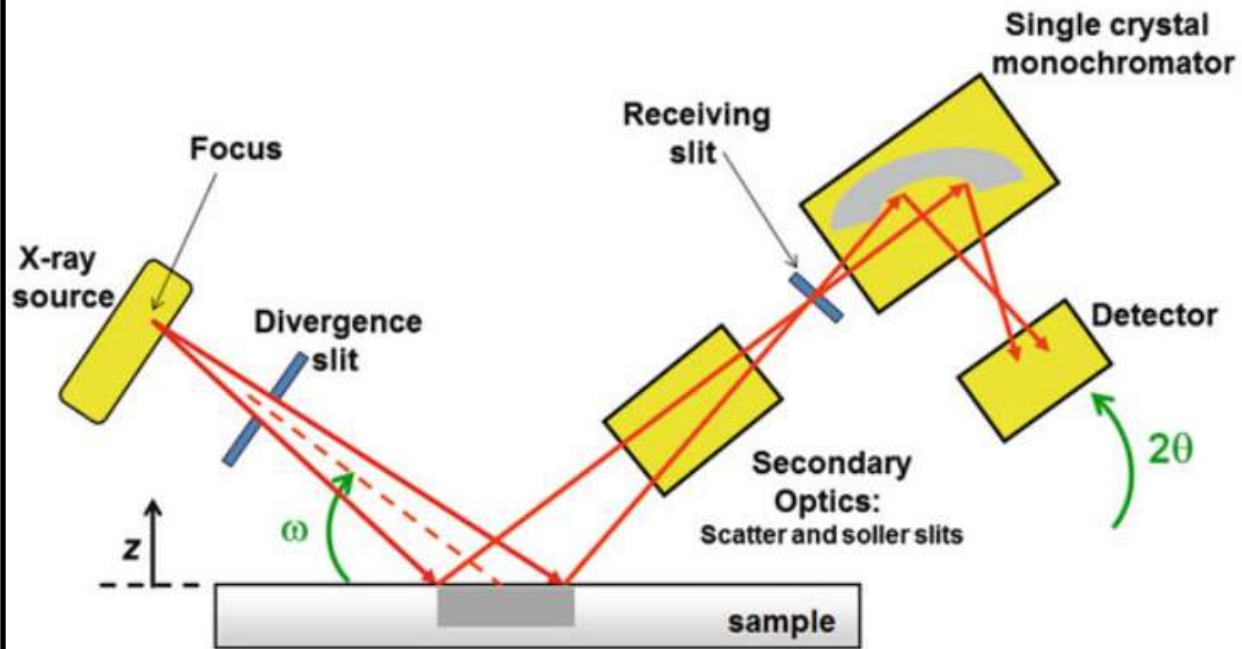
Irradiated volume may **change**:
 surface area decreases, depth increases with increasing ω

2θ peak position: Z is critical (**sample displacement error**)
 Parallel beam vs. Bragg Brentano configuration

Peak shapes: optics, configuration, surface shape, fine vs coarse grains during powder prep.

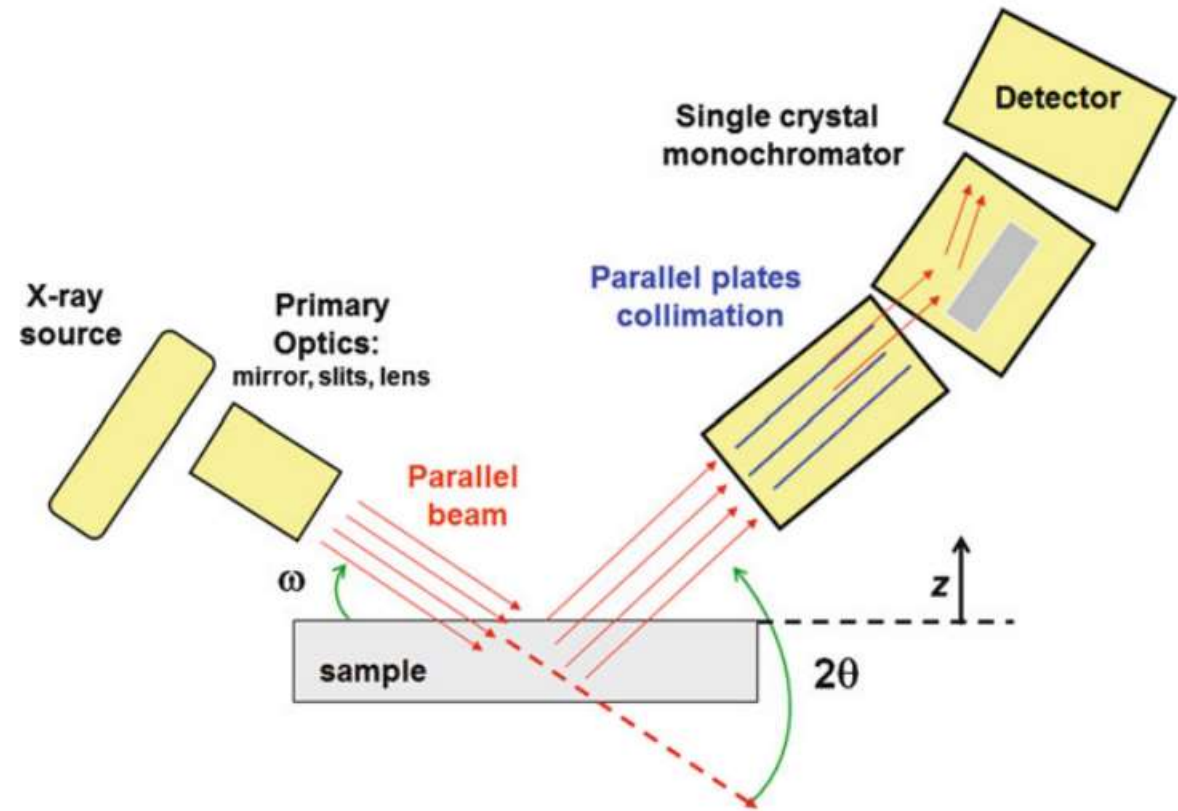
Bragg-Brentano vs. parallel beam configurations

Bragg-Brentano or focusing configuration



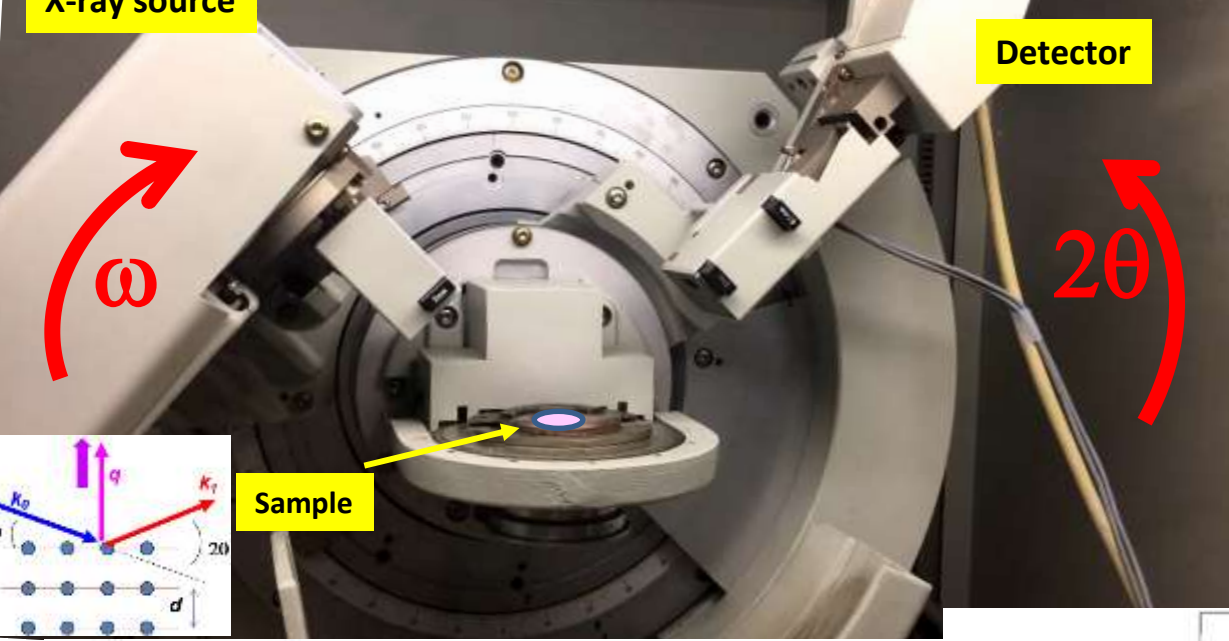
Simpler peak shape

Parallel beam configuration



Less sensitive to sample displacement error (Z error)
Better for non-flat surfaces
Better for GI-XRD, XRR

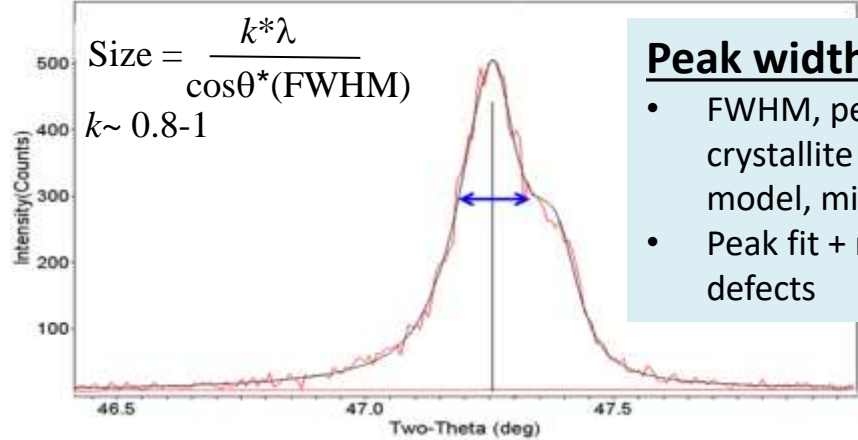
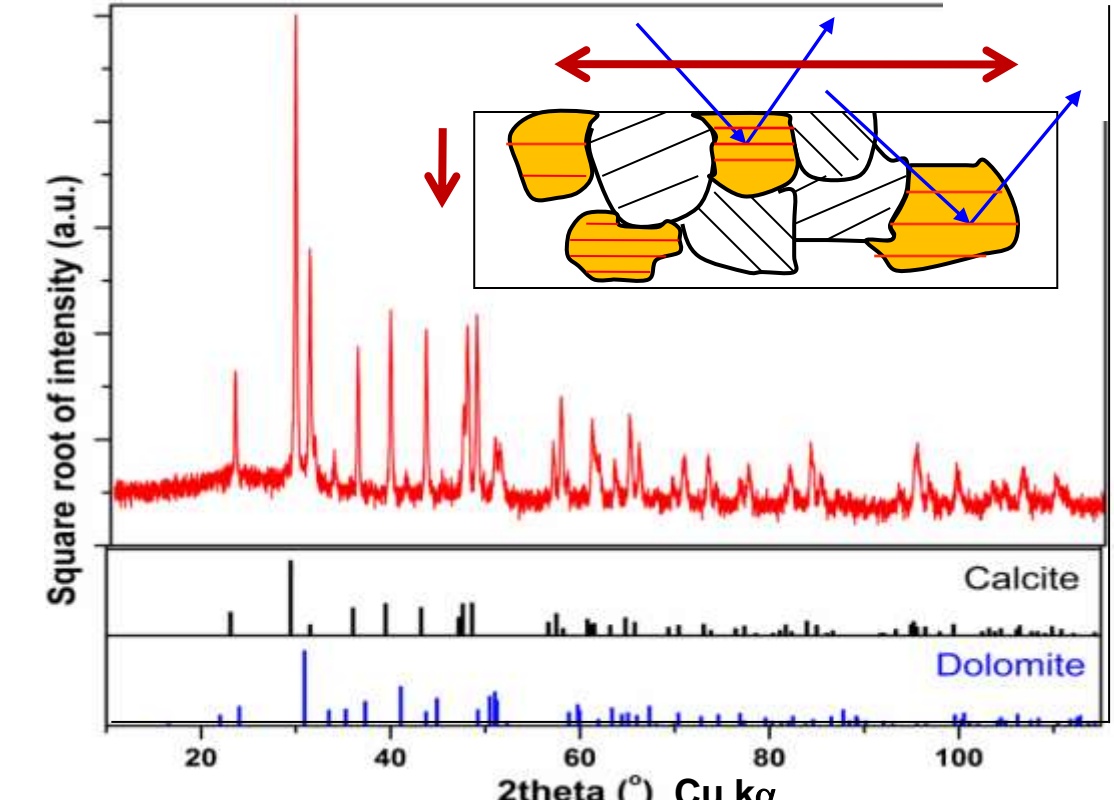
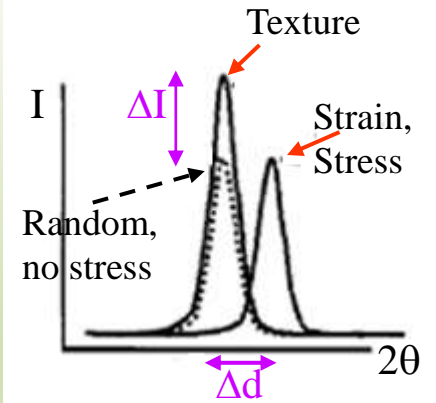




Information from typical XRD data

Peak position:

- 2θ , Bragg's law, d -spacing, crystalline phase identification, (hkl) for each peak, structure determination, lattice parameters ($a, b, c, \alpha, \beta, \gamma$)
- Δd , lattice mismatch, strain (compressive or tensile stress), alloy composition
- Can identify elements, compounds, polymorphs (ex: Ti vs. TiO_2 rutile vs. TiO_2 anatase)



Peak width (peak shape analysis):

- FWHM, peak fit, Scherrer's equation, crystallite size, grain size, Williamson-Hall model, microstrain
- Peak fit + modeling, extended and point defects

Data background:

Amorphous (short range order) contents

Peak area ratio:

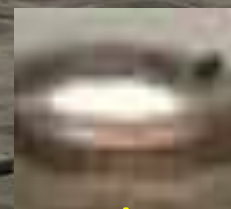
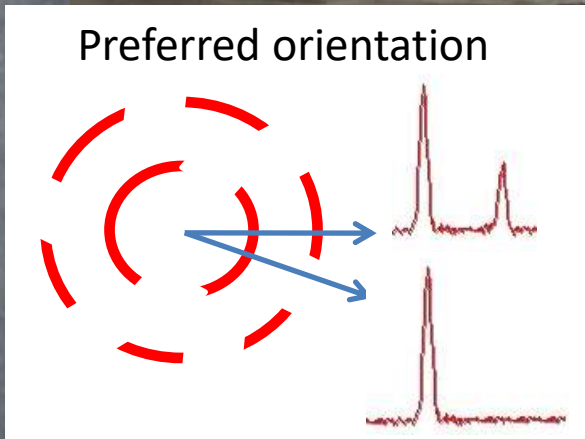
Quantitative analysis of multiple phases (> 0.1 w%)
Preferred orientation / texture (type and quantification of texture)

Whole pattern fitting:

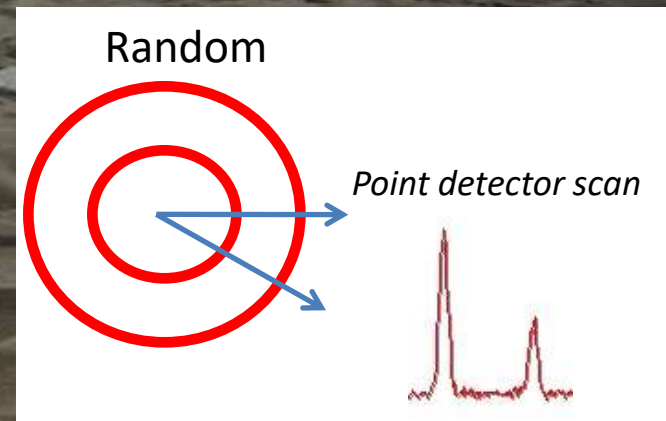
Rietveld structure refinement, accurate quantification of phases, size analysis, atomic position, etc.



**Round surface:
broad peaks**

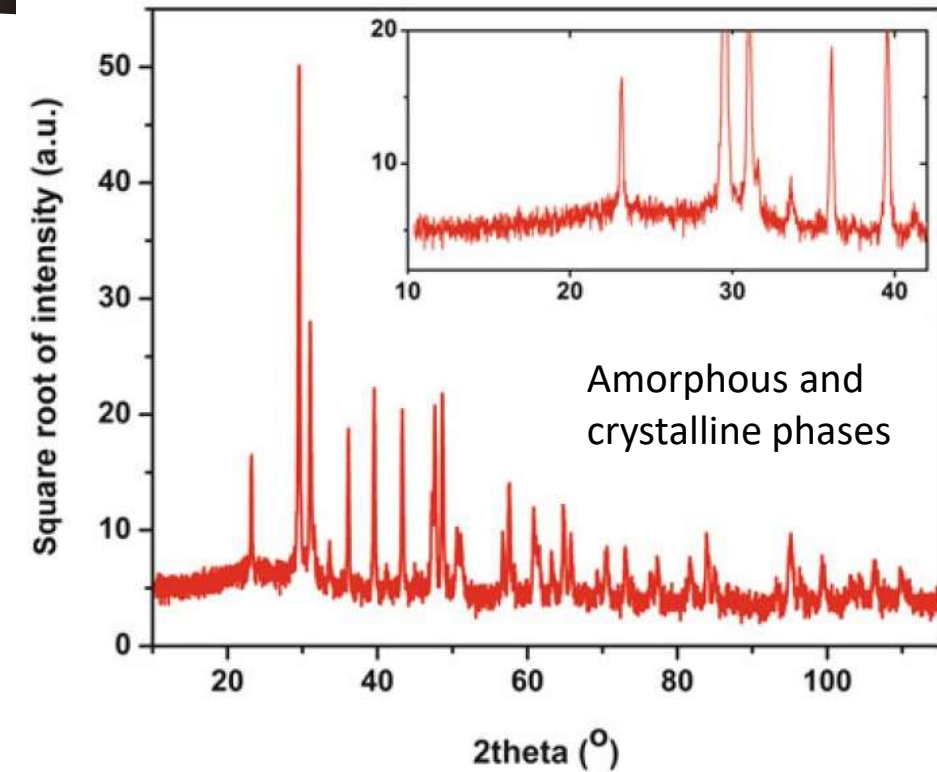
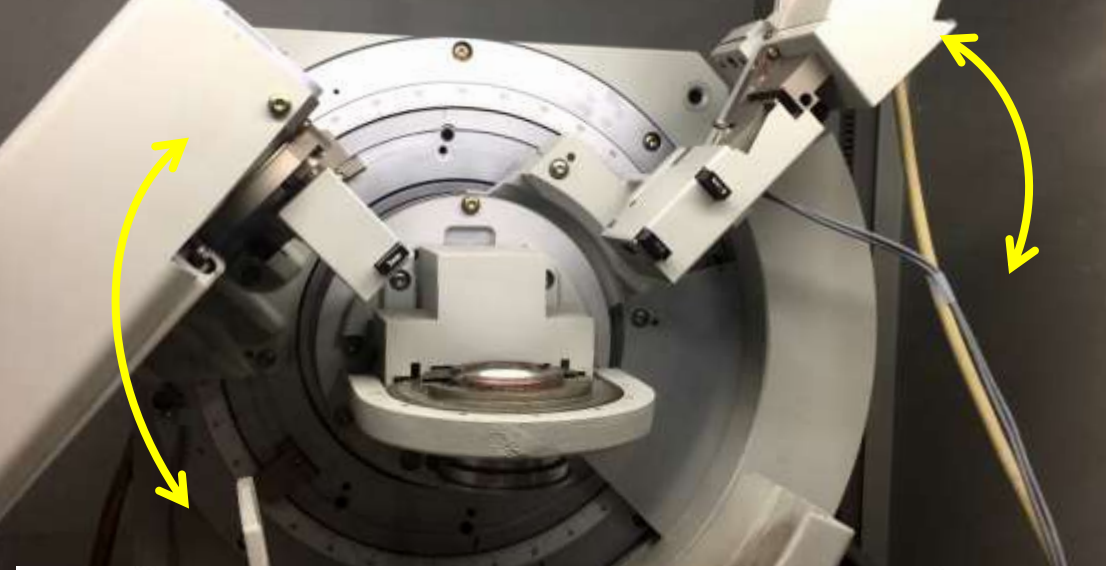


**Powder prep:
flat surface**

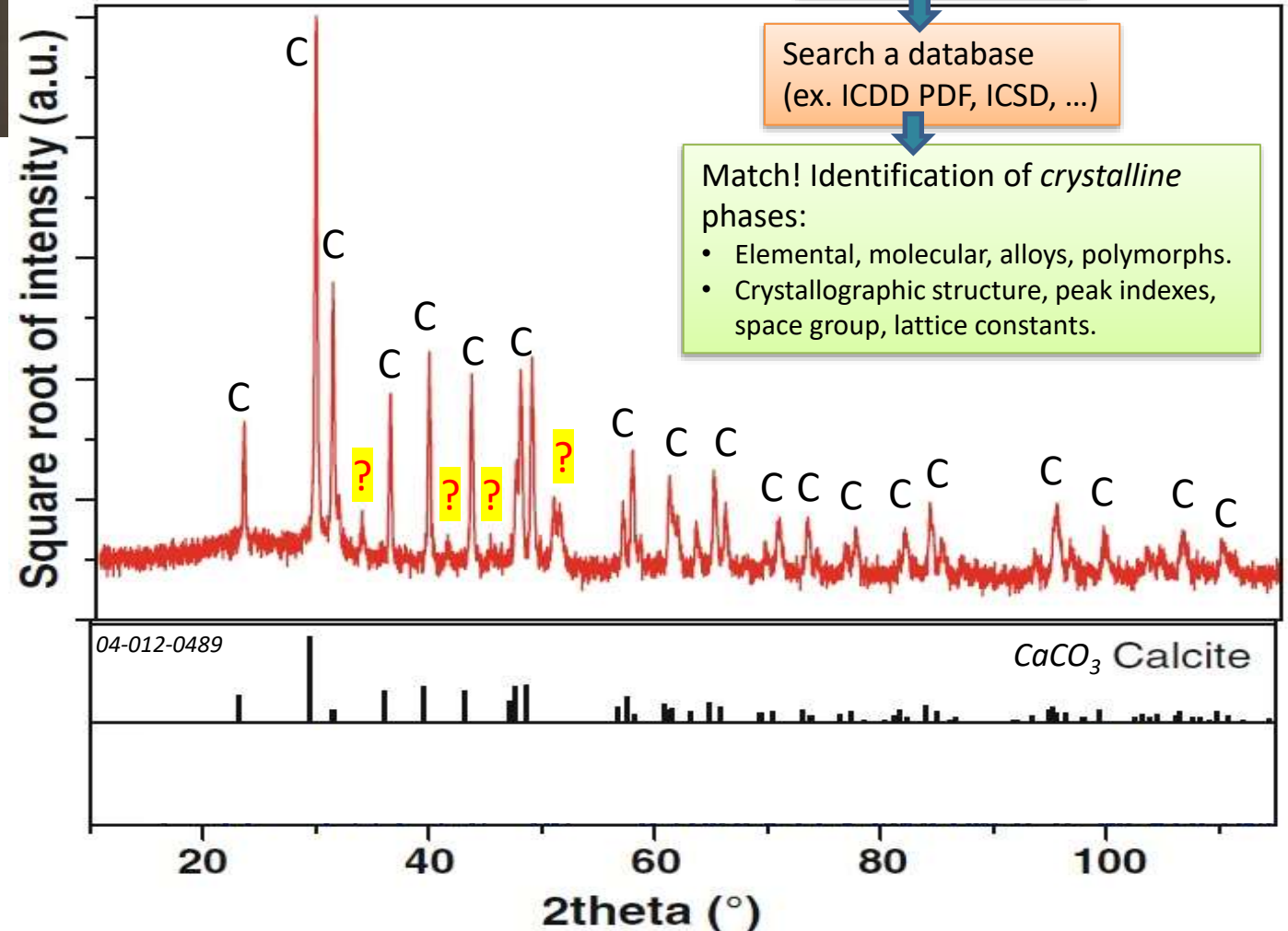


Point detector scan

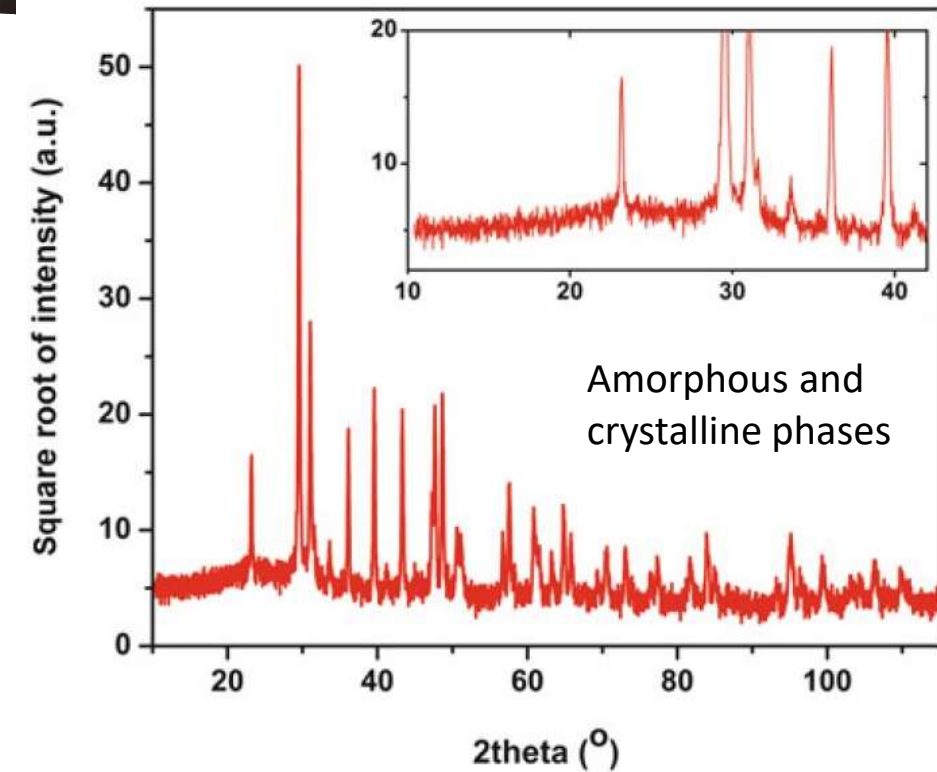
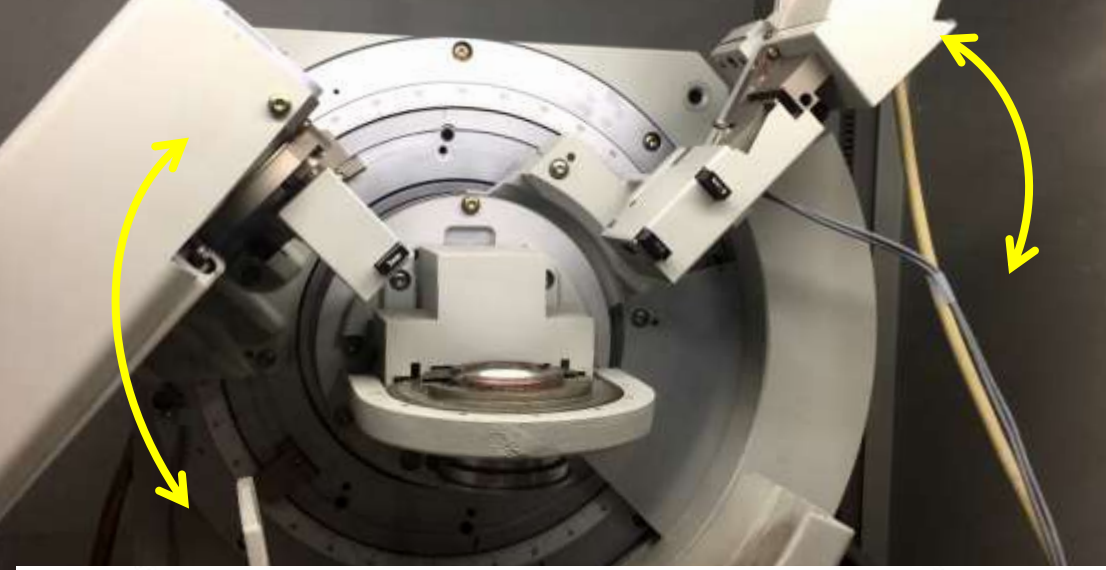
I XRD analysis walkthrough: phase identification



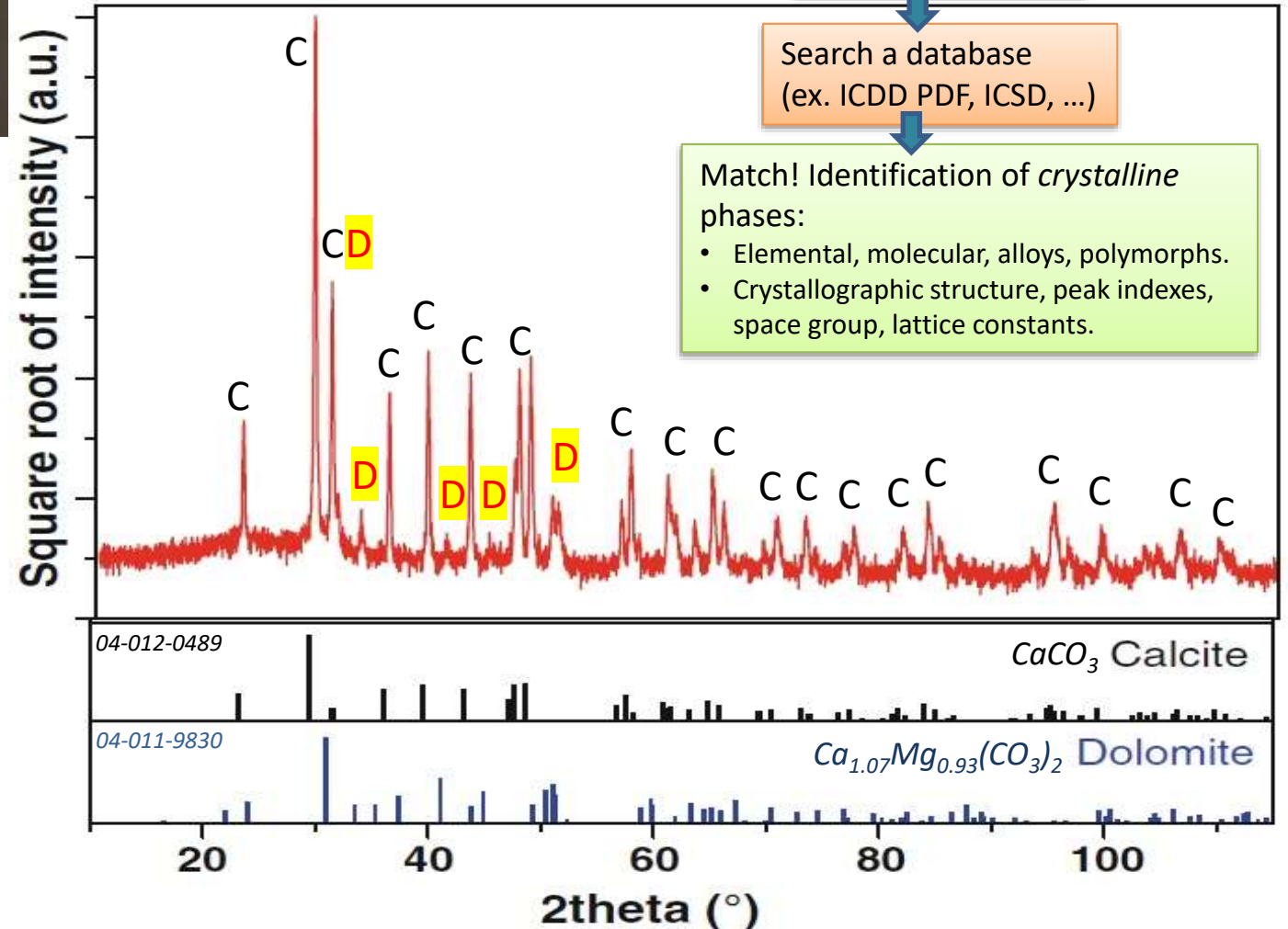
Use a *low-background* sample holder in order to identify and quantify amorphous contents.



I XRD analysis walkthrough: phase identification



Use a *low-background* sample holder in order to identify and quantify amorphous contents.



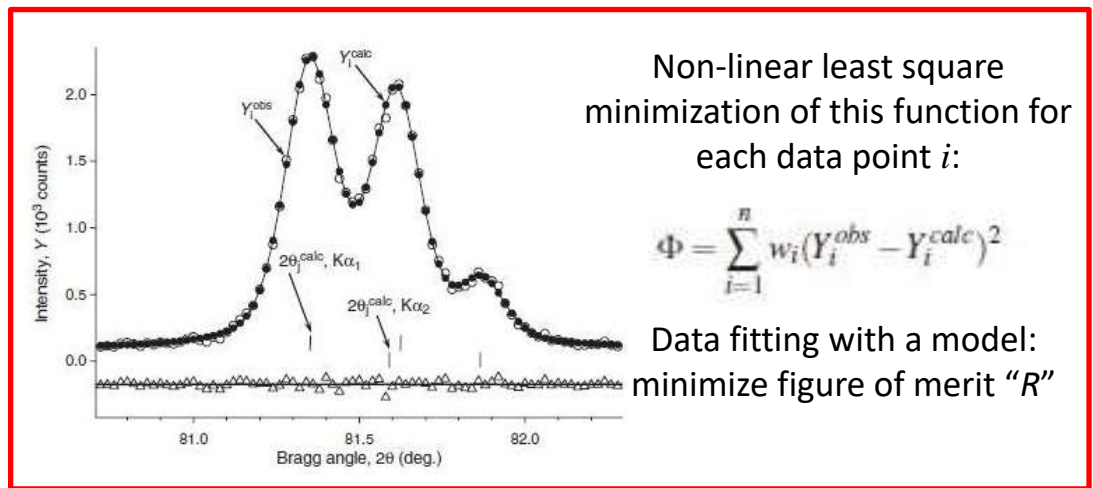
XRD analysis walkthrough: quantitative analysis



H. Rietveld
(1932-2016)

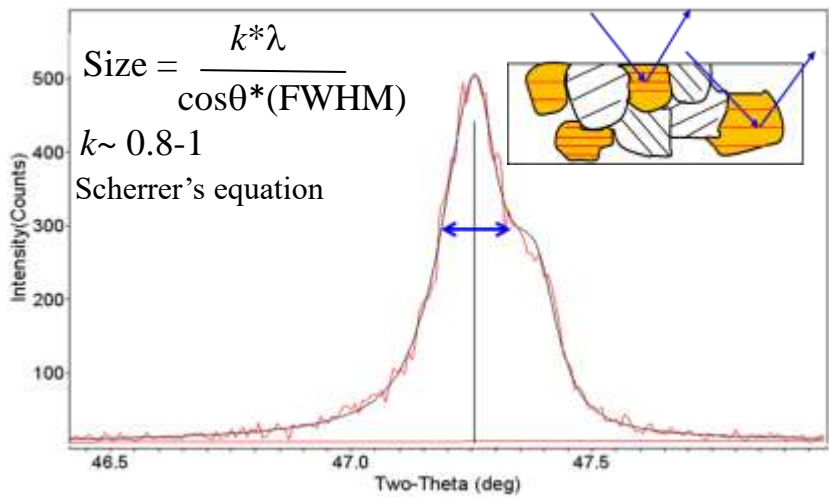
Rietveld refinement:

- Input:**
- Data
 - Peaks and background fit
 - Phases and crystalline structures
 - Instrument resolution function (peak shape)



- Output:**
- **Quantitative analysis:**
% of each phase and % of amorphous
 - Crystallite size
 - Unit cell and lattice parameters
 - Preferred orientation
 - Scale factors
 - Atomic positions/displacements in the structure
 - ...

Crystalline size:



Domain (volume) of diffraction

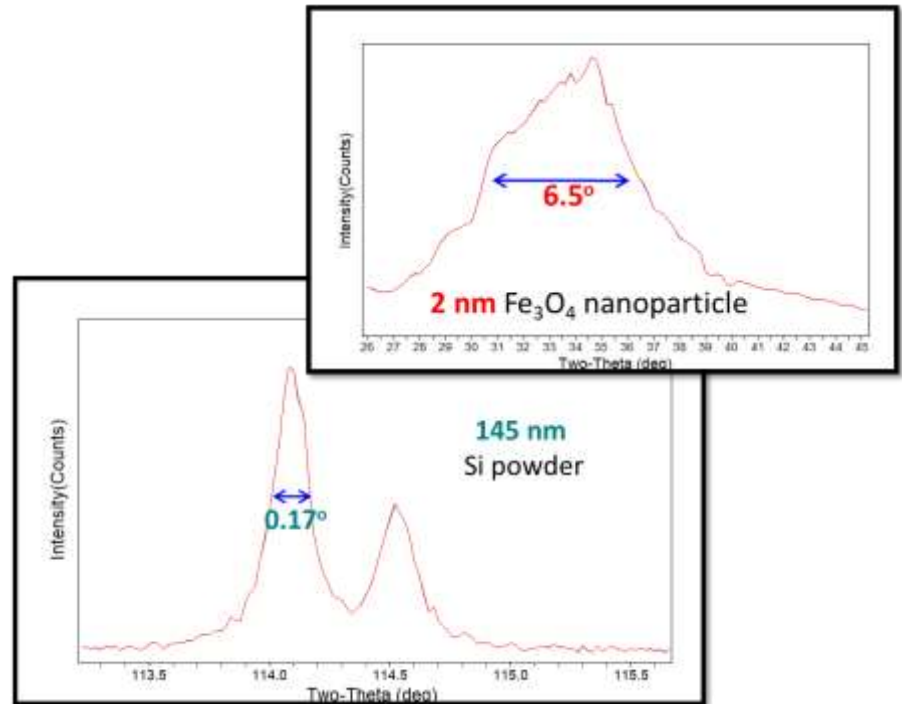
Peak fit

Choice of peak shape function:
Pseudo-Voigt, Lorentzian, Gaussian, ...

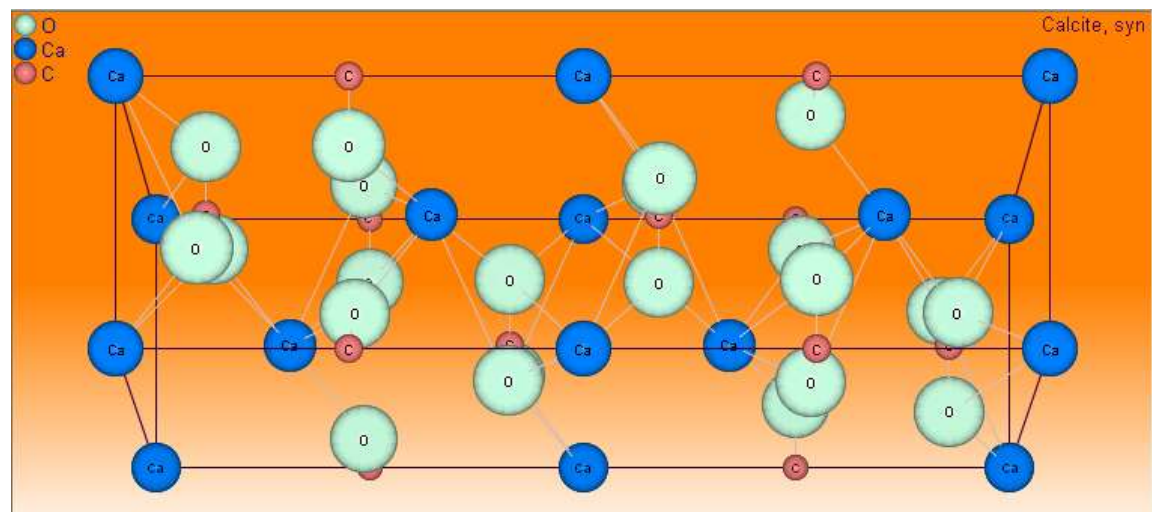
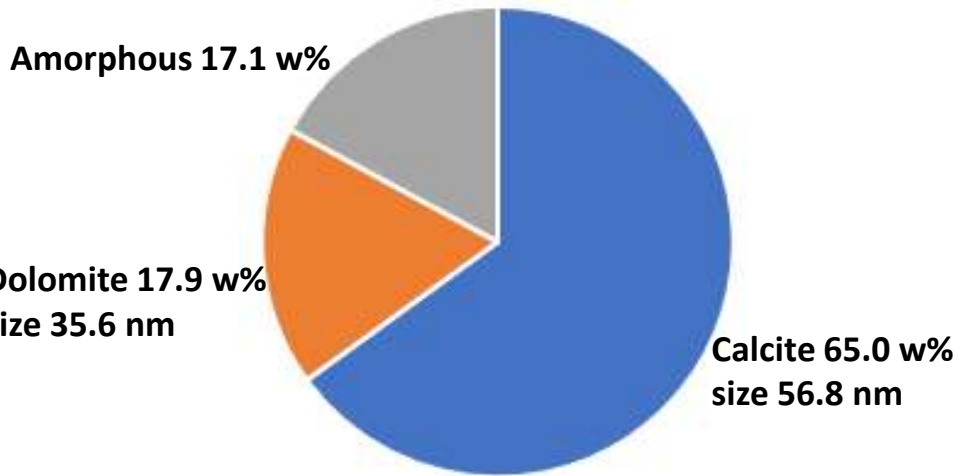
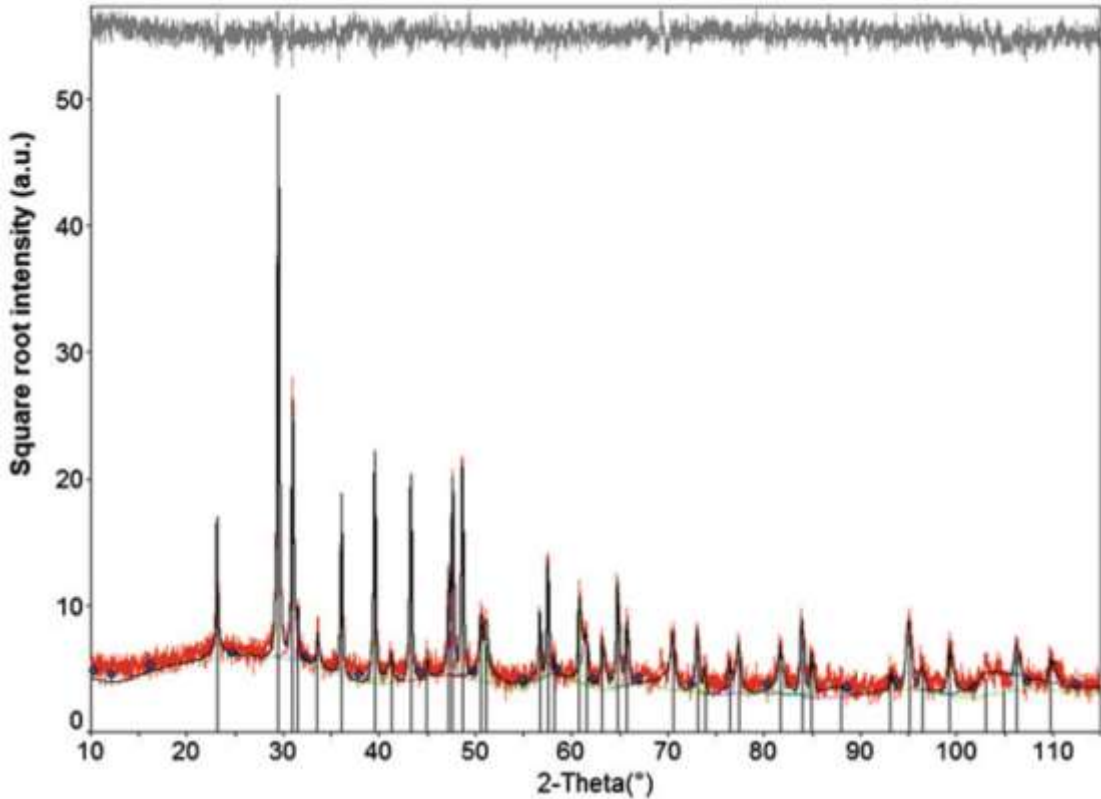
Choice of instrument peak shape function
Need standard (NIST LaB6, ...)

Scherrer's equation limitations
Directional size information
Volume average (SEM is number average)
Crystallite size \leq grain size \leq particle size

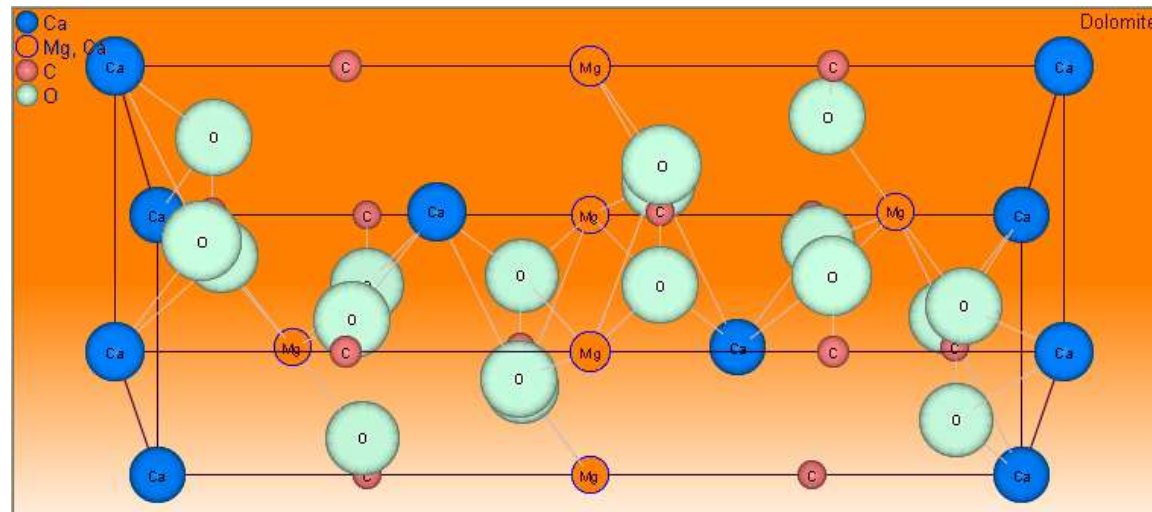
Range $< \sim 500$ nm



XRD analysis walkthrough: Rietveld analysis



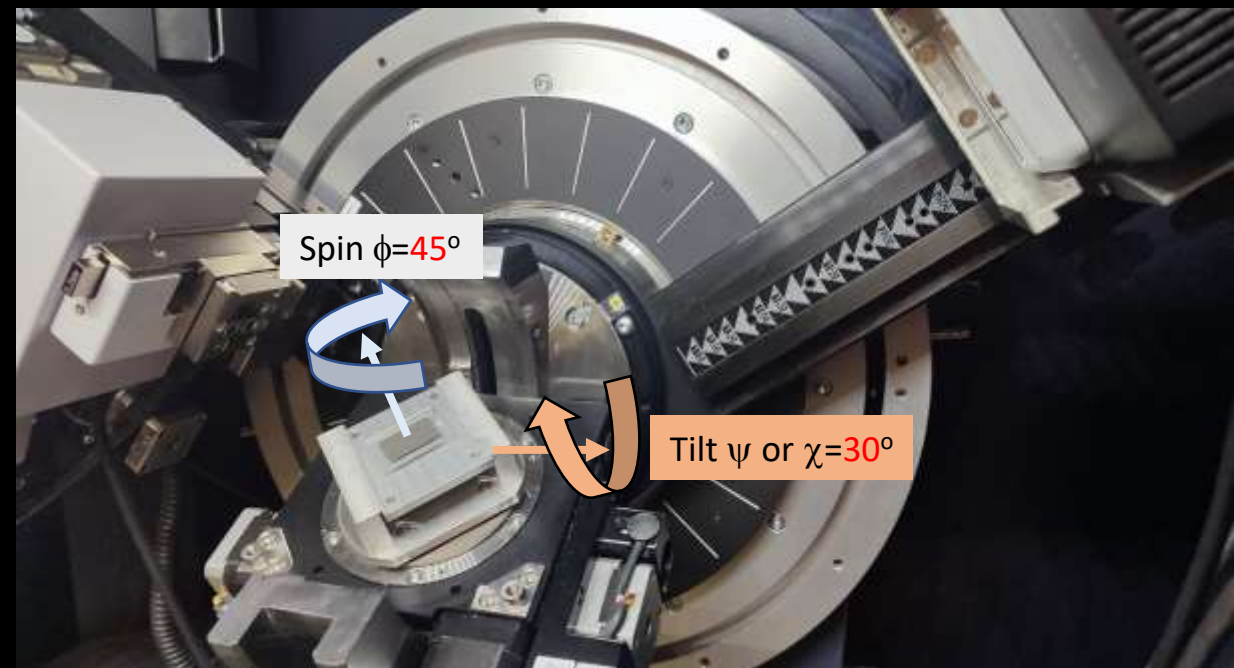
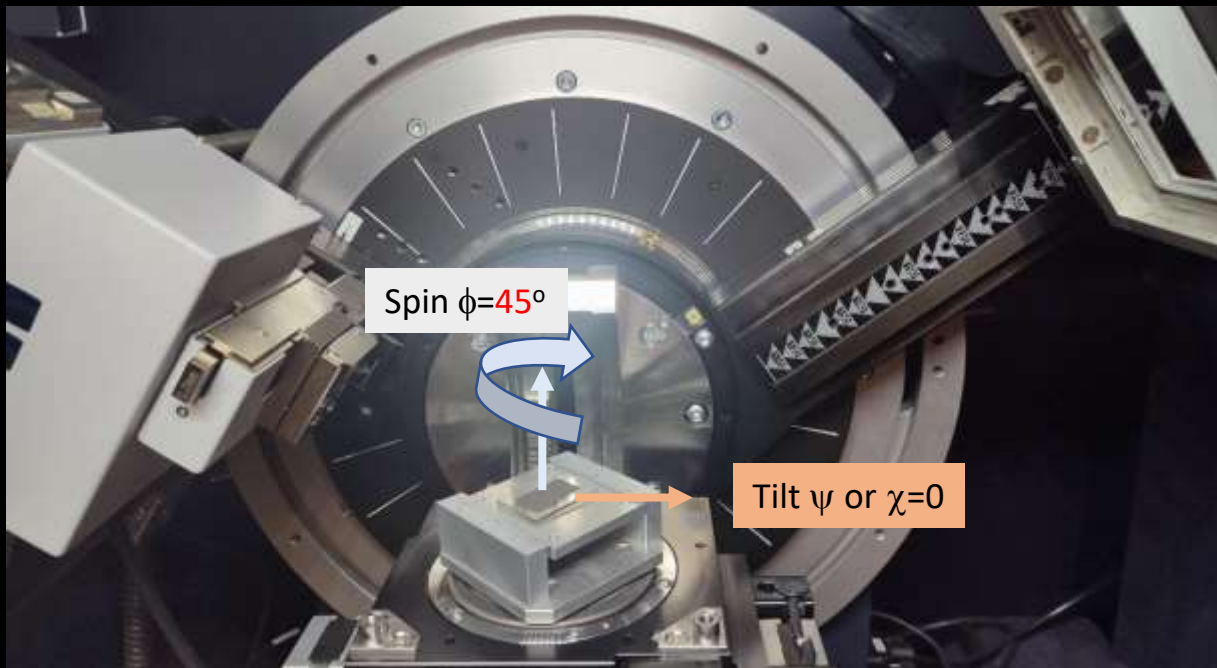
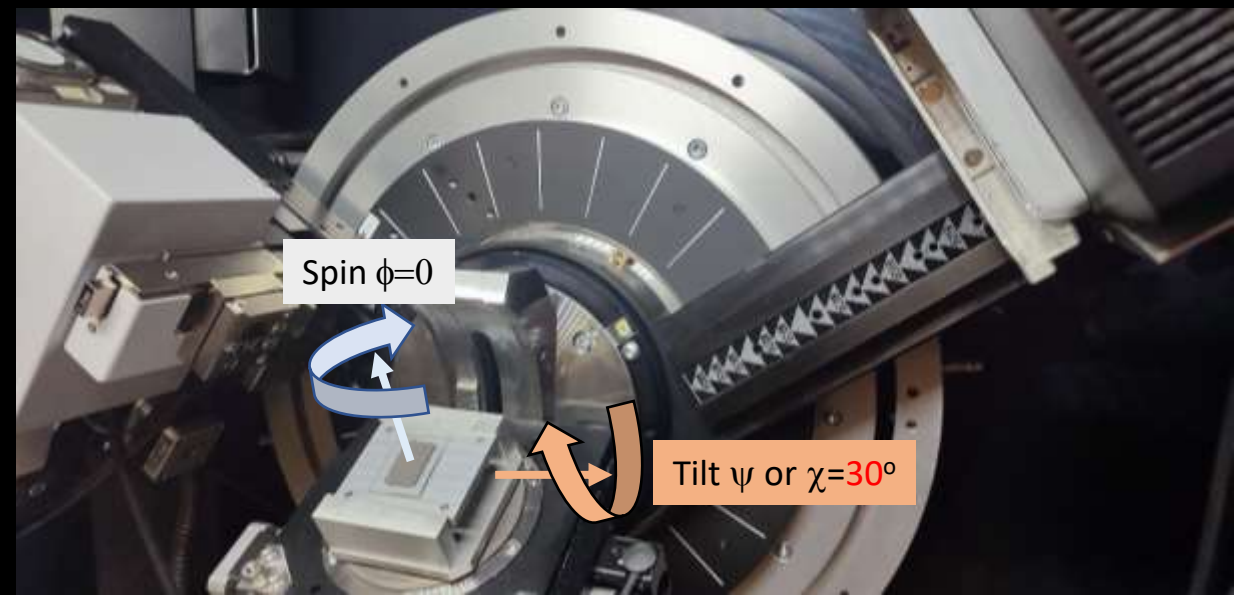
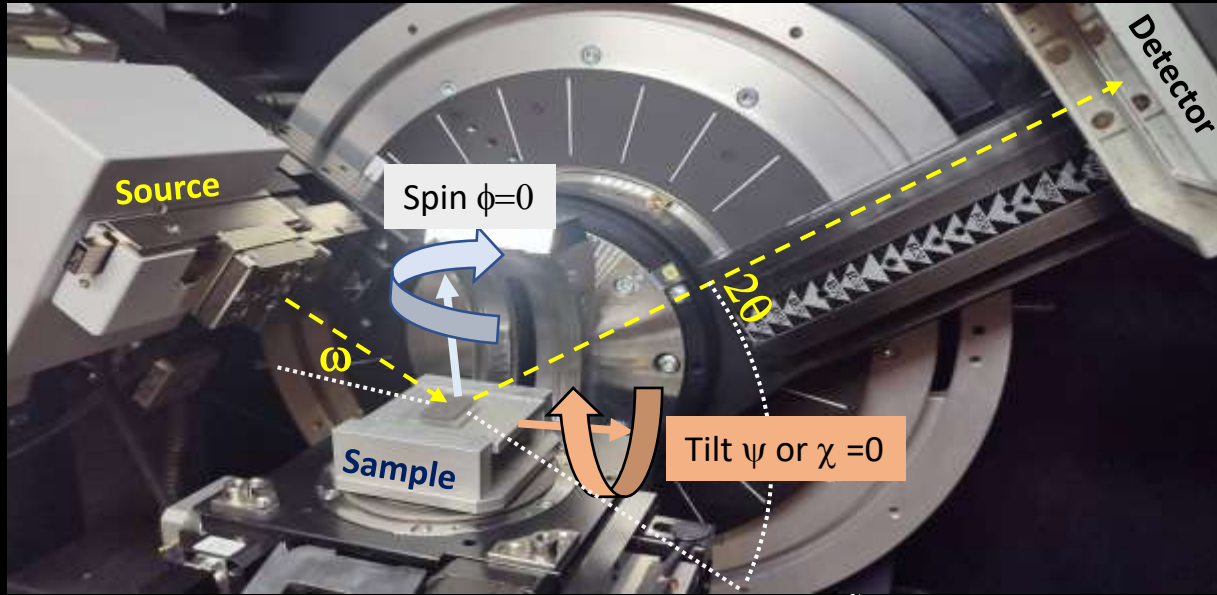
Calcite, CaCO_3 , hexagonal, R3c (167)
0.499 nm / 0.499 nm / 1.705 nm <90.0/90.0/120.0>



Dolomite, $\text{Ca}_{1.07}\text{Mg}_{0.93}(\text{CO}_3)_2$, hexagonal, R3 (148)
0.481 nm / 0.4819 nm / 1.602 nm <90.0/90.0/120.0>

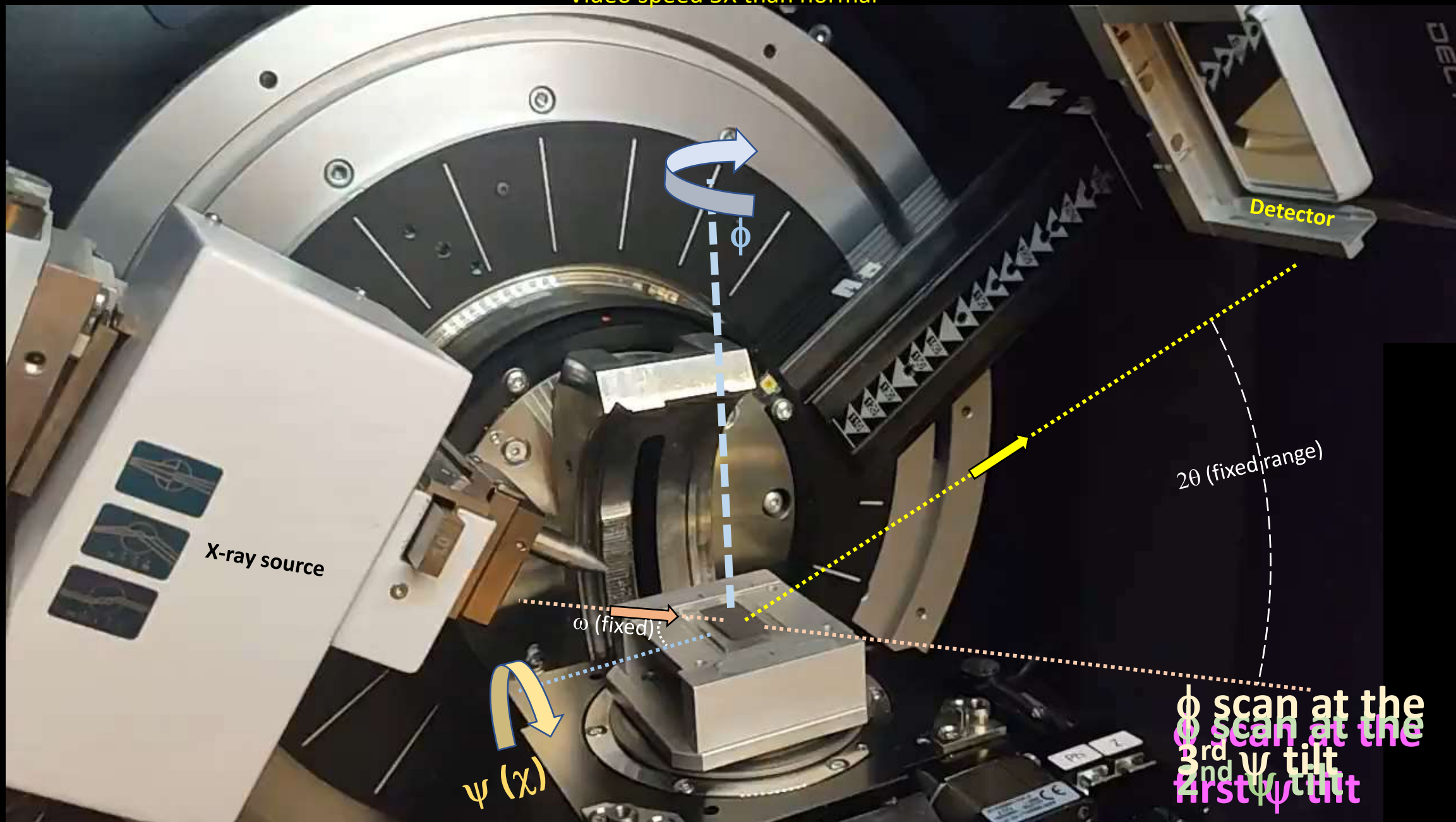


Tilt and spinning rotations



Pole figure measurement using a theta/theta XRD system with point focus and 2D detector with full ROI

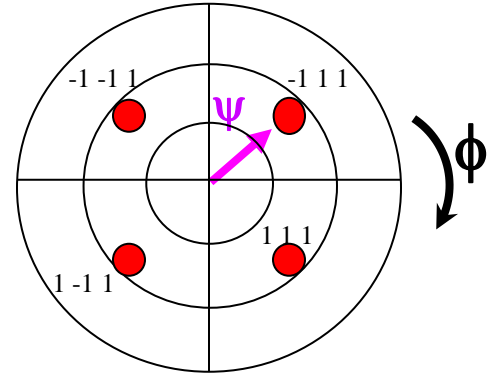
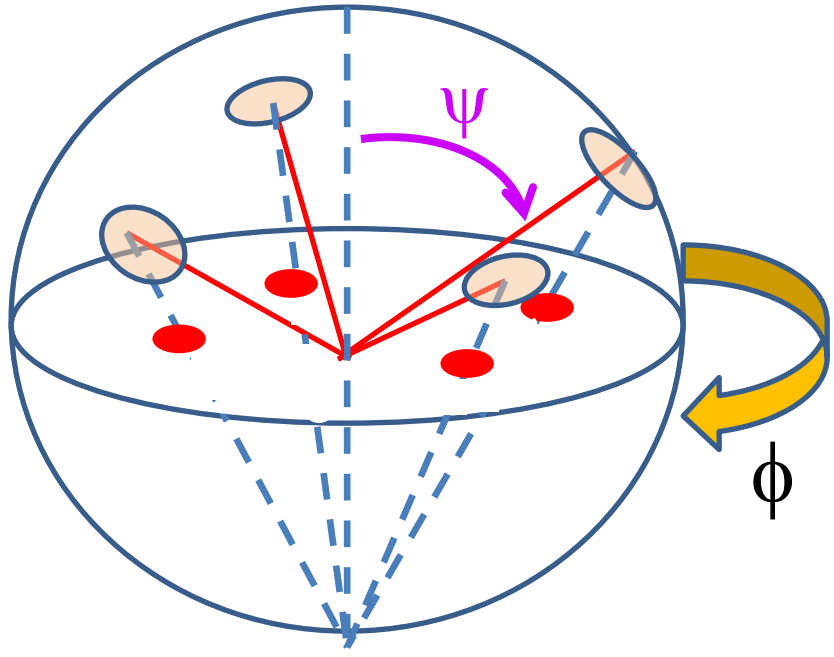
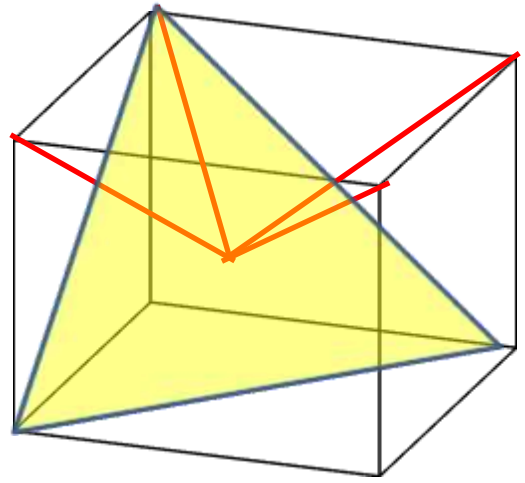
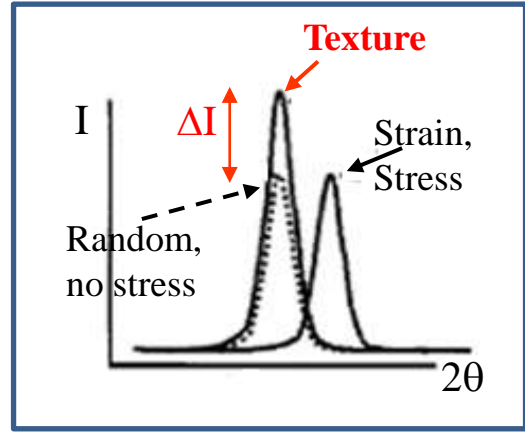
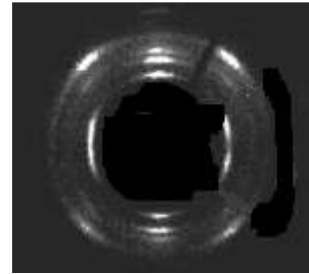
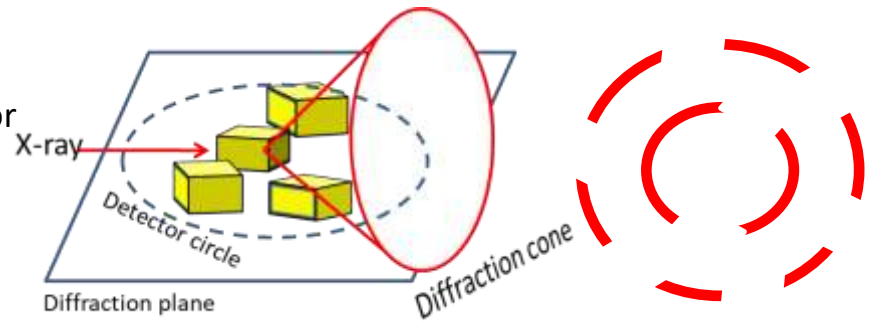
Video speed 5X than normal



Texture / preferred orientation

- What is the preferred (hkl) orientation?
What is the **texture type and its strength**?
- How is a (hkl) orientation distributed in the material? Use **pole figure** measurements for a certain (hkl).
- Use a combination of pole figures to determine the **orientation distribution function (ODF)**.
- ODF describe the plans, directions and volume of each orientation present.

Poly crystal (texture)

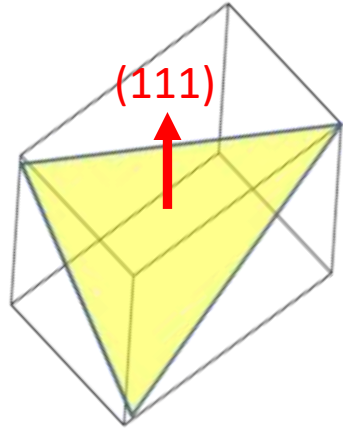


Azimuth
 $\phi = 45^\circ, 135^\circ, 225^\circ, 315^\circ$

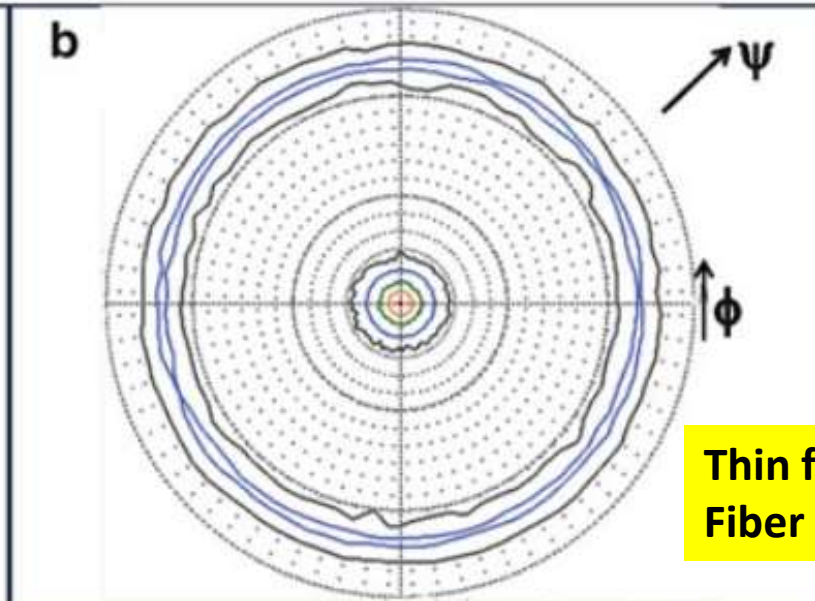
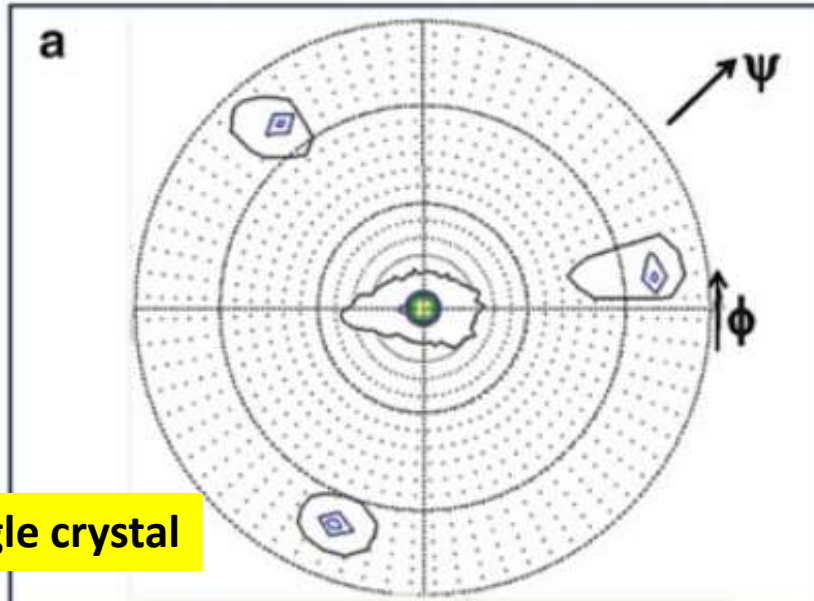
Tilt $\psi = 54.7^\circ$

$\psi: [100], [111]$

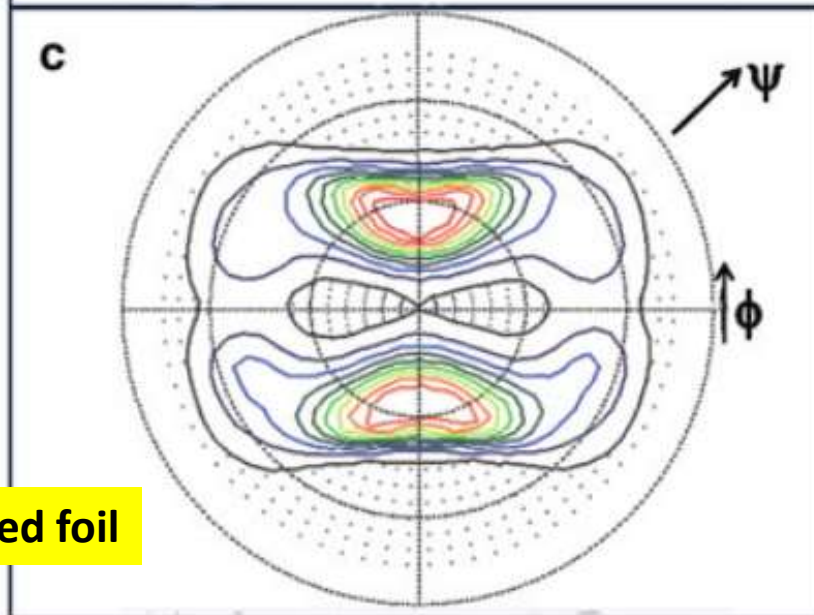
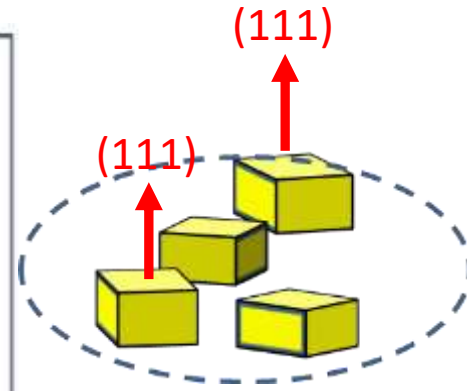
I (111) pole figures from 4 Cu samples: thin film, rolled foil and two types of single crystal



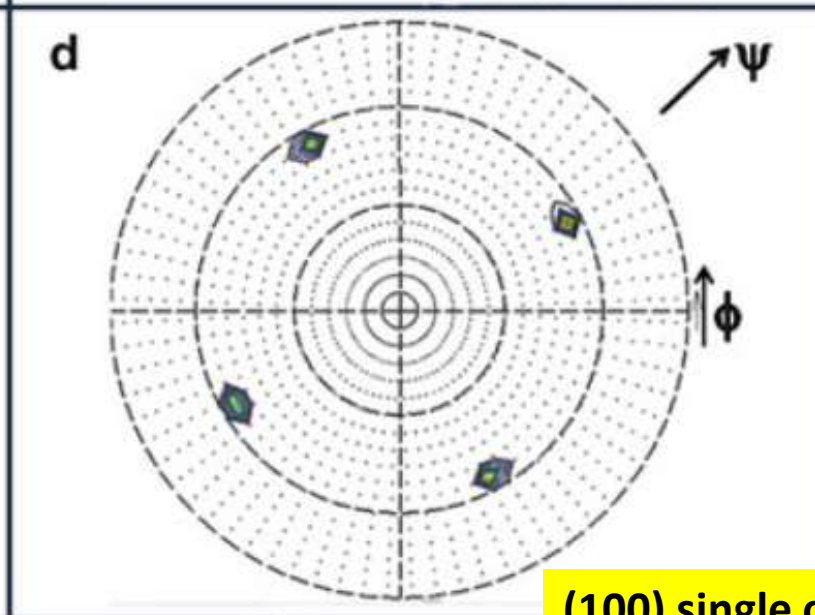
(111) single crystal



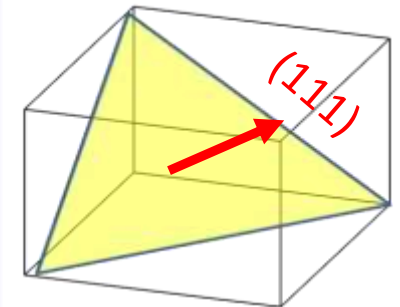
Thin film
Fiber texture



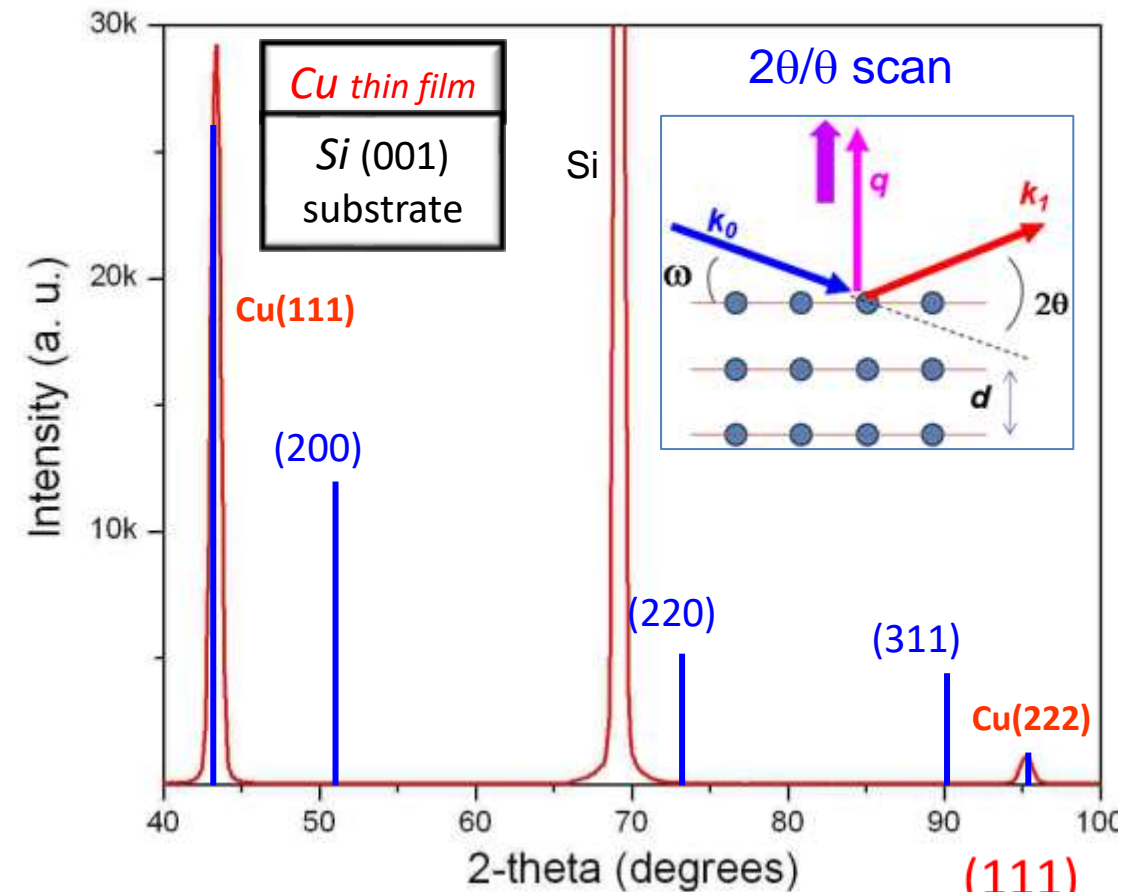
Rolled foil



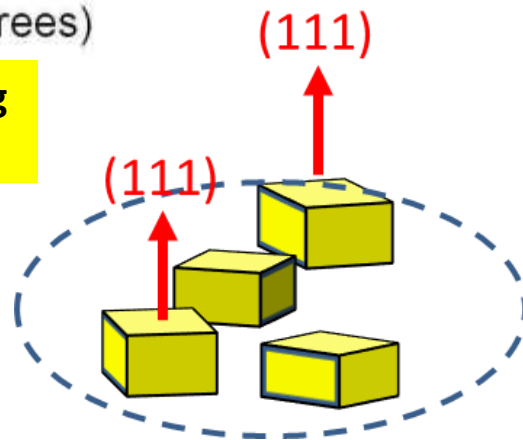
(100) single crystal



Preferred orientation in a thin film



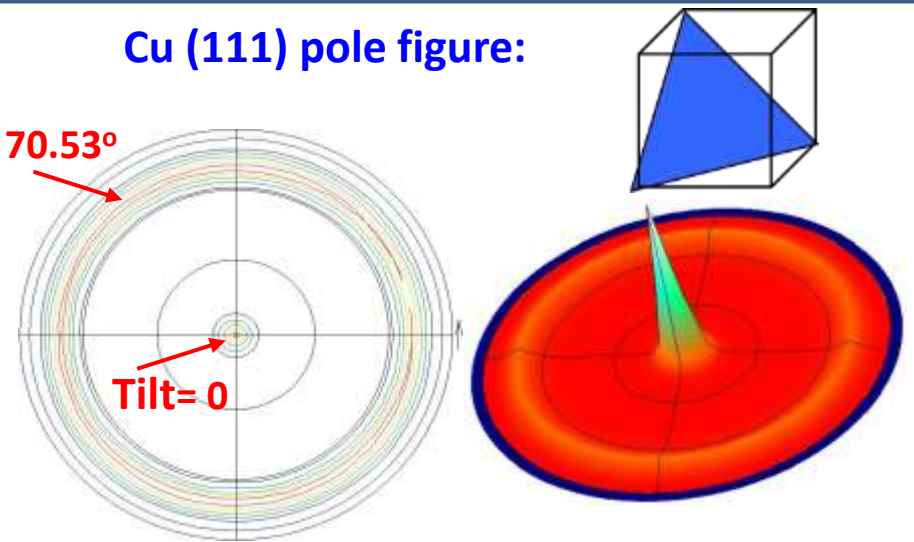
All grains are **<111>** oriented along the film growth direction.



Cu (111) pole figure:

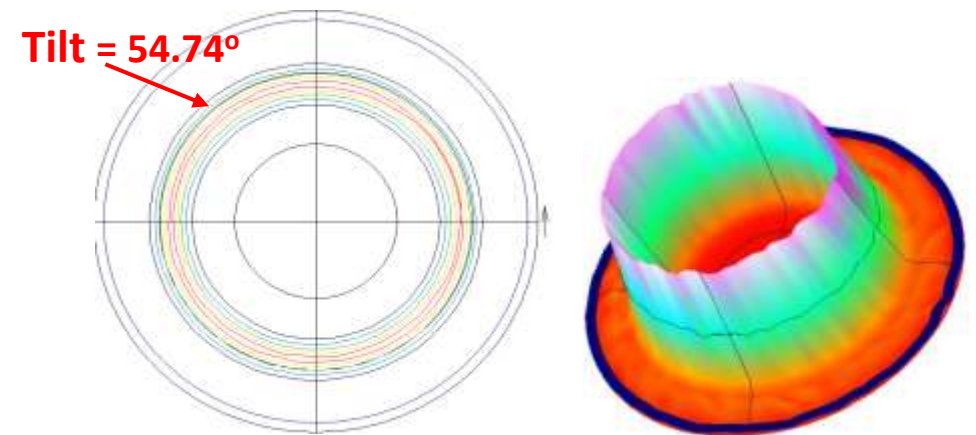
Tilt = 70.53°

Tilt = 0



Cu (200) Pole figure:

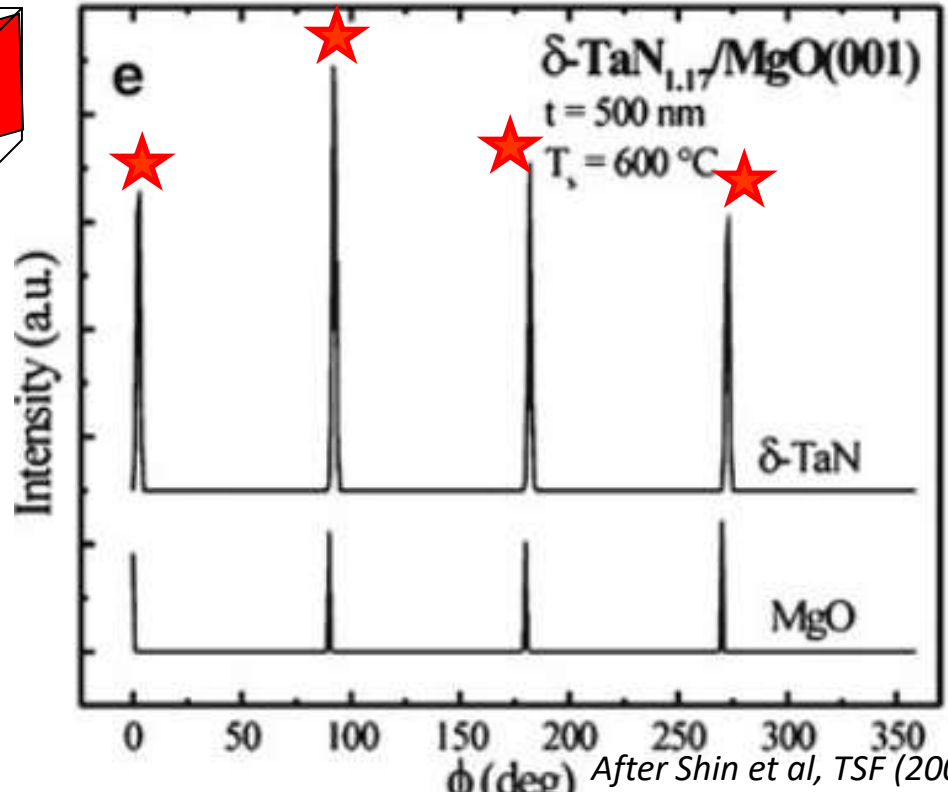
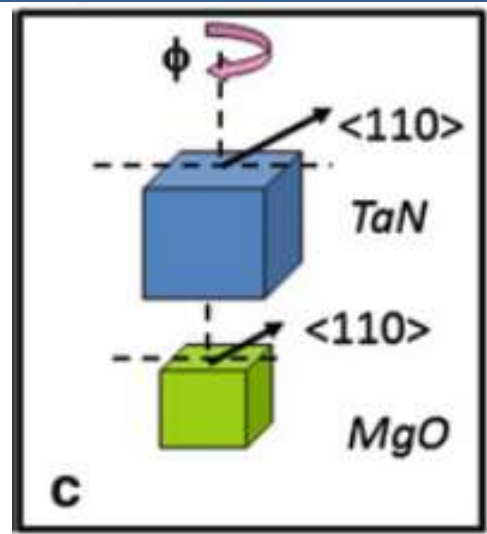
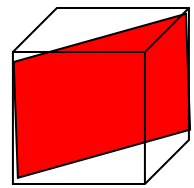
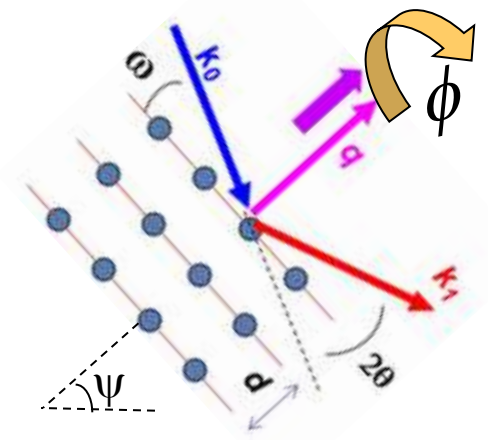
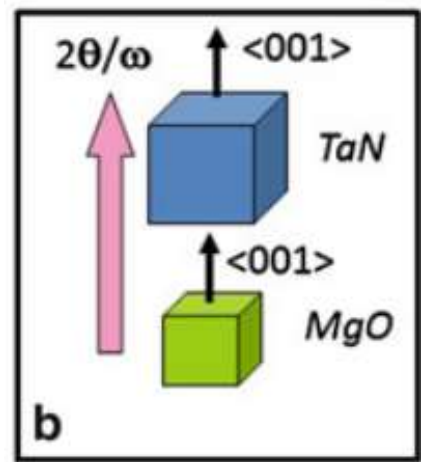
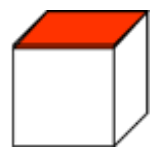
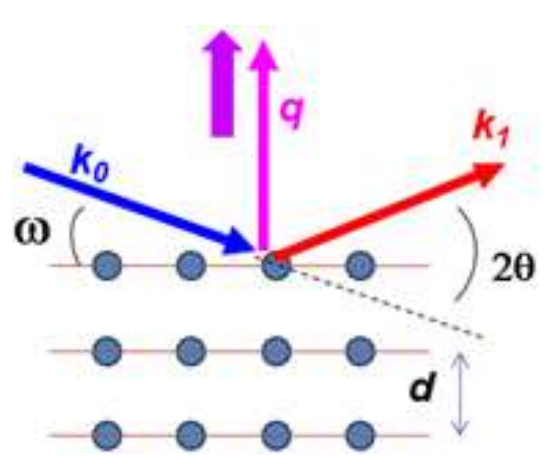
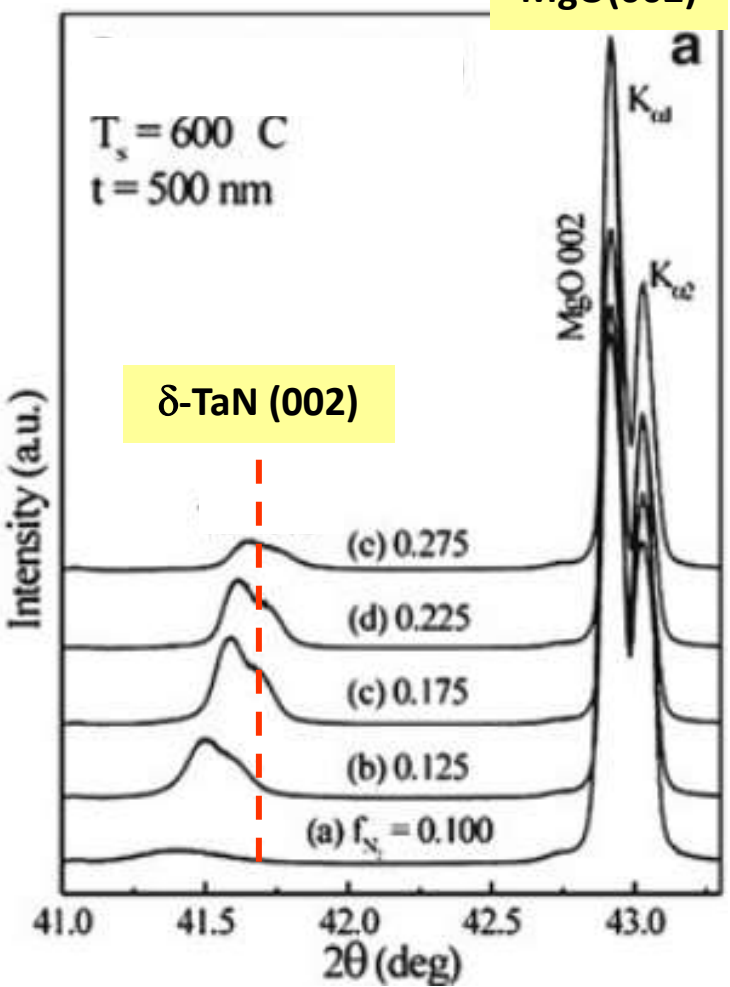
Tilt = 54.74°



Grains are **randomly** oriented along the surface

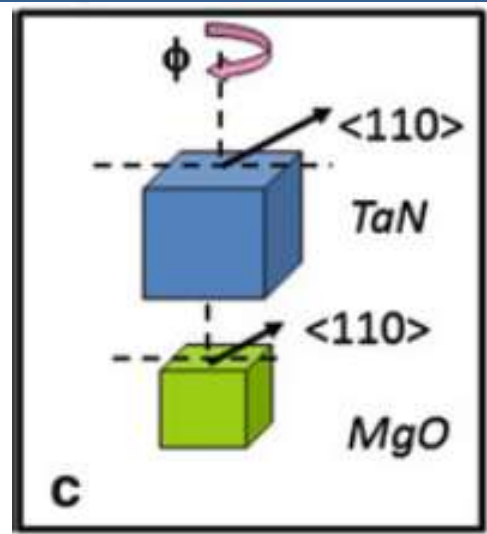
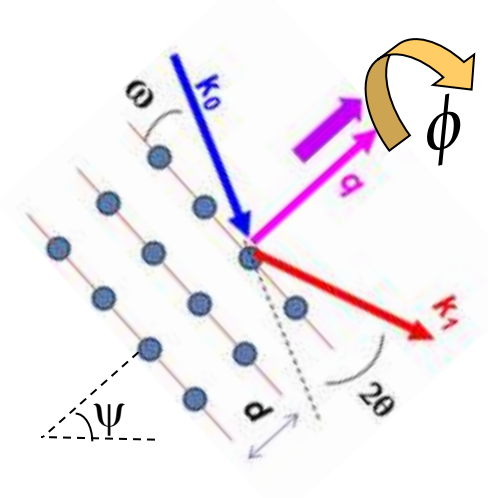
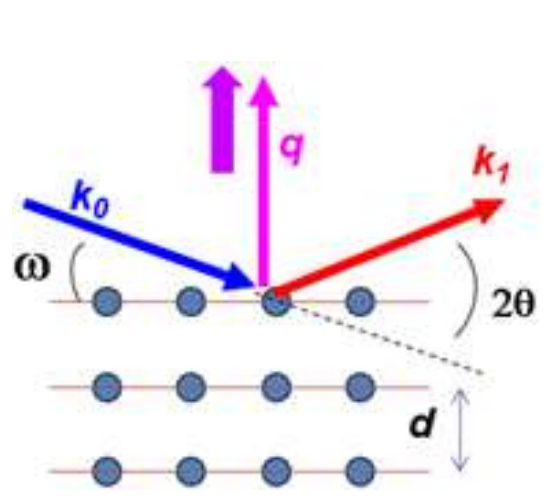
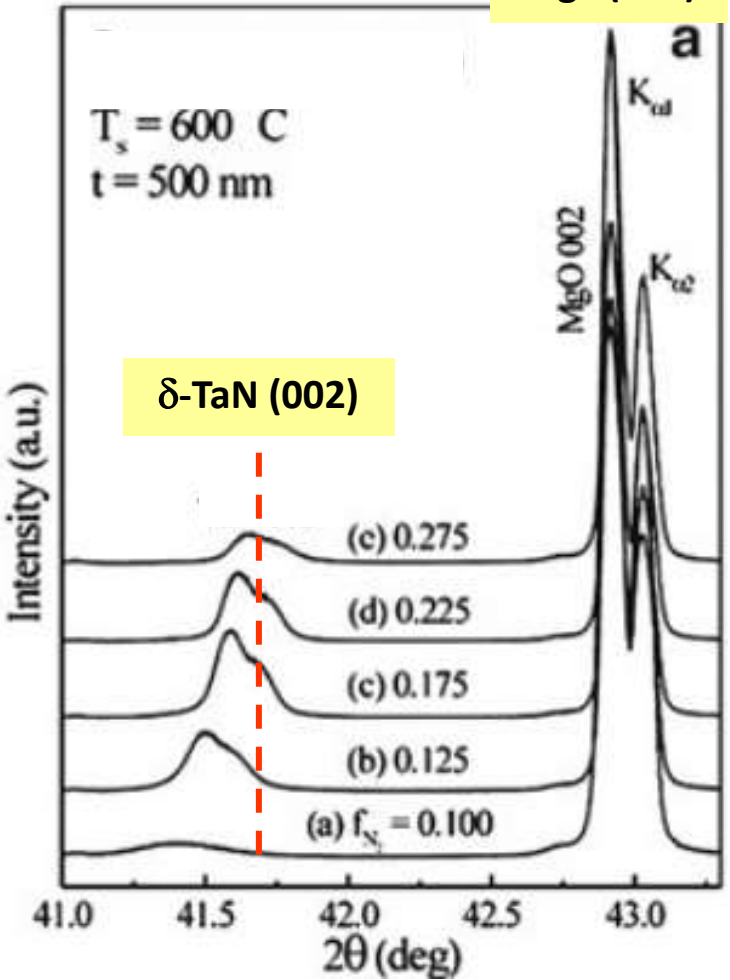
TaN film
MgO (001) substrate

MgO(002)

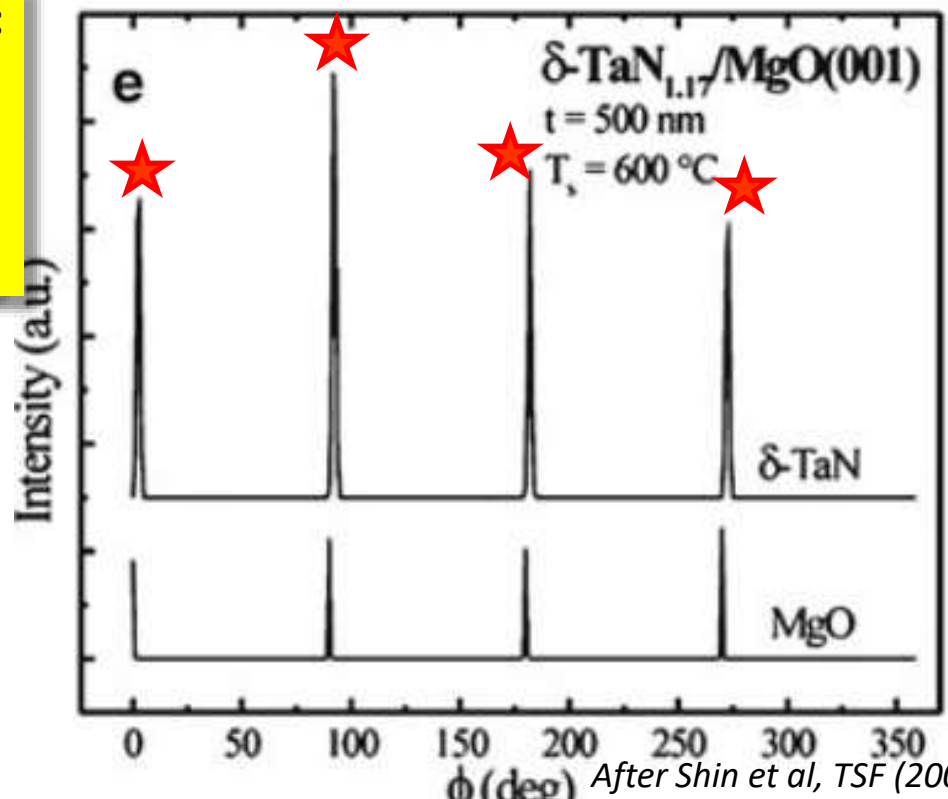
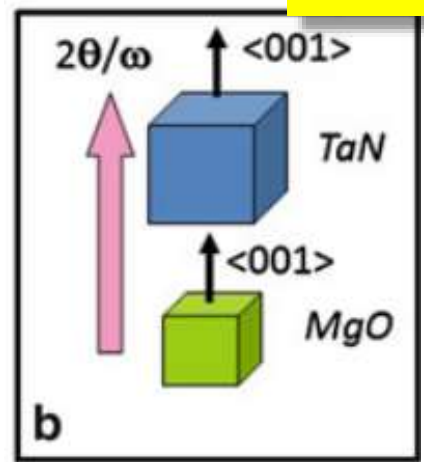


TaN film
MgO (001) substrate

MgO(002)

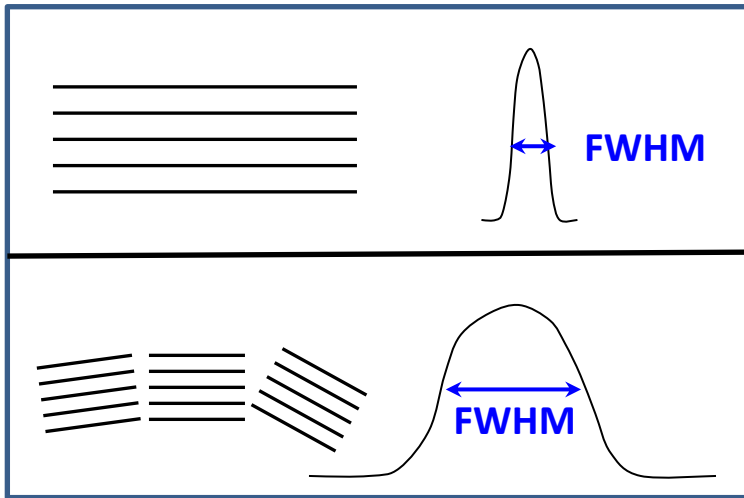
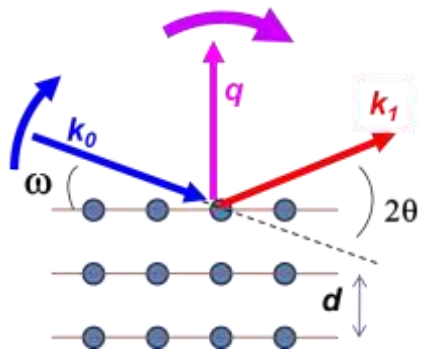


Cube on cube epitaxy:
 $(001)_{\text{TaN}} // (001)_{\text{MgO}}$
 $(100)_{\text{TaN}} // (100)_{\text{MgO}}$

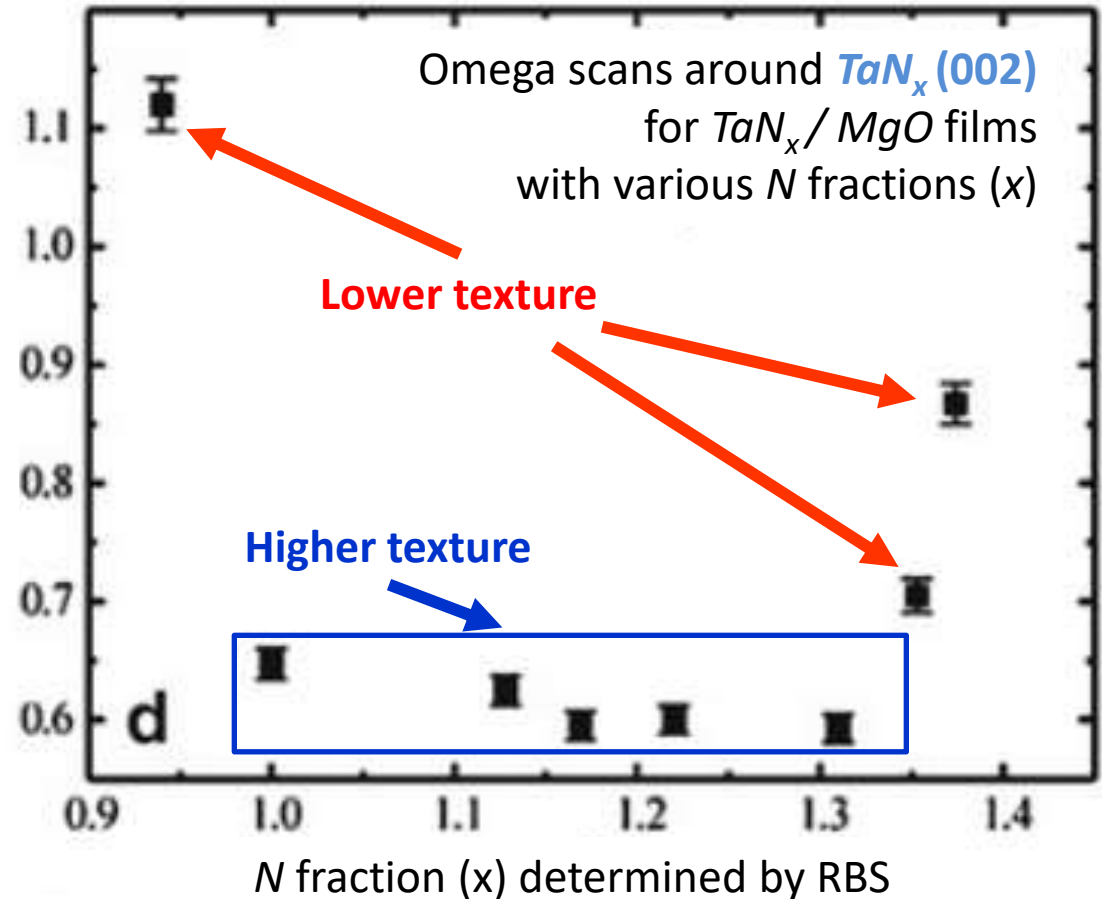


TaN film
MgO (001) substrate

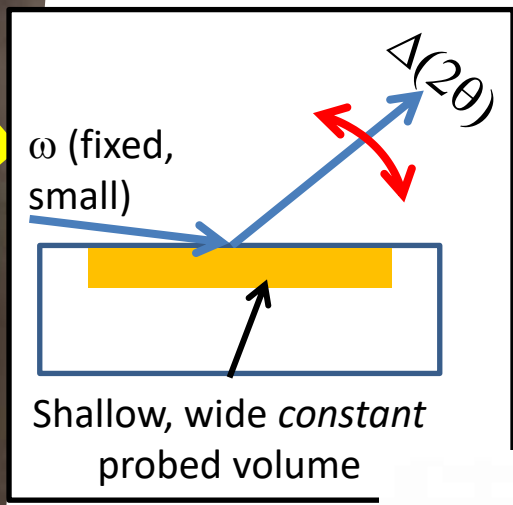
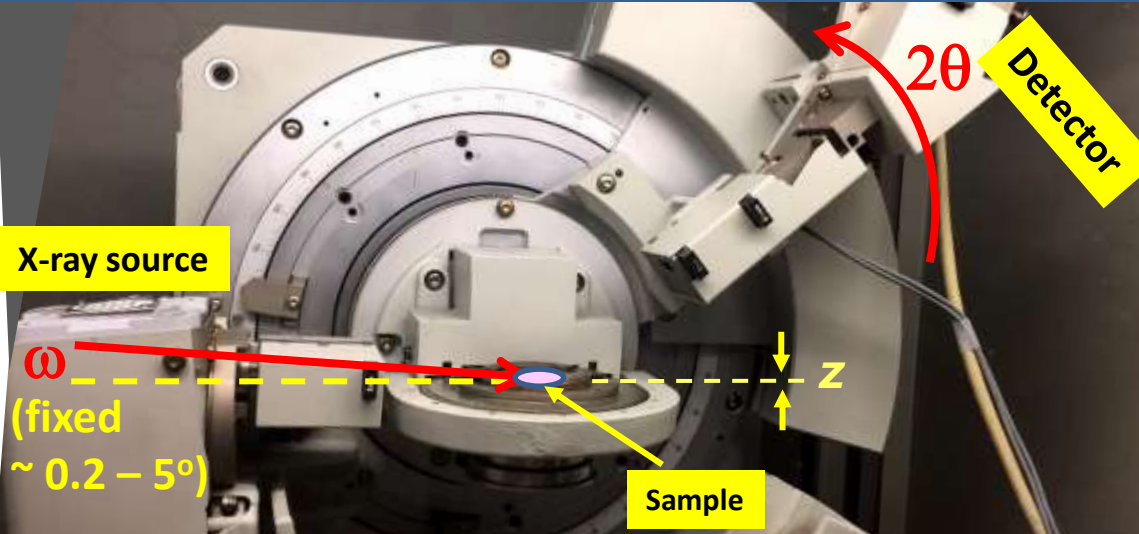
Omega scan around a (hkl) peak
 preferred orientation analysis



Omega scan peak width ($^\circ$)



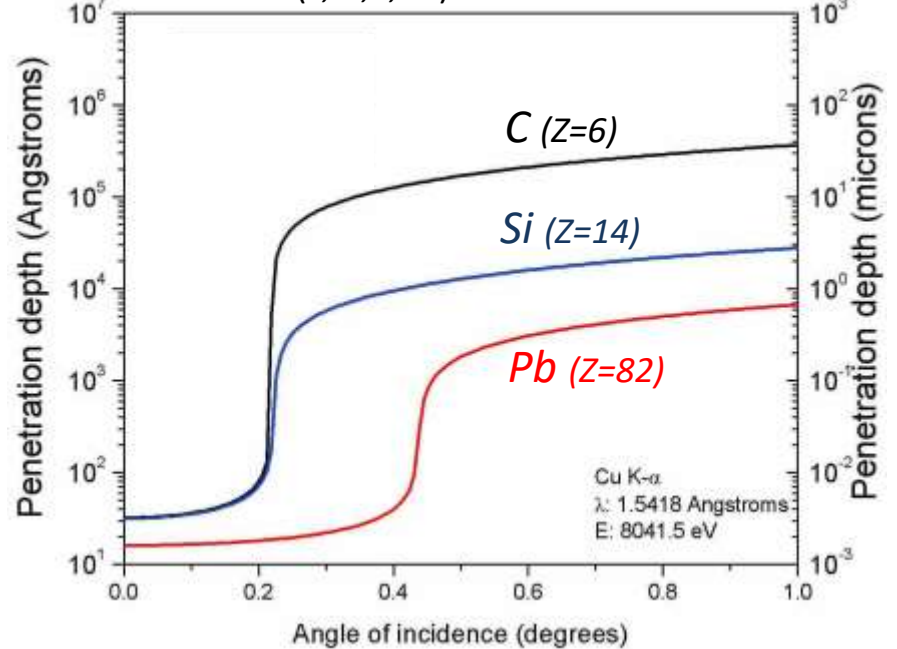
Glancing incidence x-ray diffraction (GI-XRD)



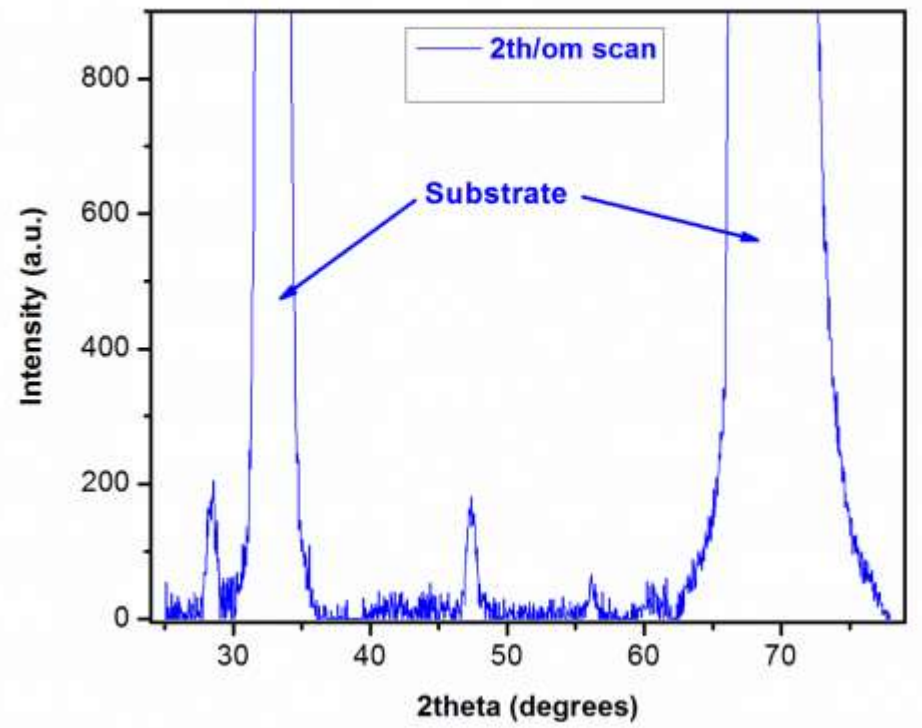
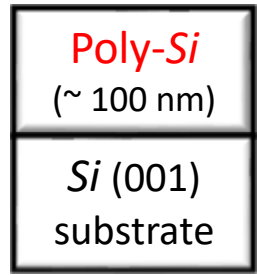
- Enhances intensities from **surface, near surface** regions.
- Phases and grain orientations in **multiple directions** also not parallel to the surface (2θ only scan).
- Change ω to probe different depth ("**depth profiling**")
- Sample height (z) critical: use **parallel**

X-ray penetration depth:

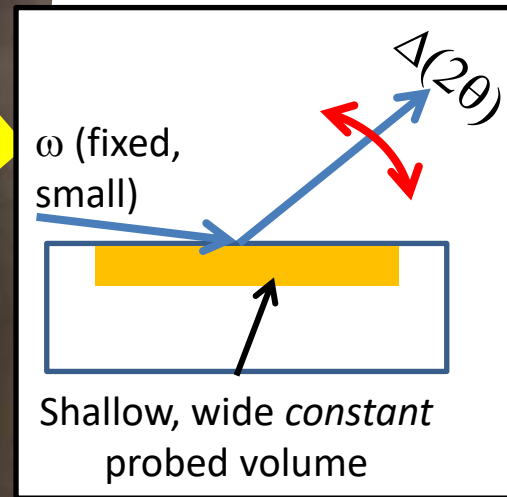
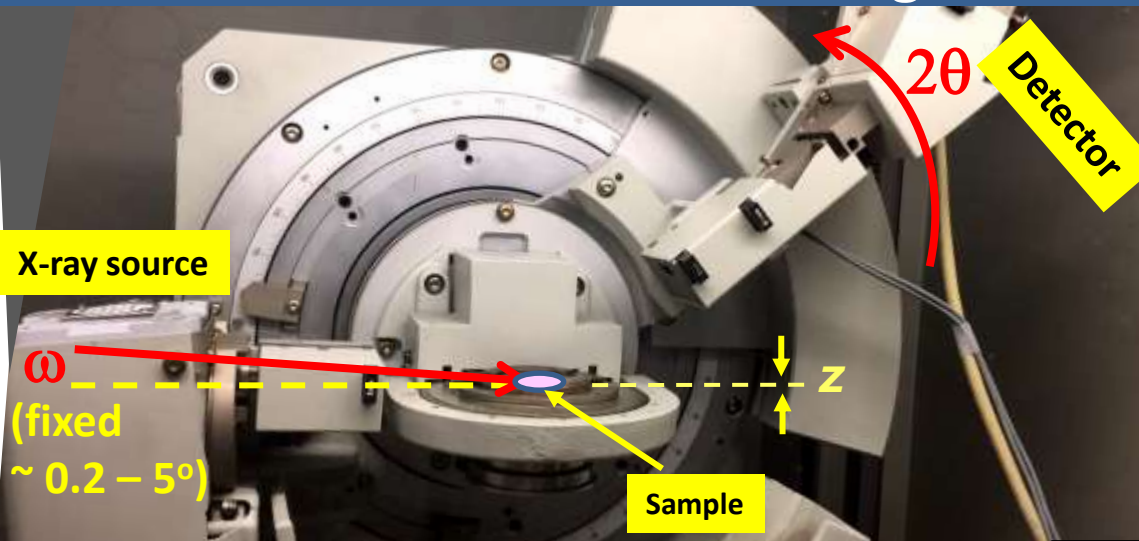
Type of radiation, angle of incidence, material (Z , A , r , m)



Example:
Poly-Si gate in CMOS



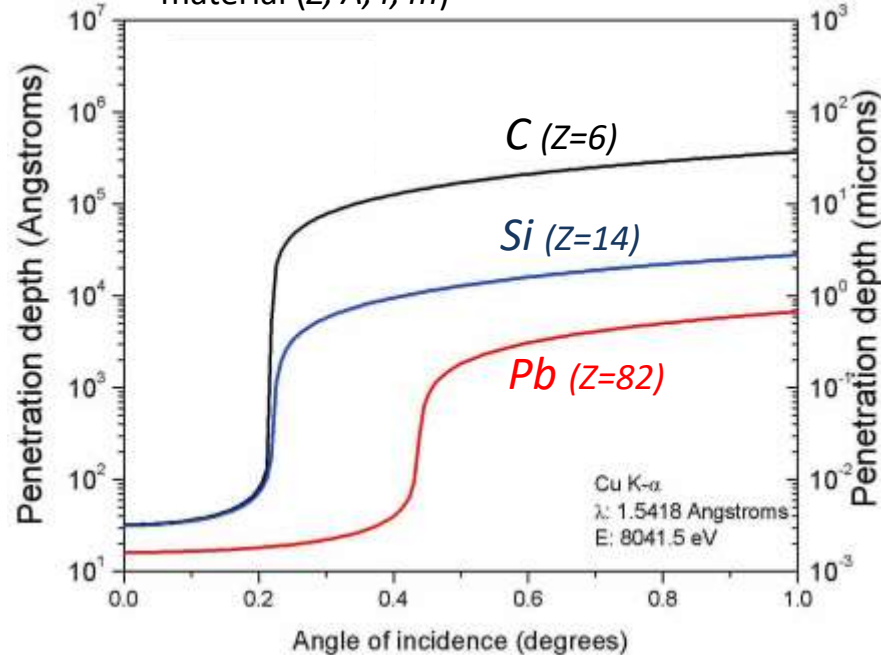
Glancing incidence x-ray diffraction (GI-XRD)



- Enhances intensities from **surface, near surface** regions.
- Phases and grain orientations in **multiple directions** also not parallel to the surface (2θ only scan).
- Change ω to probe different depth ("**depth profiling**")
- Sample height (z) critical: use **parallel beam configuration**.

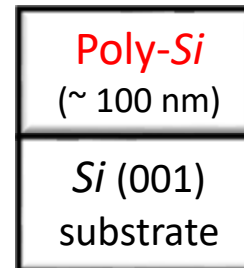
X-ray penetration depth:

Type of radiation, angle of incidence, material (Z , A , r , m)

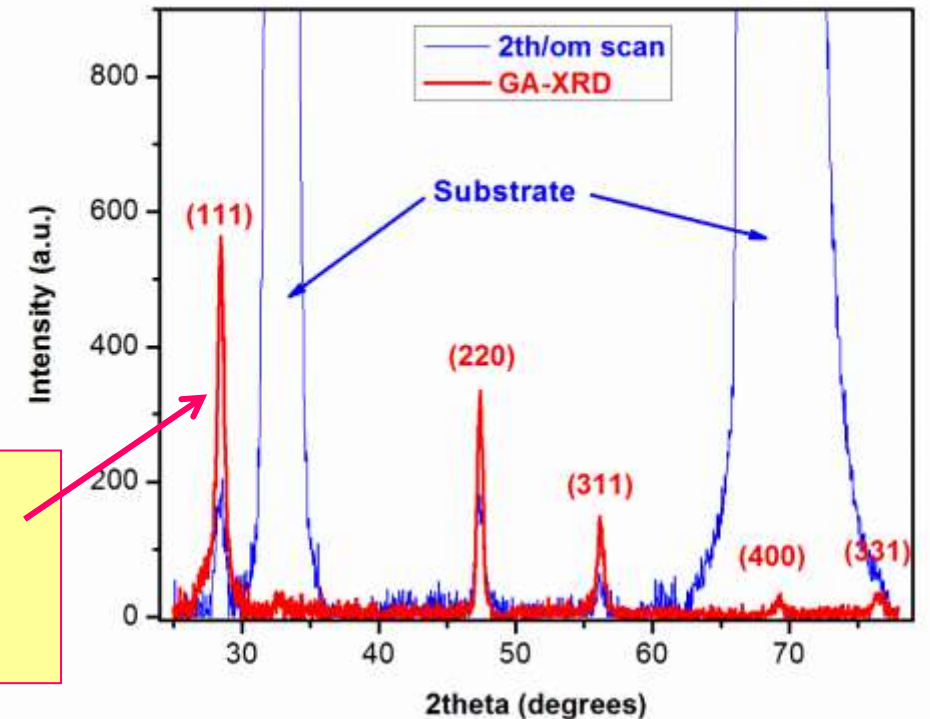


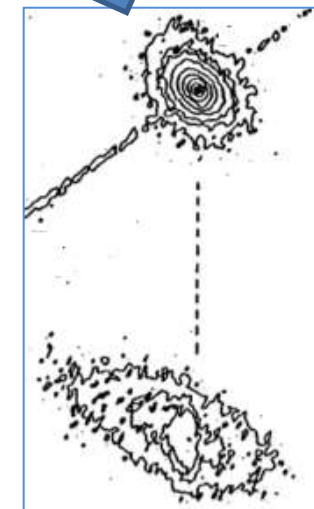
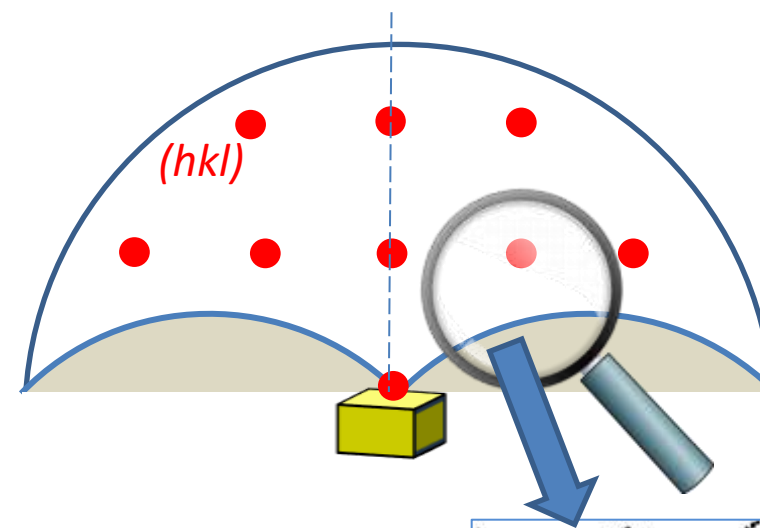
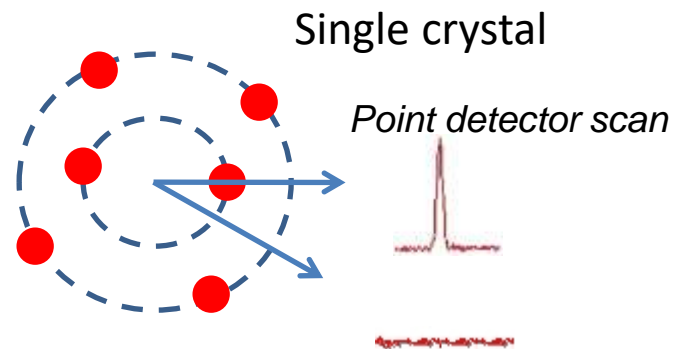
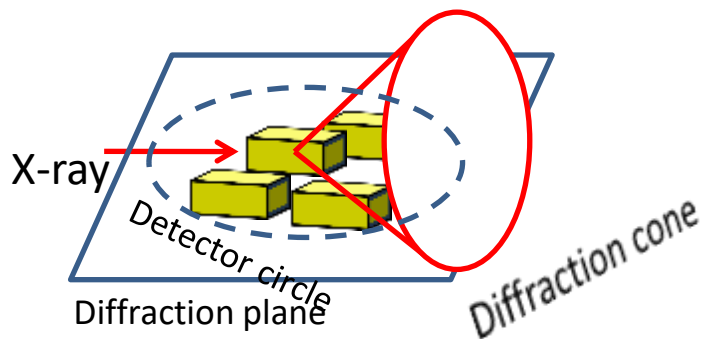
Example:

Poly-Si gate in CMOS

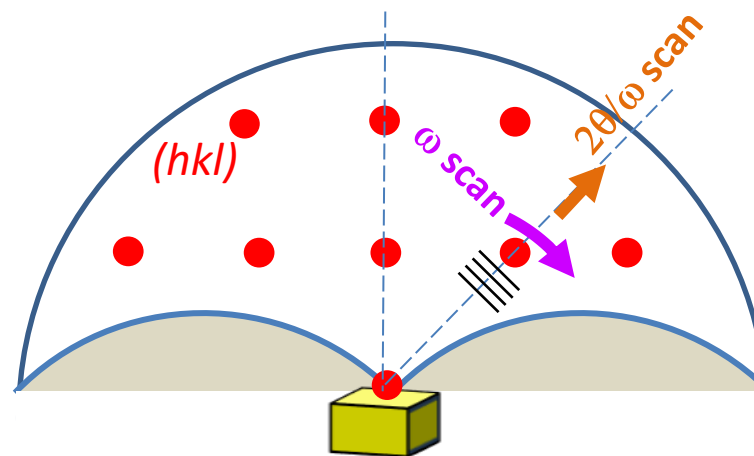


GI-XRD:
more accurate
phase id, texture and
grain size analysis

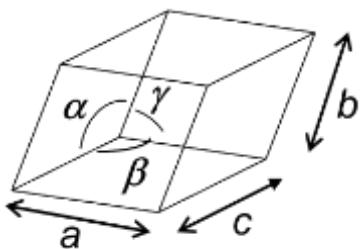




Multiple RLP's
(Reciprocal Lattice Points)
Relative position
Orientation
Shape

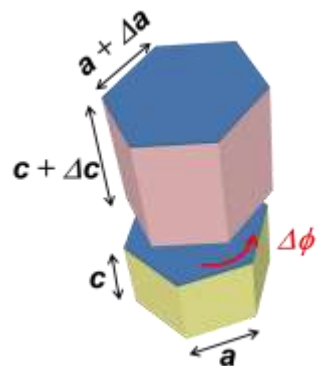


Single crystals



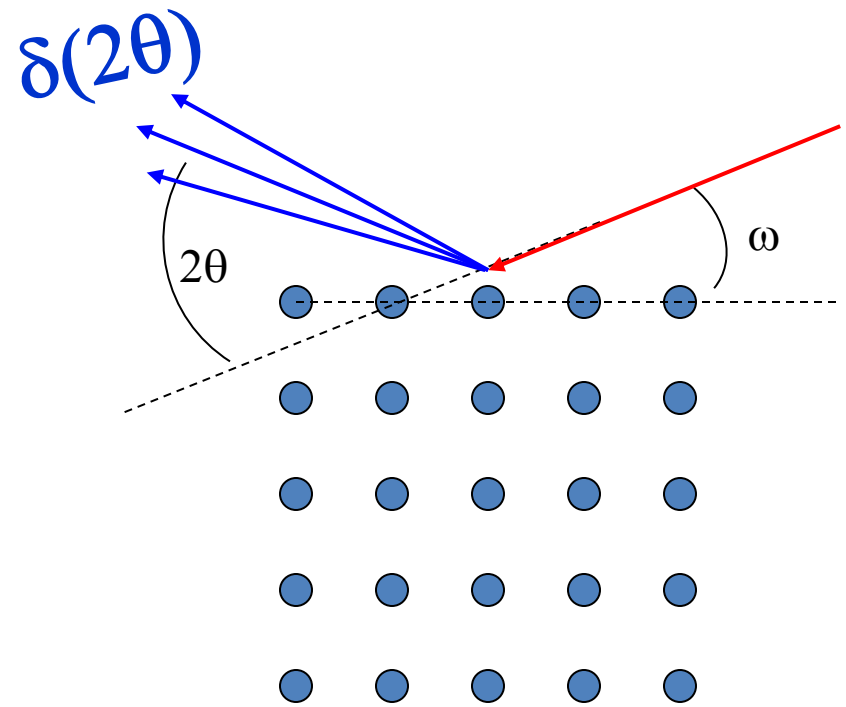
- Accurate lattice parameter measurements.
- Accurate peak shape analysis: defects, mosaicity.

Epitaxial thin films on substrates



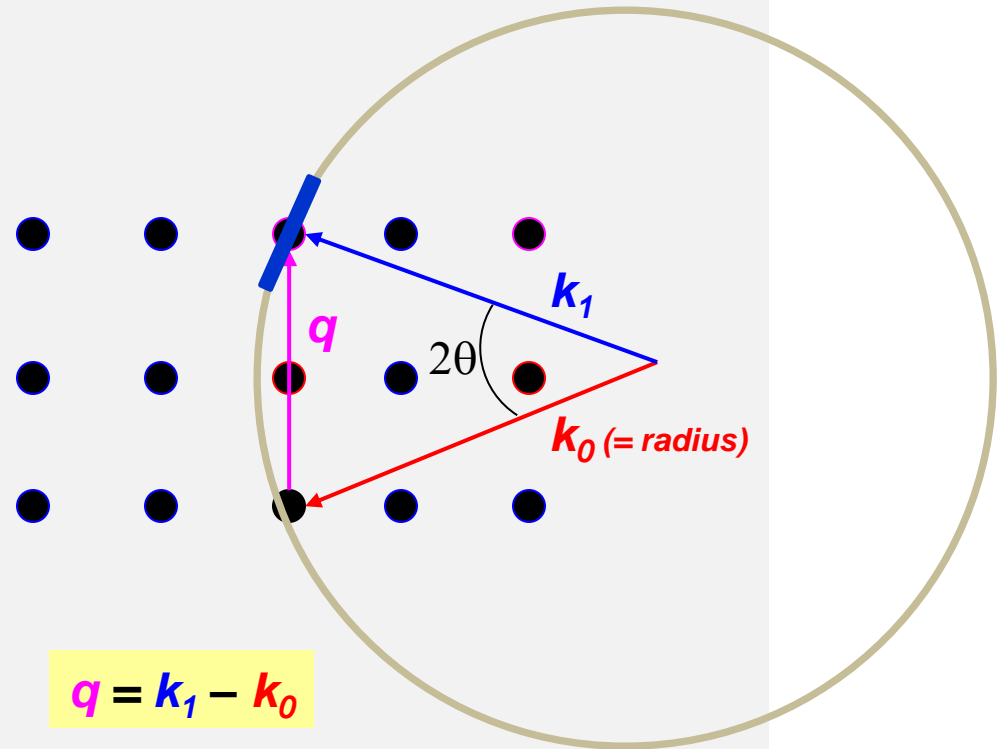
- Measure small lattice distortions (Δa , $\Delta c \sim 10^{-5}$).
- Layer tilts $\Delta\phi$
- Accurate peak shape analysis: defects, strain, mosaicity

“Real” space

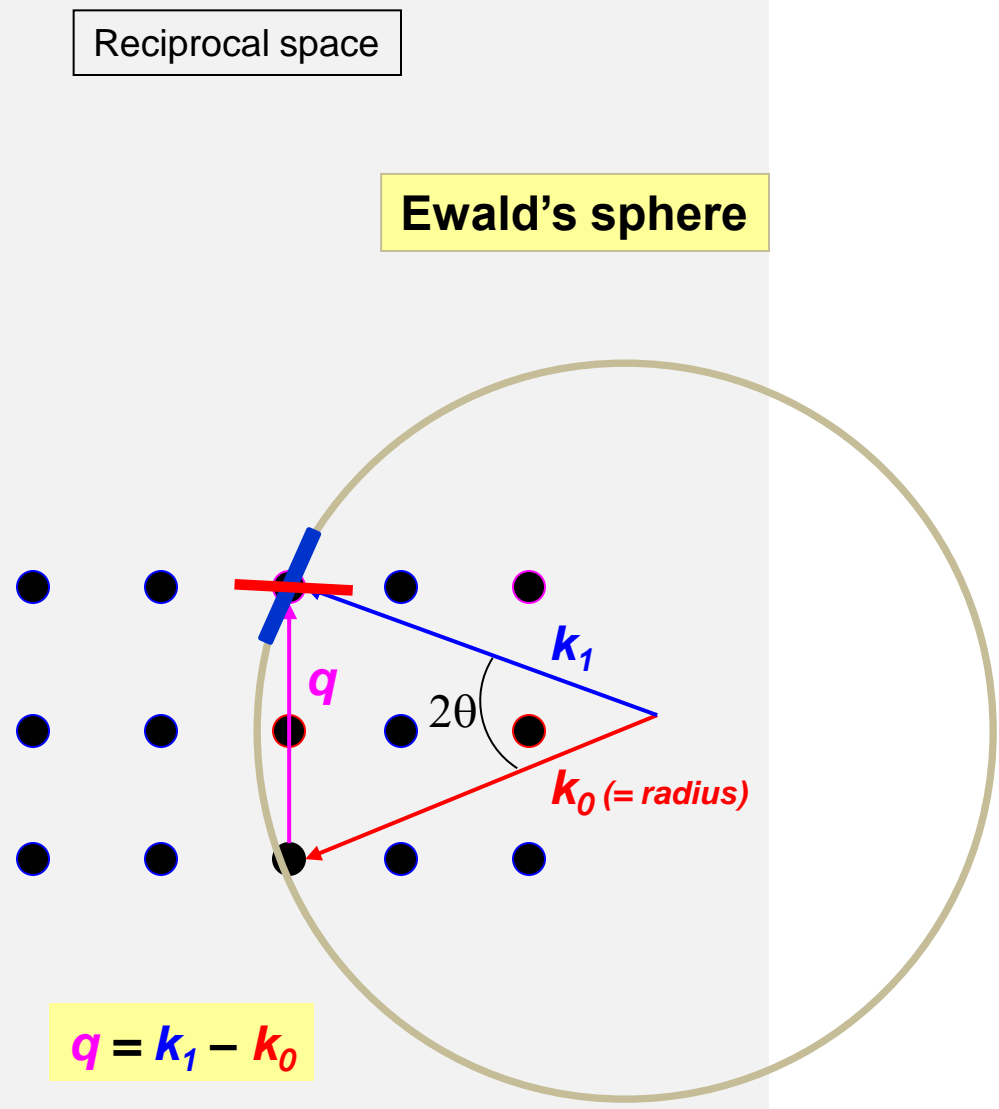
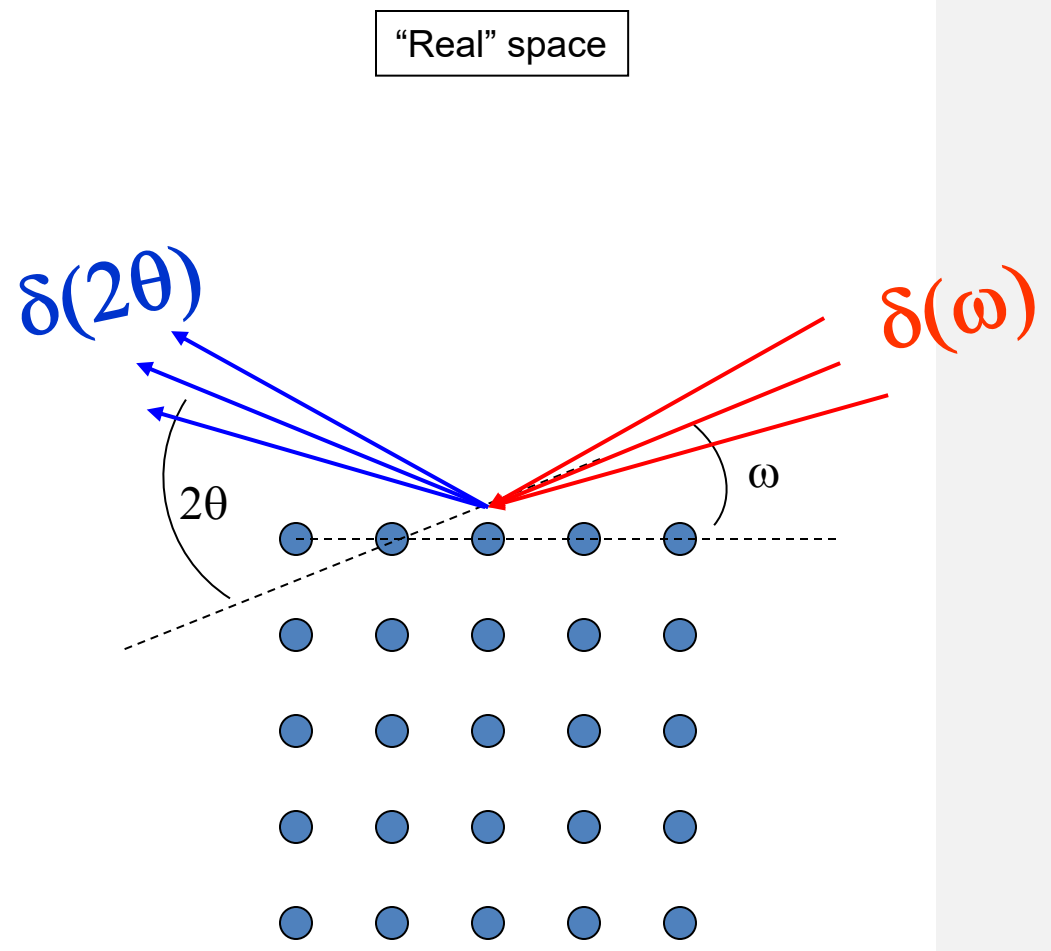


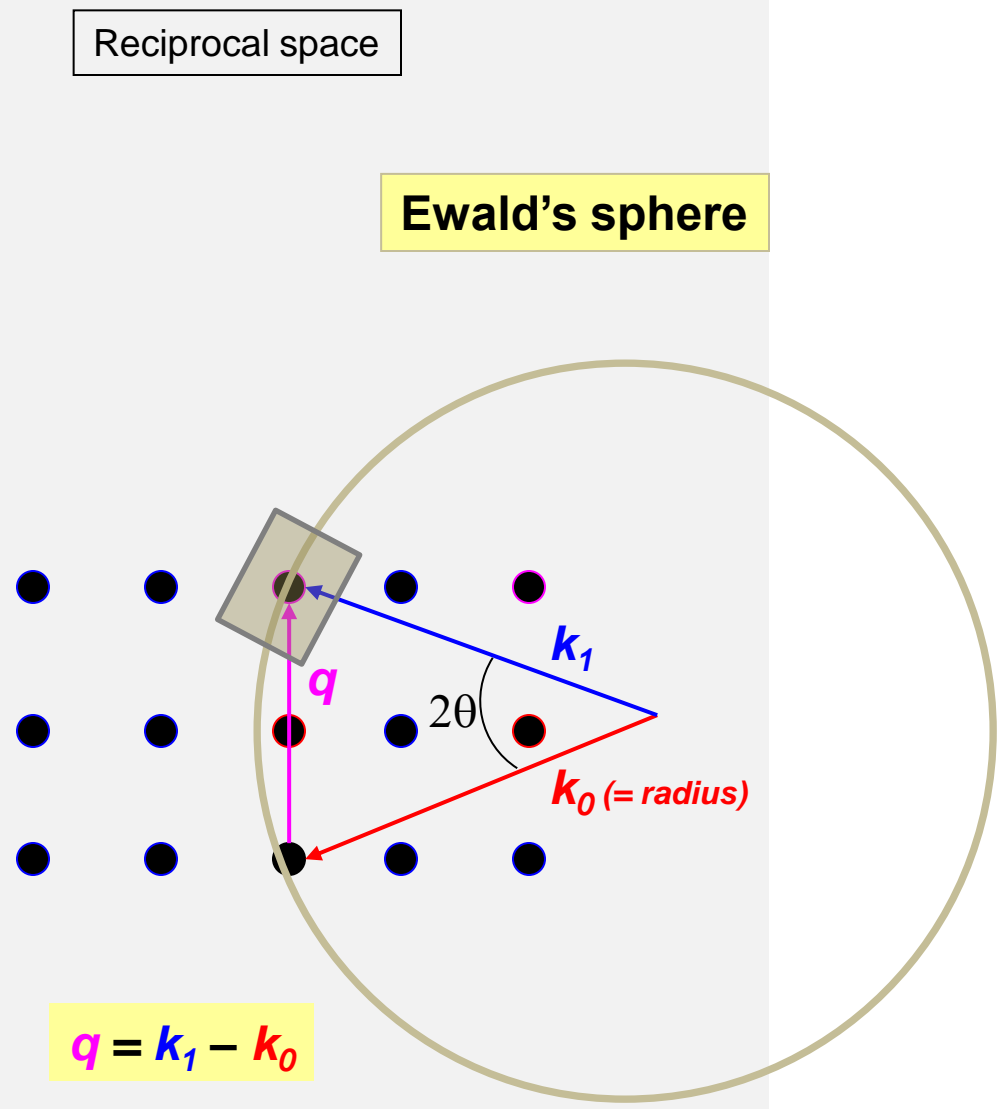
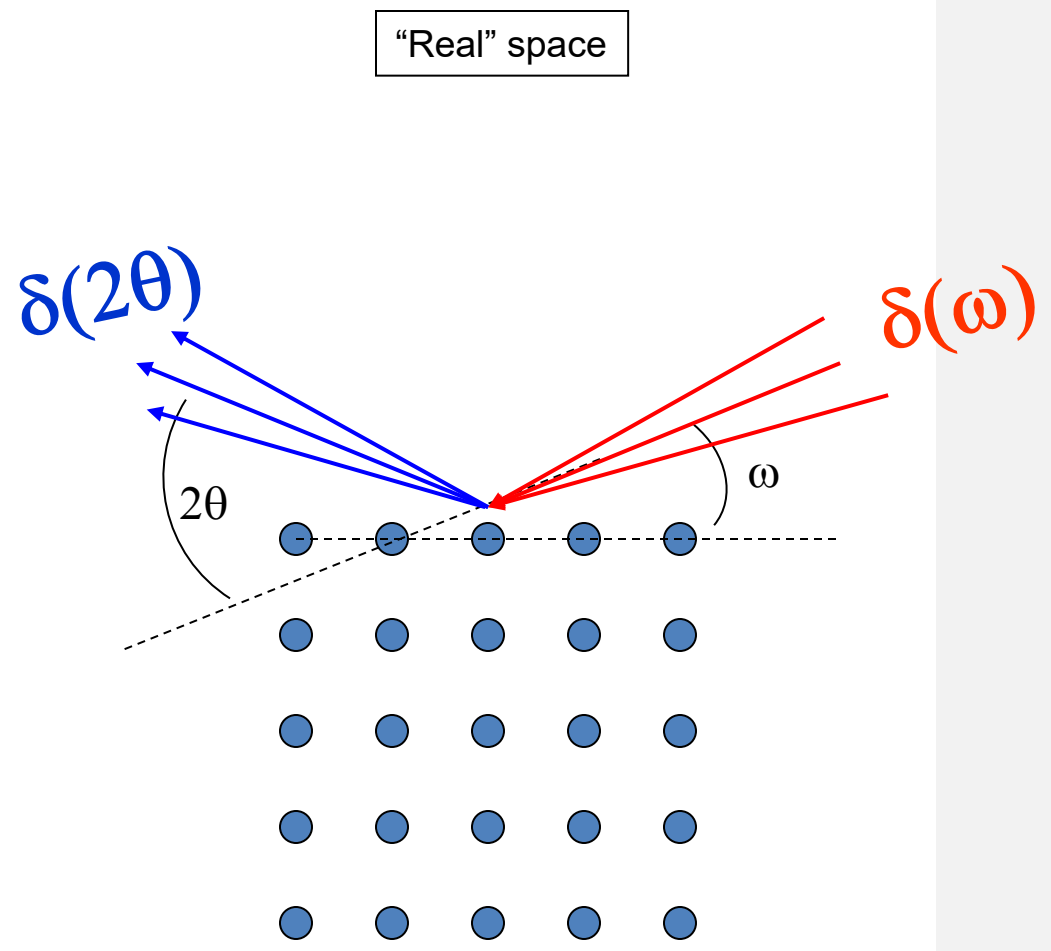
Reciprocal space

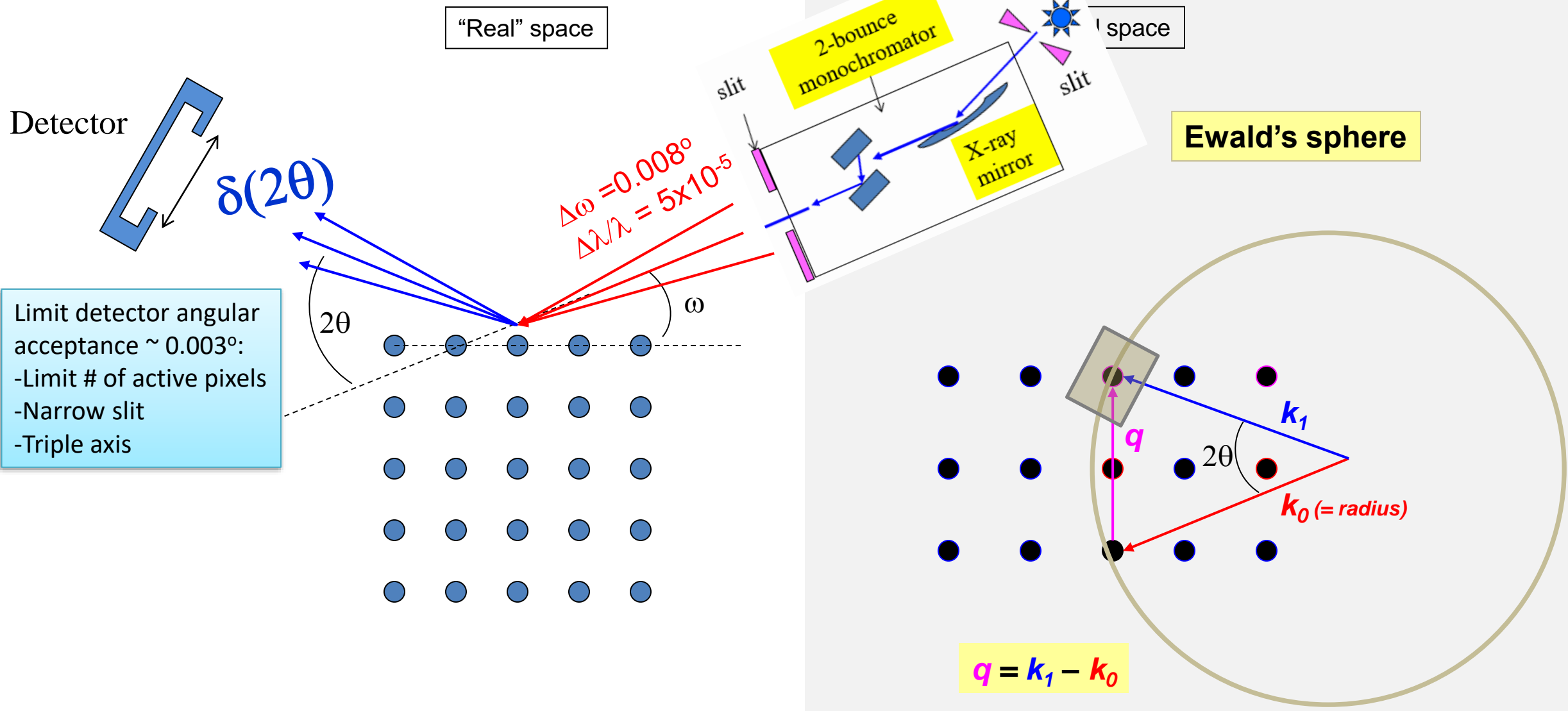
Ewald's sphere



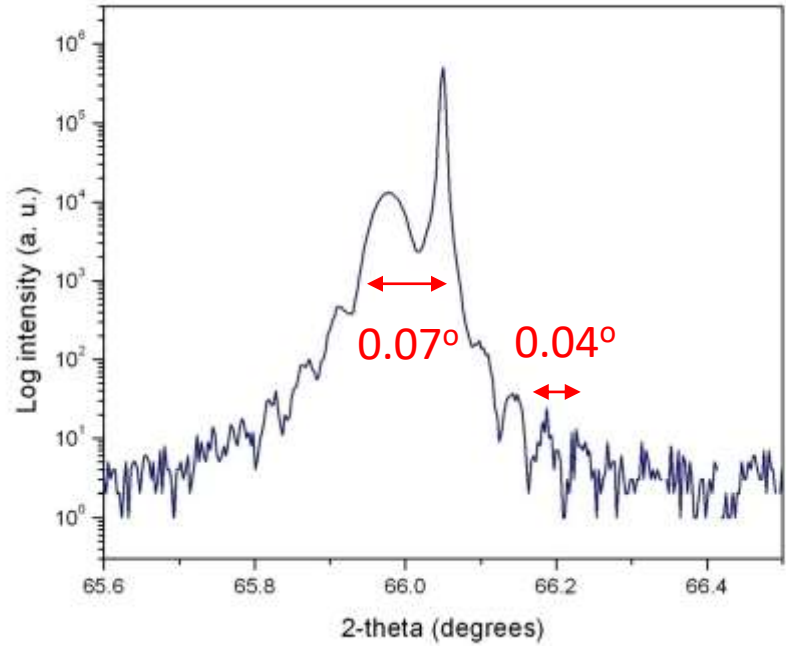
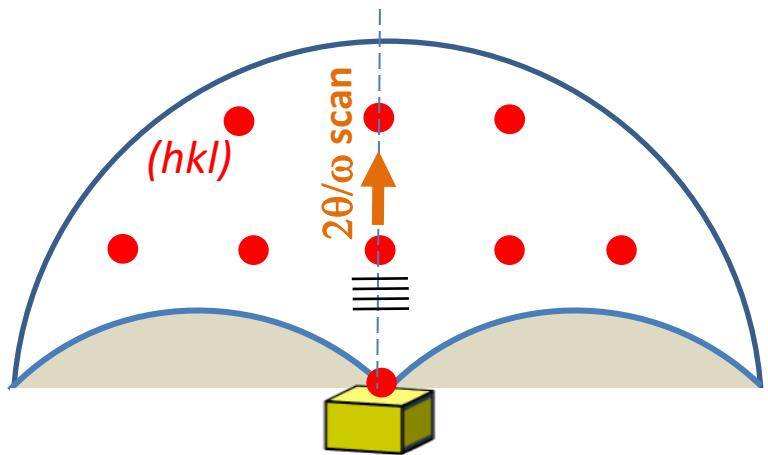
$$q = k_1 - k_0$$







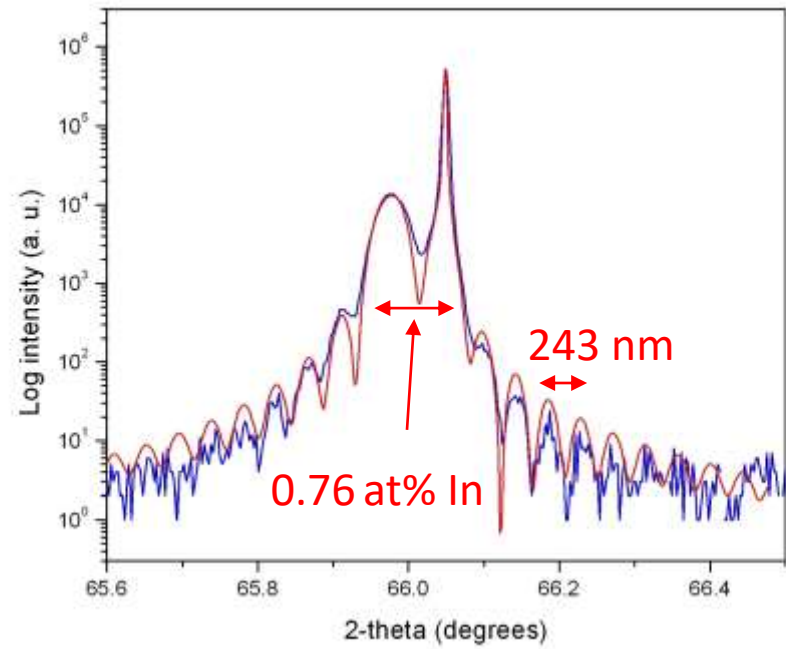
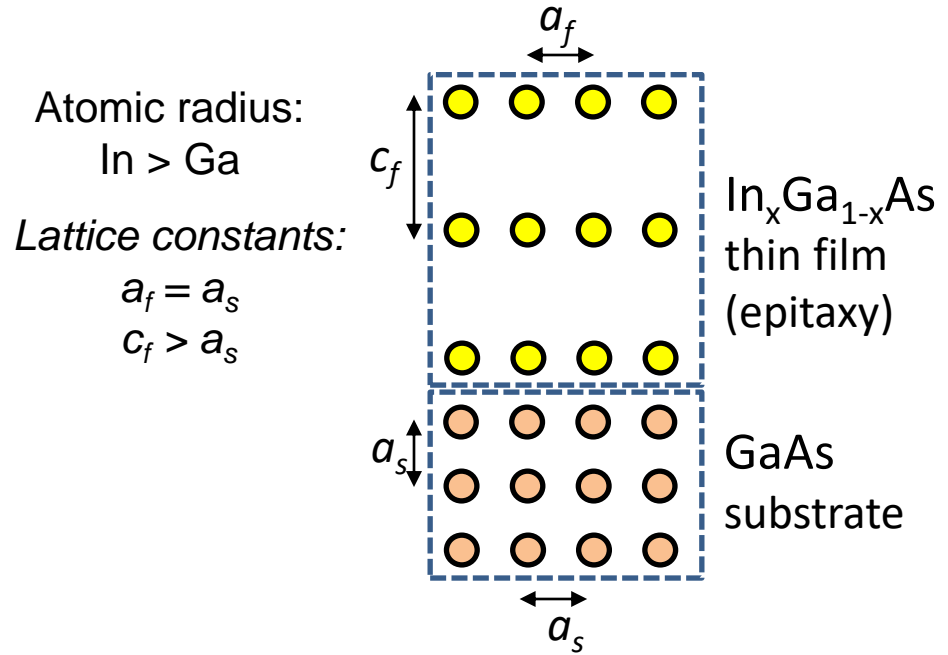
High-resolution x-ray diffraction (HR-XRD)



HR-XRD 2θ/ω scan near GaAs(004)

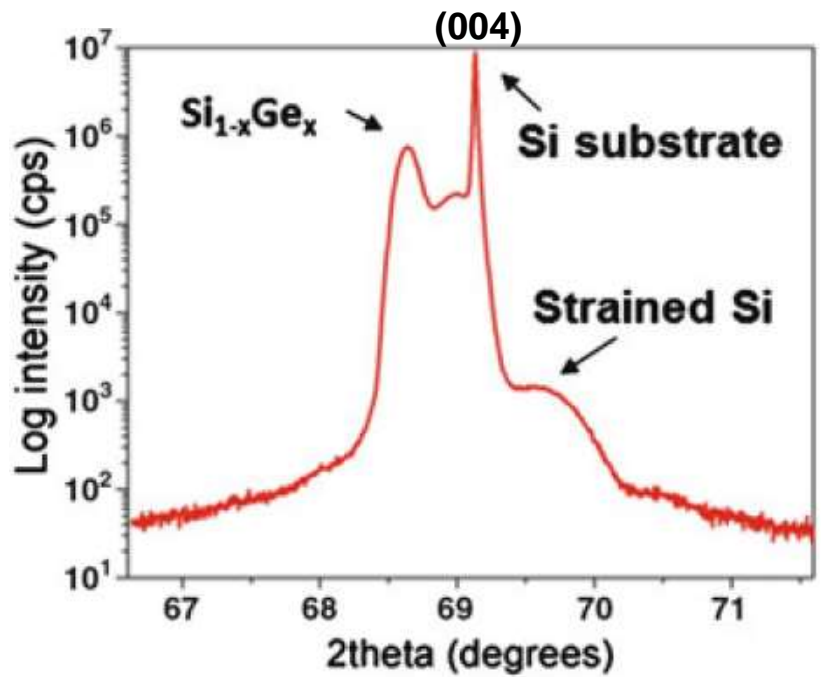
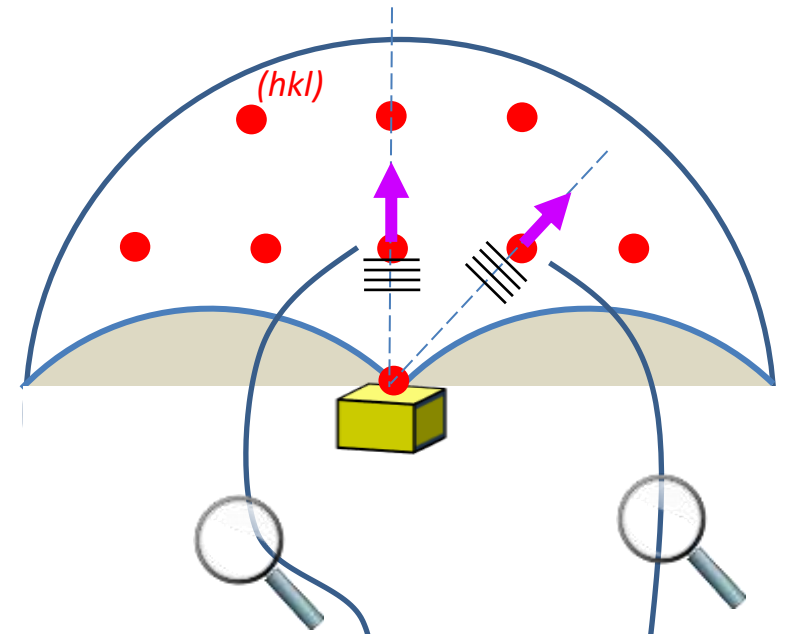
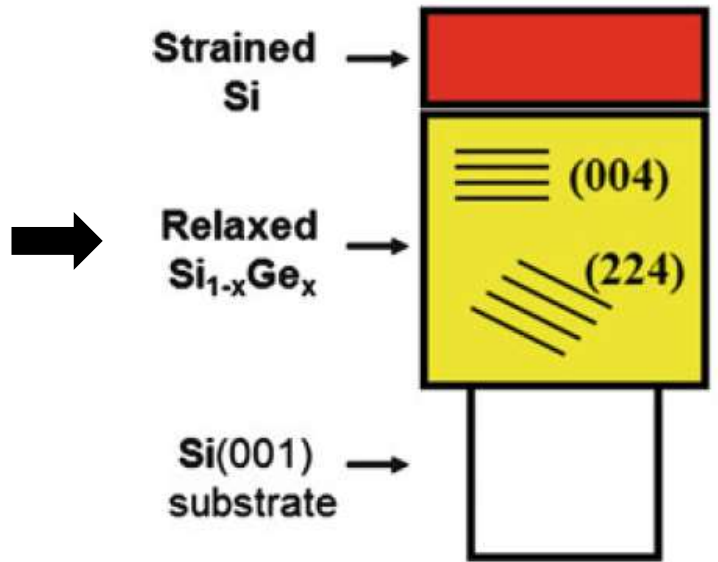
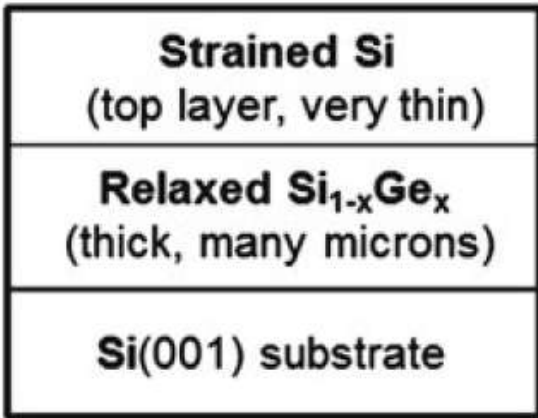
$$\frac{\Delta a}{a} = \frac{\sin \theta(\text{substrate})}{\sin \theta(\text{film})} - 1$$

$$\text{Thickness} = \frac{\lambda}{2 \Delta \theta \cos \theta}$$

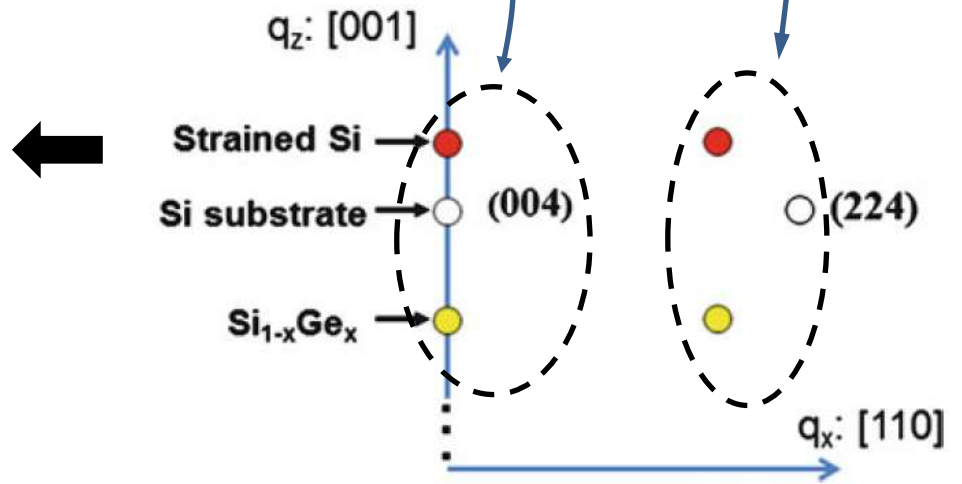


Takagi-Taupin dynamical scattering simulation

Reciprocal space mapping RSM (reciprocal lattice mapping RLM)

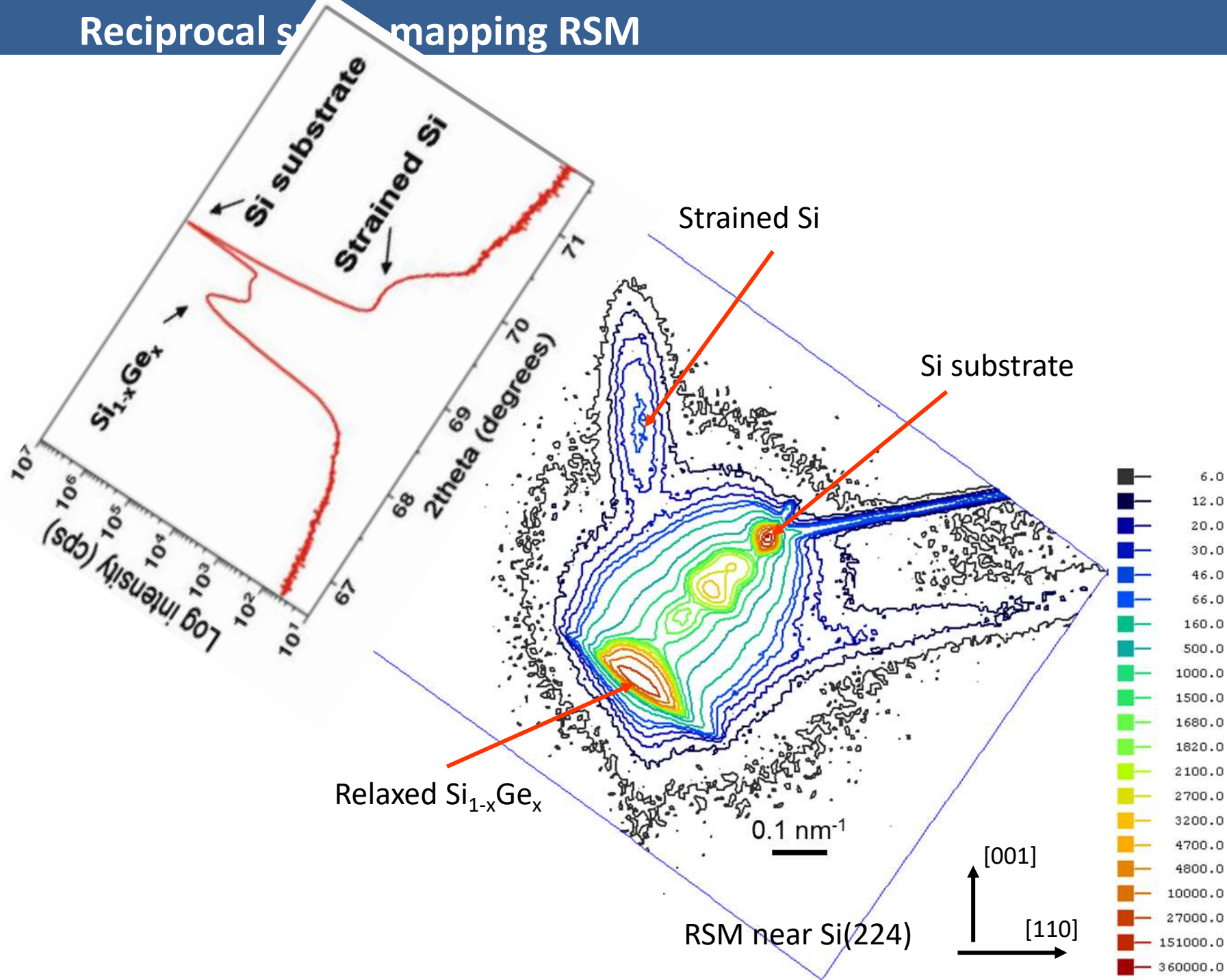
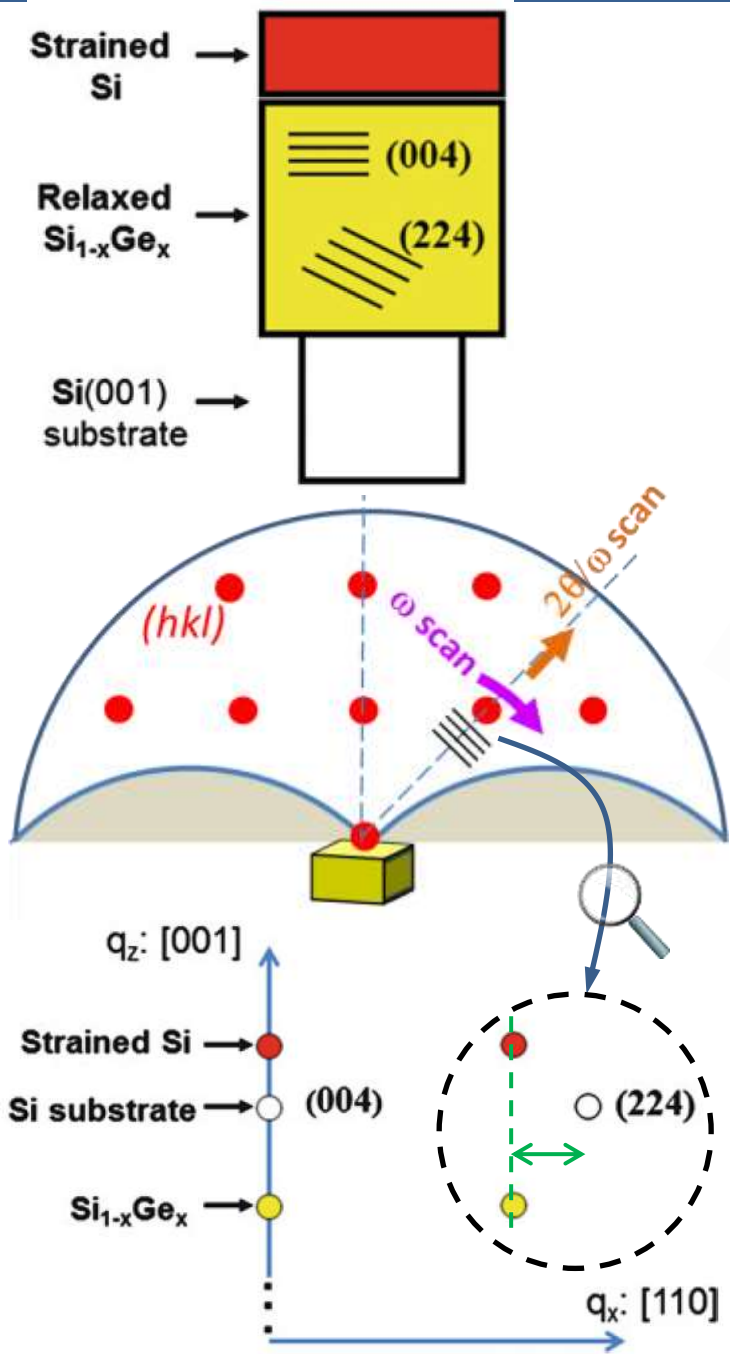


In-plane lattice constants?
Strain relaxation?
Broad peaks?



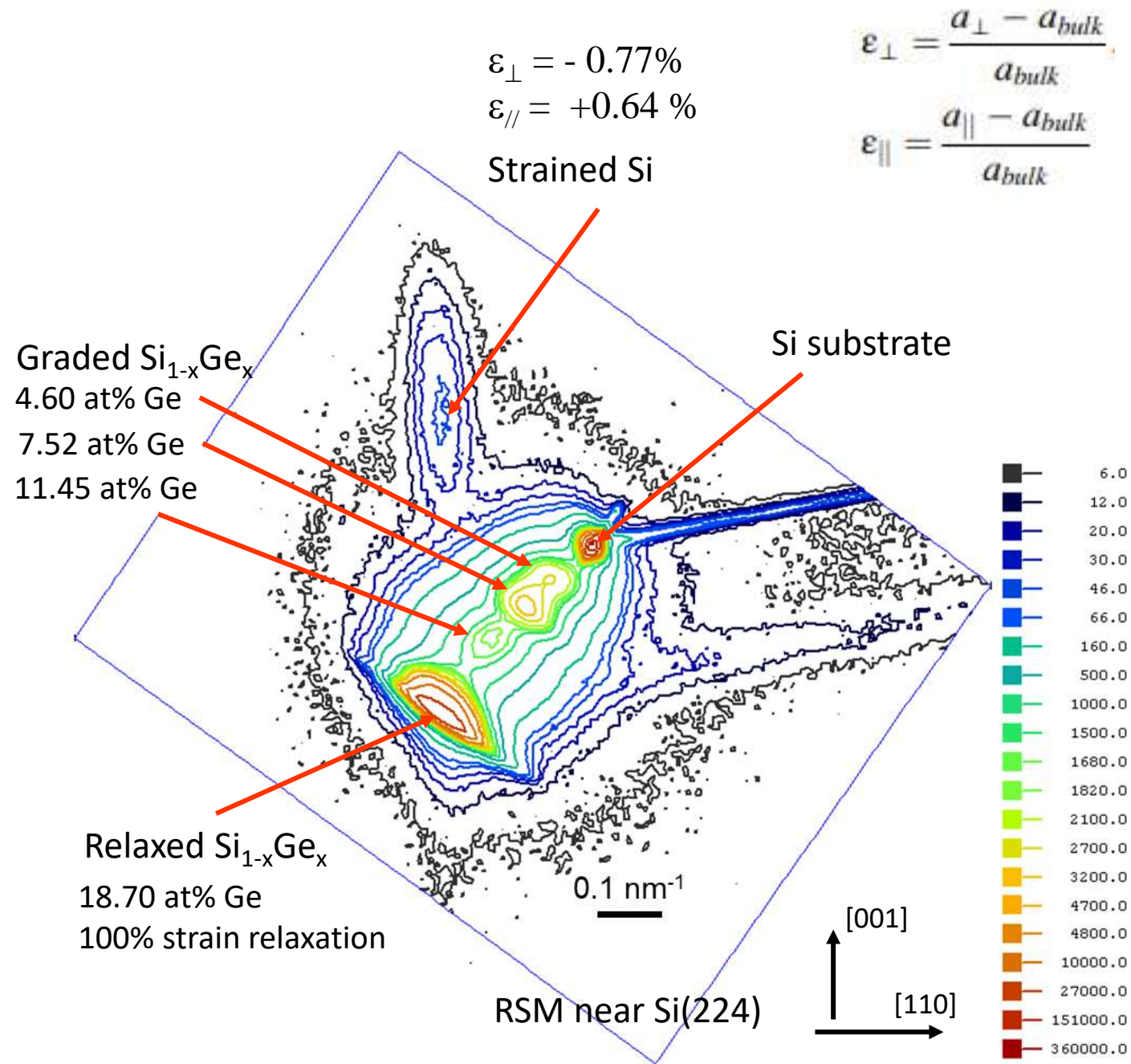
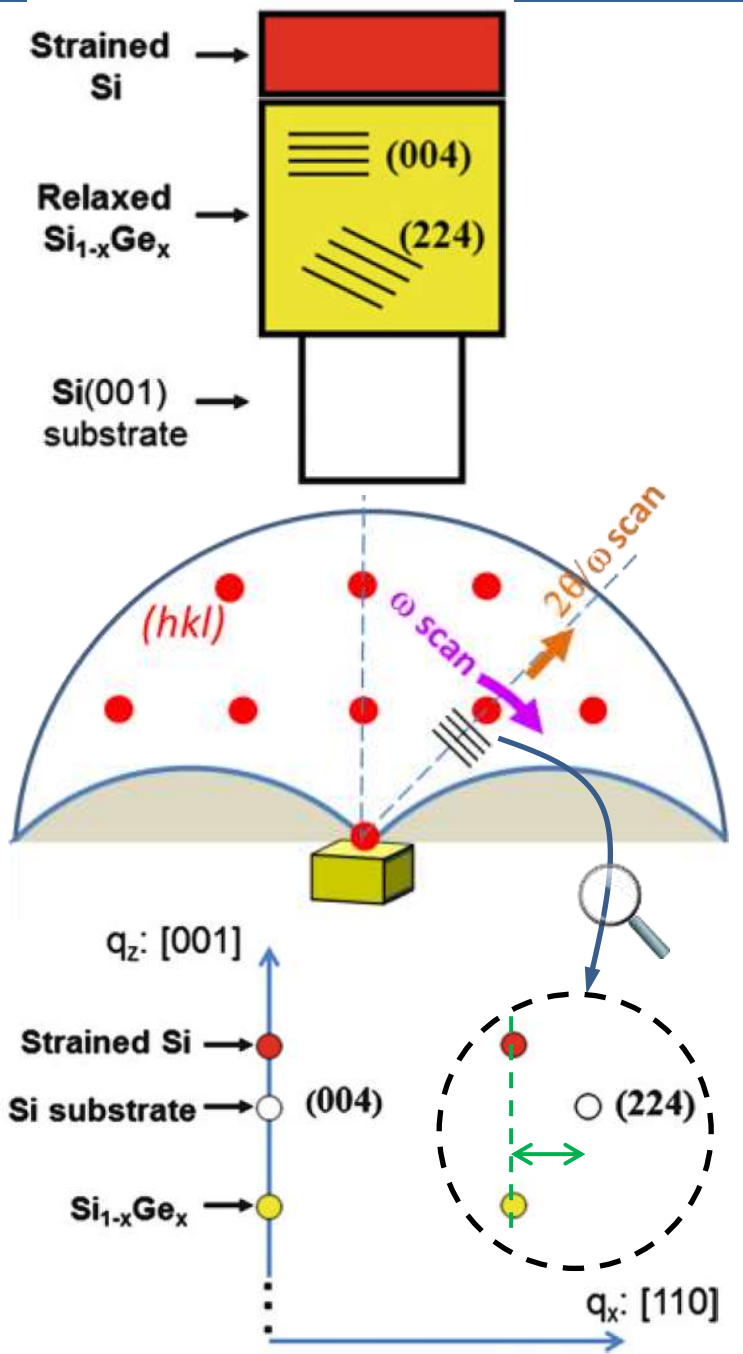
I

Reciprocal space mapping RSM



I

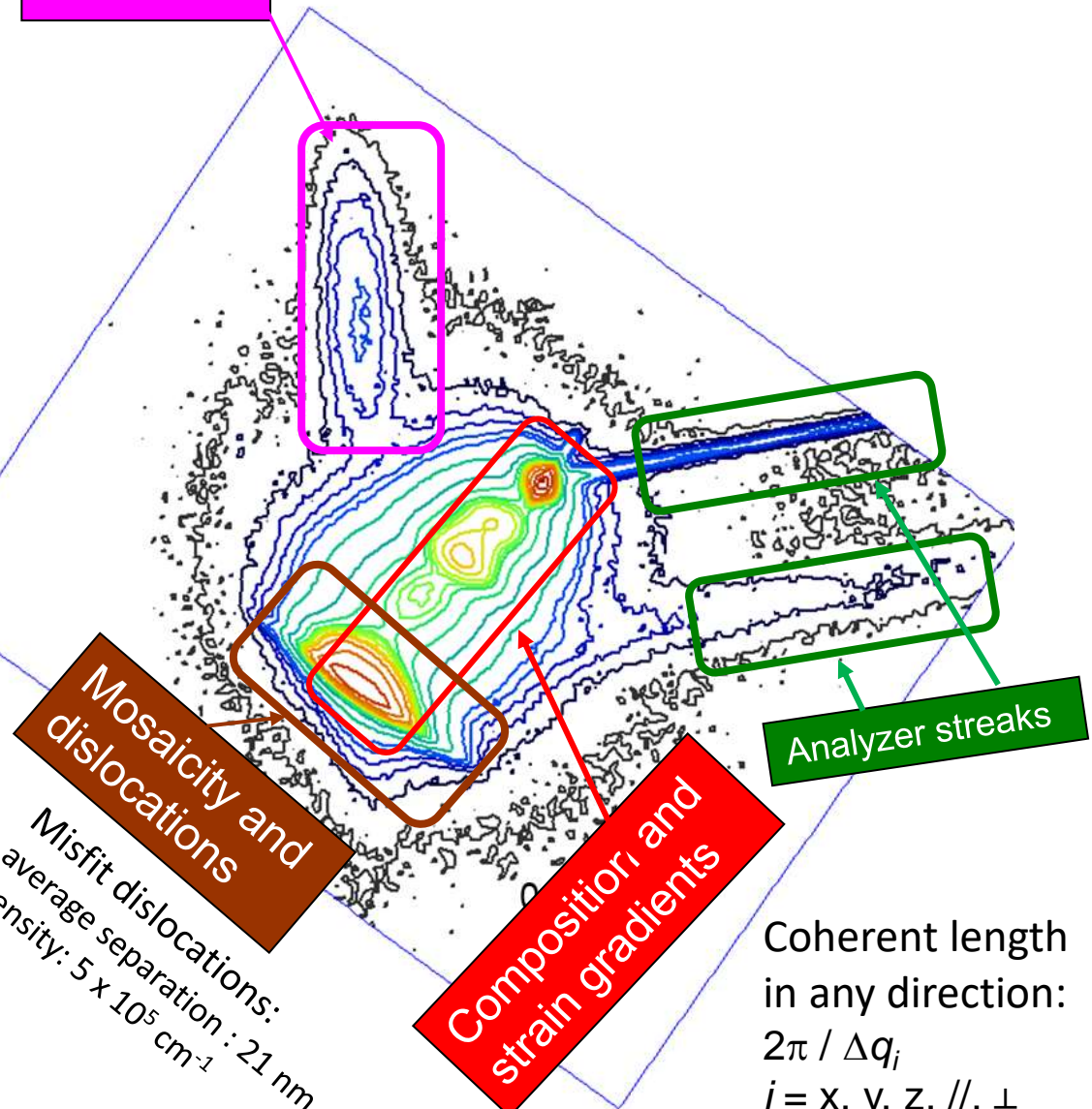
Reciprocal space mapping RSM: peak position



Reciprocal space mapping RSM: peak shape

Vertical coherent length: 14 nm

Finite size



$$\epsilon_{\perp} = -0.77\%$$

$$\epsilon_{//} = +0.64\%$$

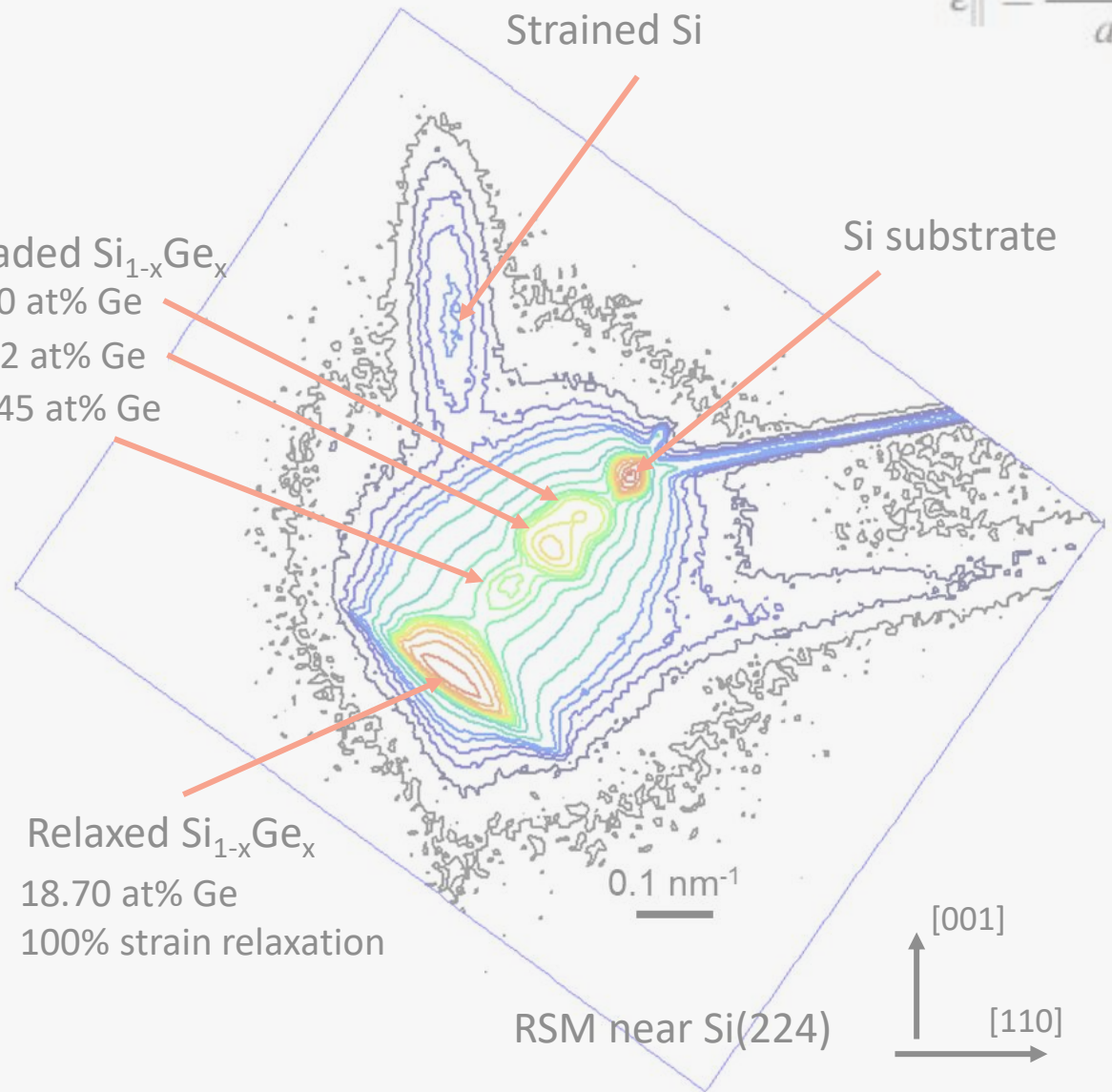
$$\epsilon_{\perp} = \frac{a_{\perp} - a_{bulk}}{a_{bulk}}$$

$$\epsilon_{//} = \frac{a_{//} - a_{bulk}}{a_{bulk}}$$

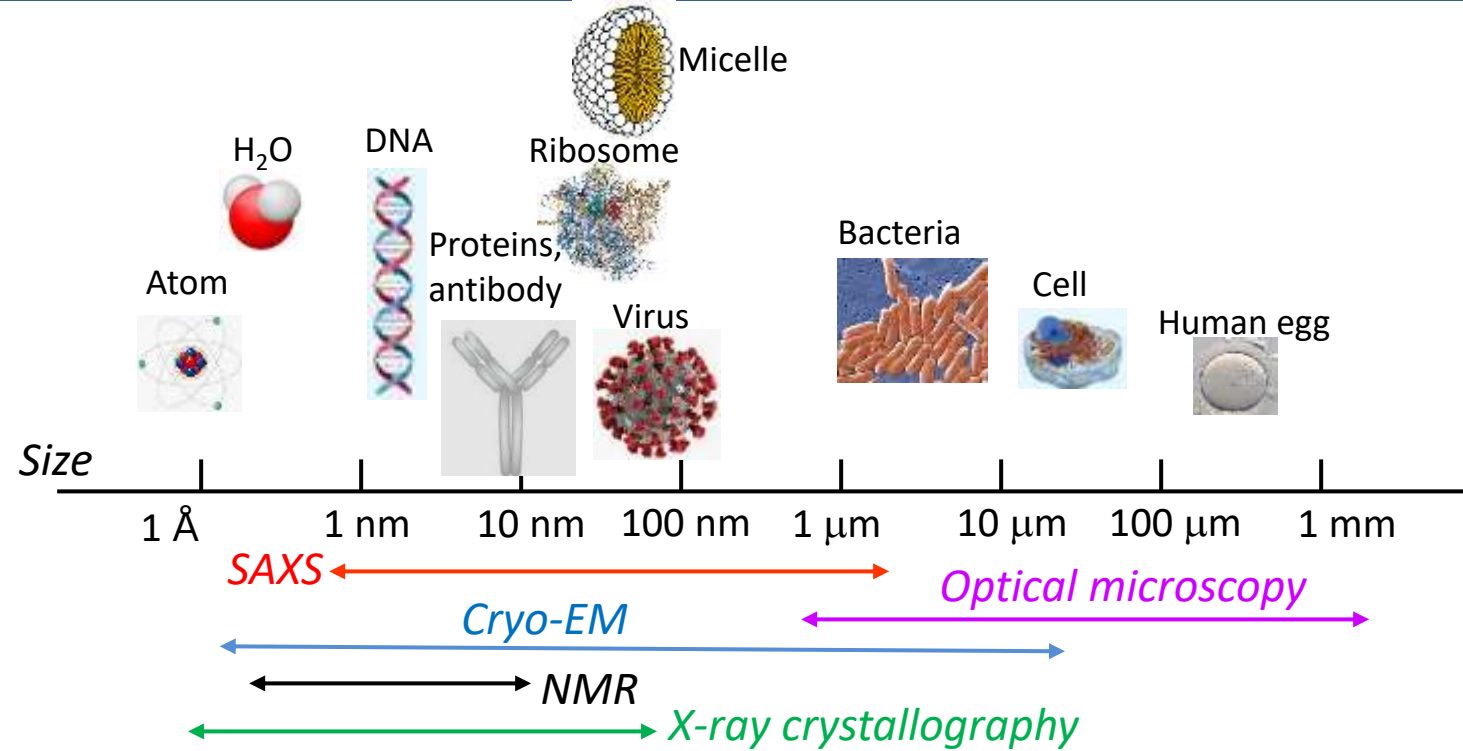
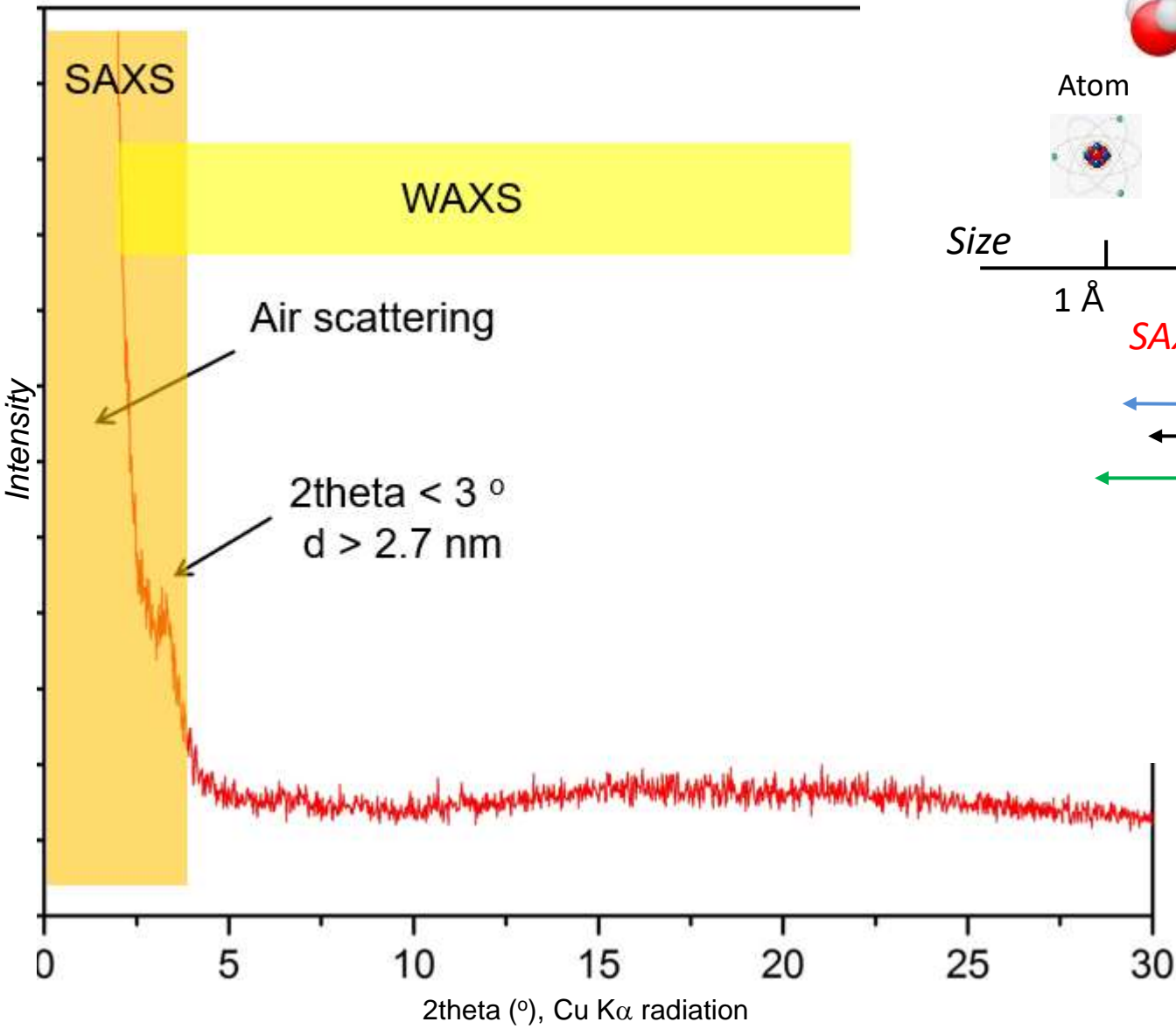
Strained Si

Graded $\text{Si}_{1-x}\text{Ge}_x$
4.60 at% Ge
7.52 at% Ge
11.45 at% Ge

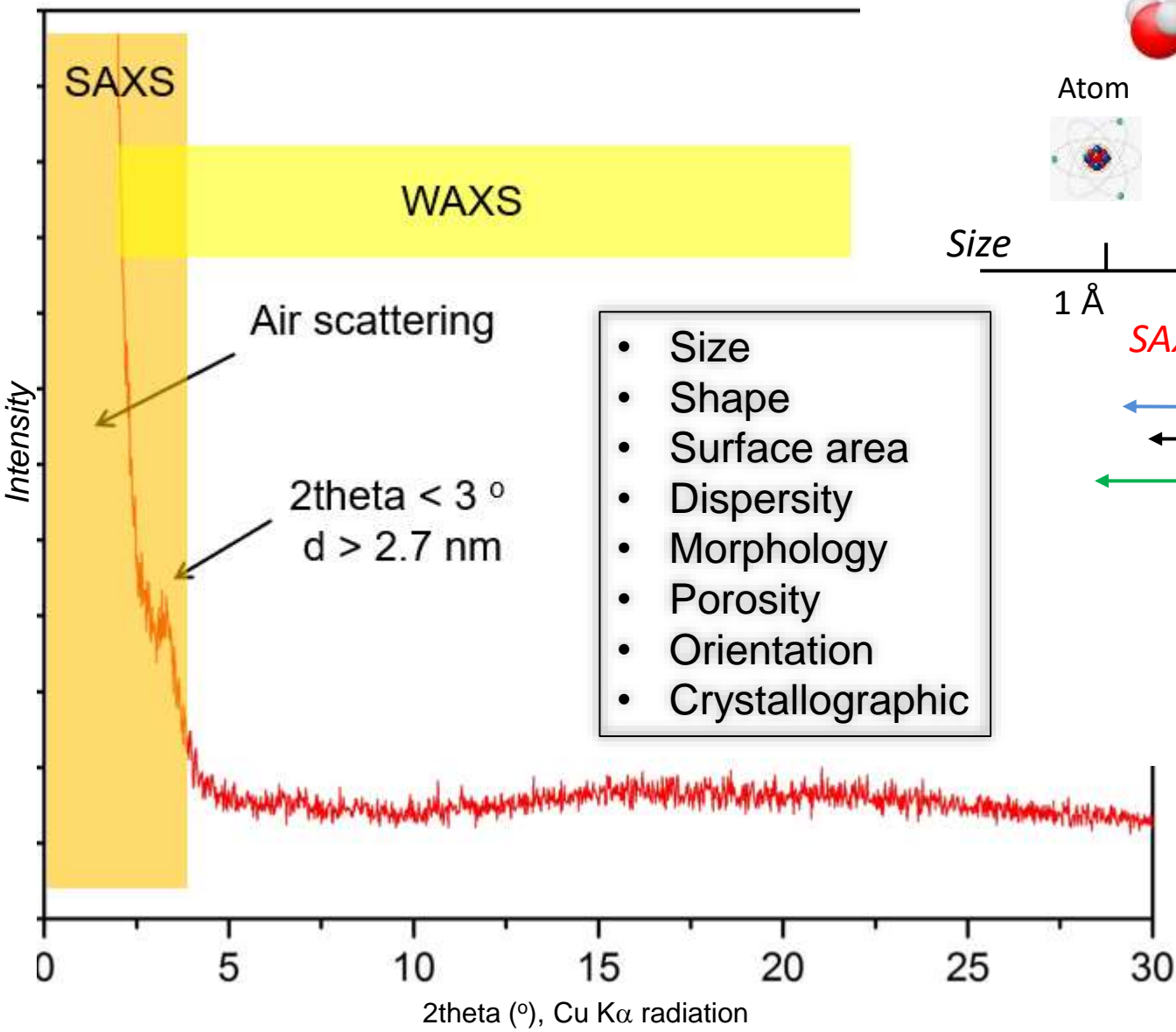
Si substrate



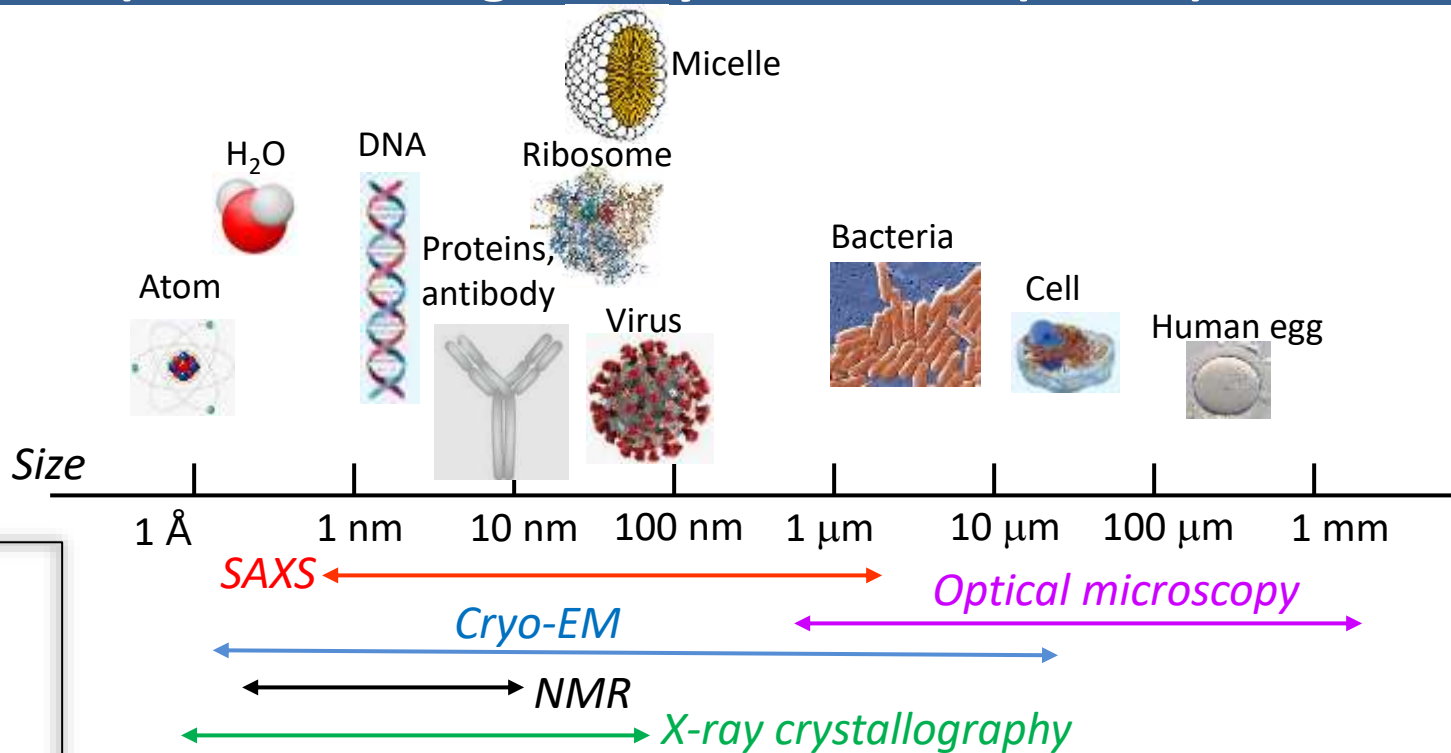
Small angles... large things...



Small angles... large things...



- Size
- Shape
- Surface area
- Dispersity
- Morphology
- Porosity
- Orientation
- Crystallographic



Large feature sizes: very low scattering angles

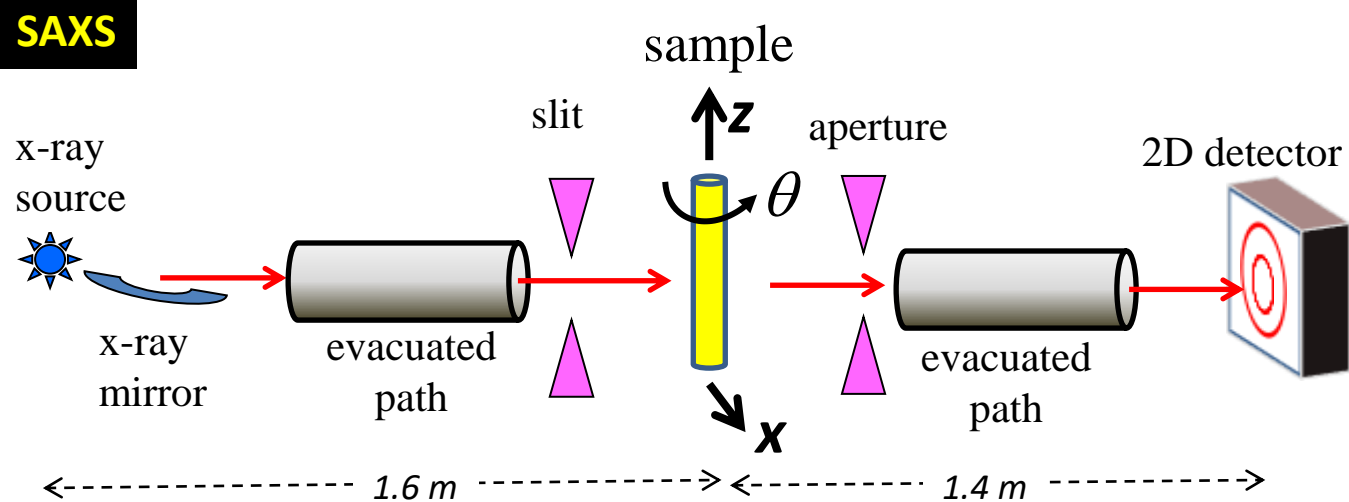
Air scattering at low scattering angles

Low scattering intensities. Subtle features in data.

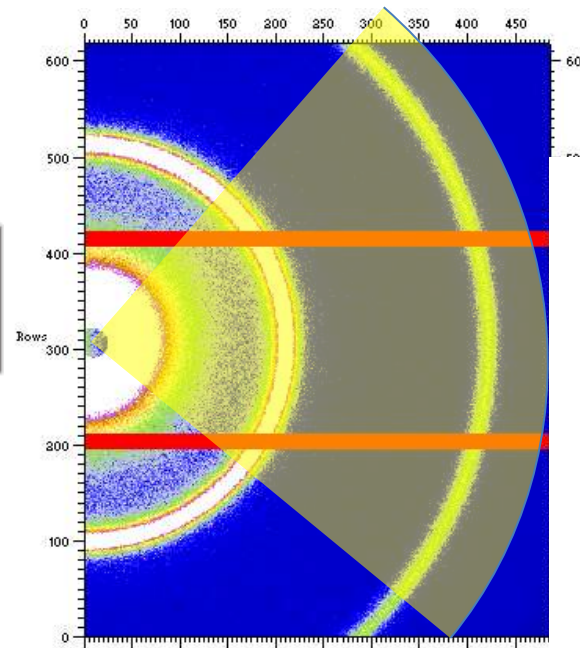
Contrary to hard materials, soft materials may be damaged by the x-ray radiation: need fast data collection

SAXS and WAXS configurations

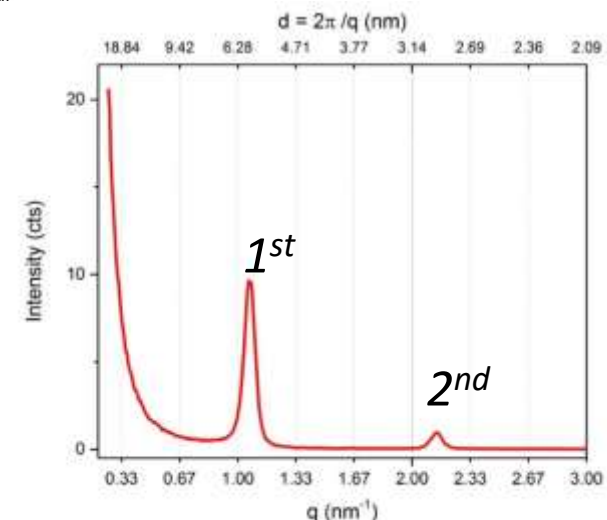
SAXS



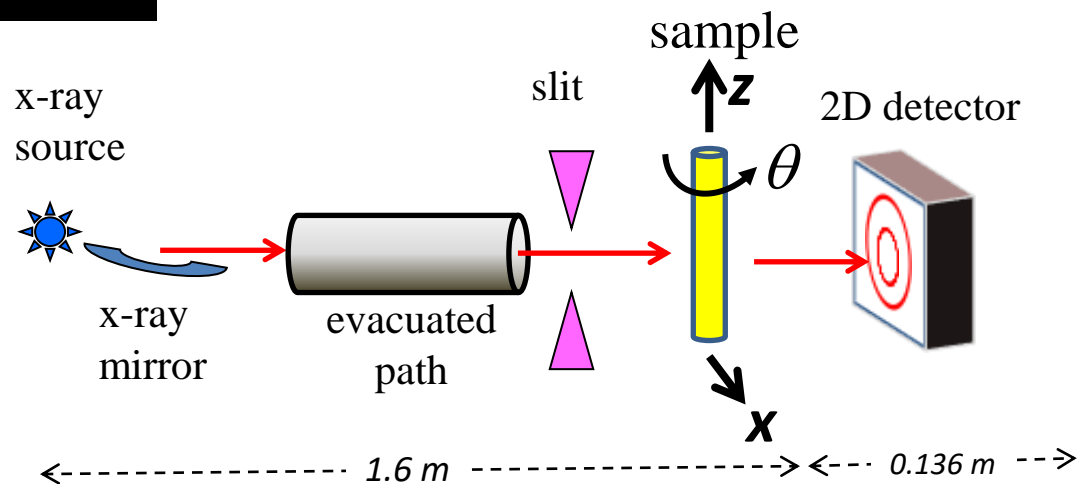
$$q \sim 0.3 - 3 \text{ nm}^{-1}, d \sim 24 - 4 \text{ nm}$$

Silver behenate $\text{AgC}_{22}\text{H}_{43}\text{O}$

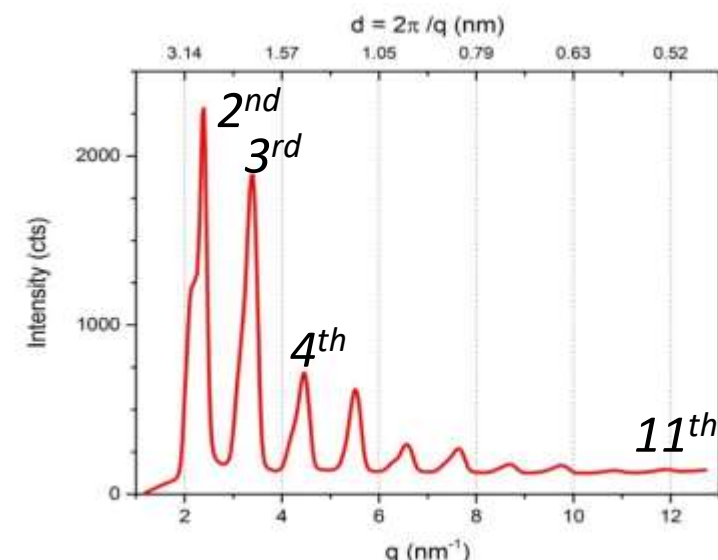
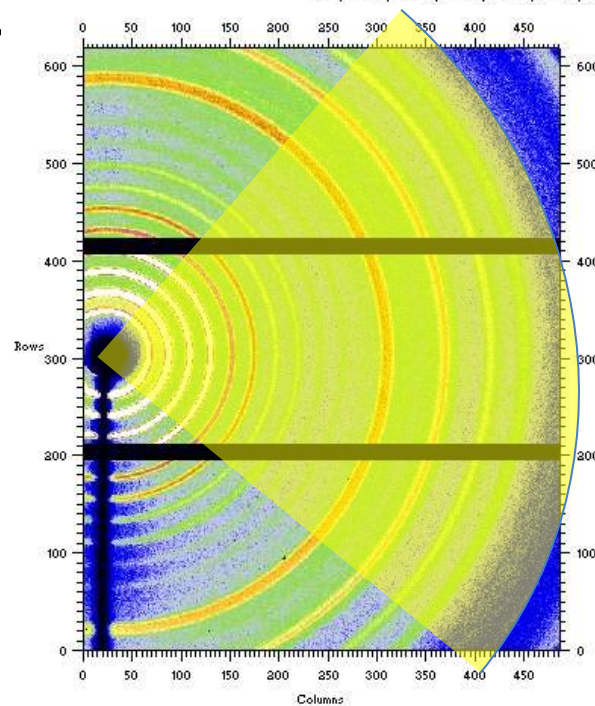
$$\frac{q_n}{q_1} = 1, 2, 3, 4 \dots (\text{lamella})$$



WAXS



$$q \sim 1.3 - 13 \text{ nm}^{-1}, d \sim 5 - 0.5 \text{ nm}$$



Typical SAXS data ranges

The slope in a graph of $\ln(I)$ vs. Q^2 gives the **radius of gyration** (R_g) (effective size of the scattering particle, ex. a polymer chain, micelle, domain in a multiphase system, etc.)

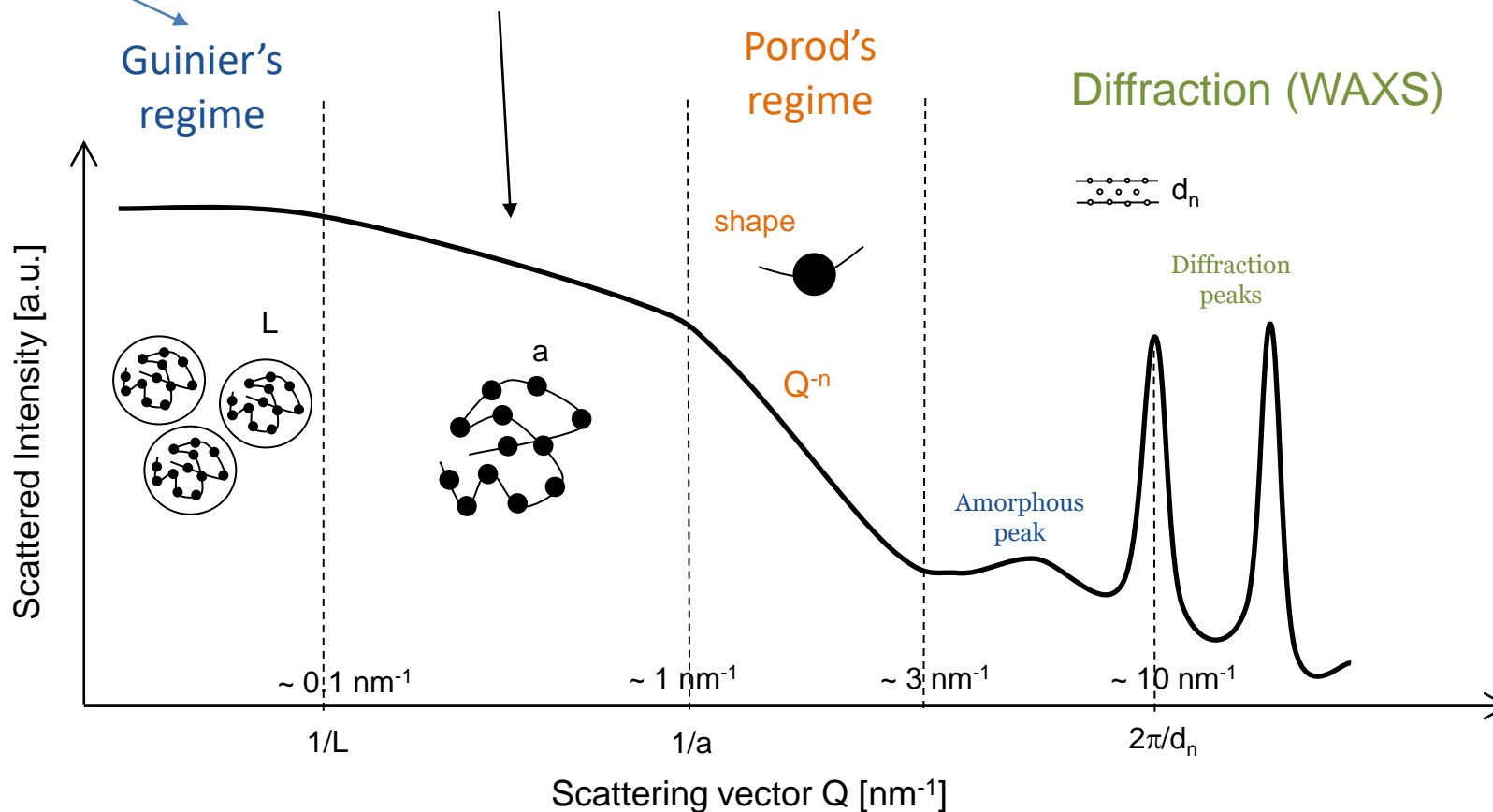
$$I(Q) = I_0 \exp\left(-\frac{Q^2 R_g^2}{3}\right)$$

$$\ln[I(Q)] = \ln[I_0] - \frac{Q^2 R_g^2}{3}$$

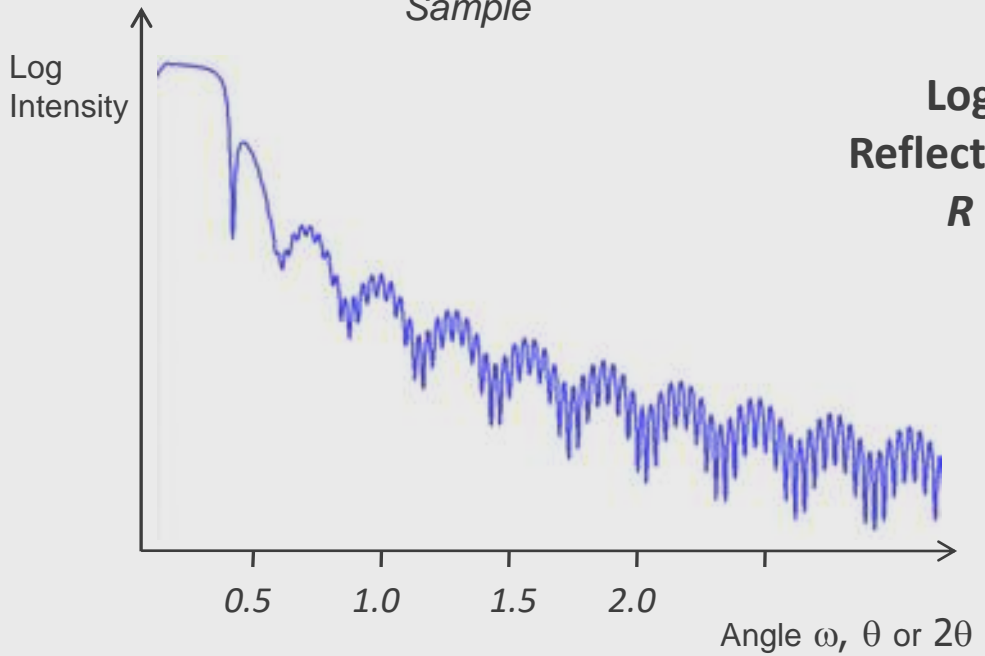
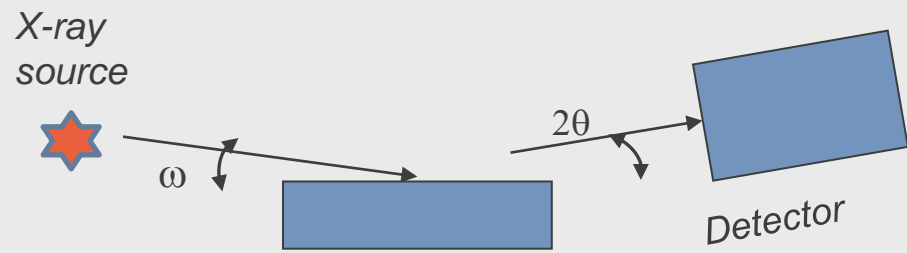
Intermediate range, different dependence on Q (elongated objects)

$$I(Q) = \frac{I(0)}{Q} \exp\left(-\frac{Q^2 R_g^2}{2}\right)$$

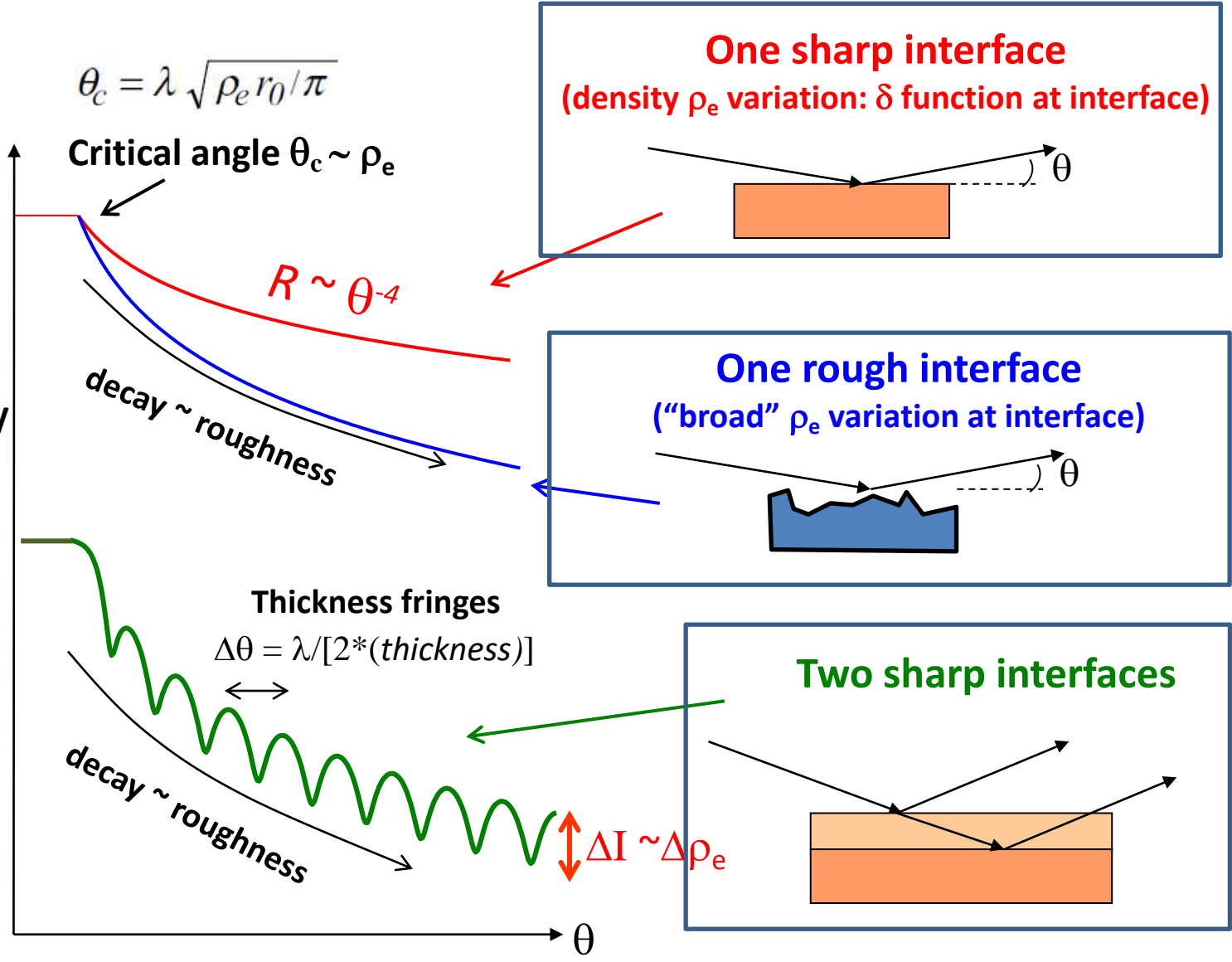
Plot $\text{Log}(I)$ vs $\text{Log}(Q)$, Porod's slope n from Q^n
 n : rigid rods, n : 3-4 rough interfaces of fractal dimension $D = 6 - n$
 n : 4, smooth surface



X-ray reflectivity (XRR)

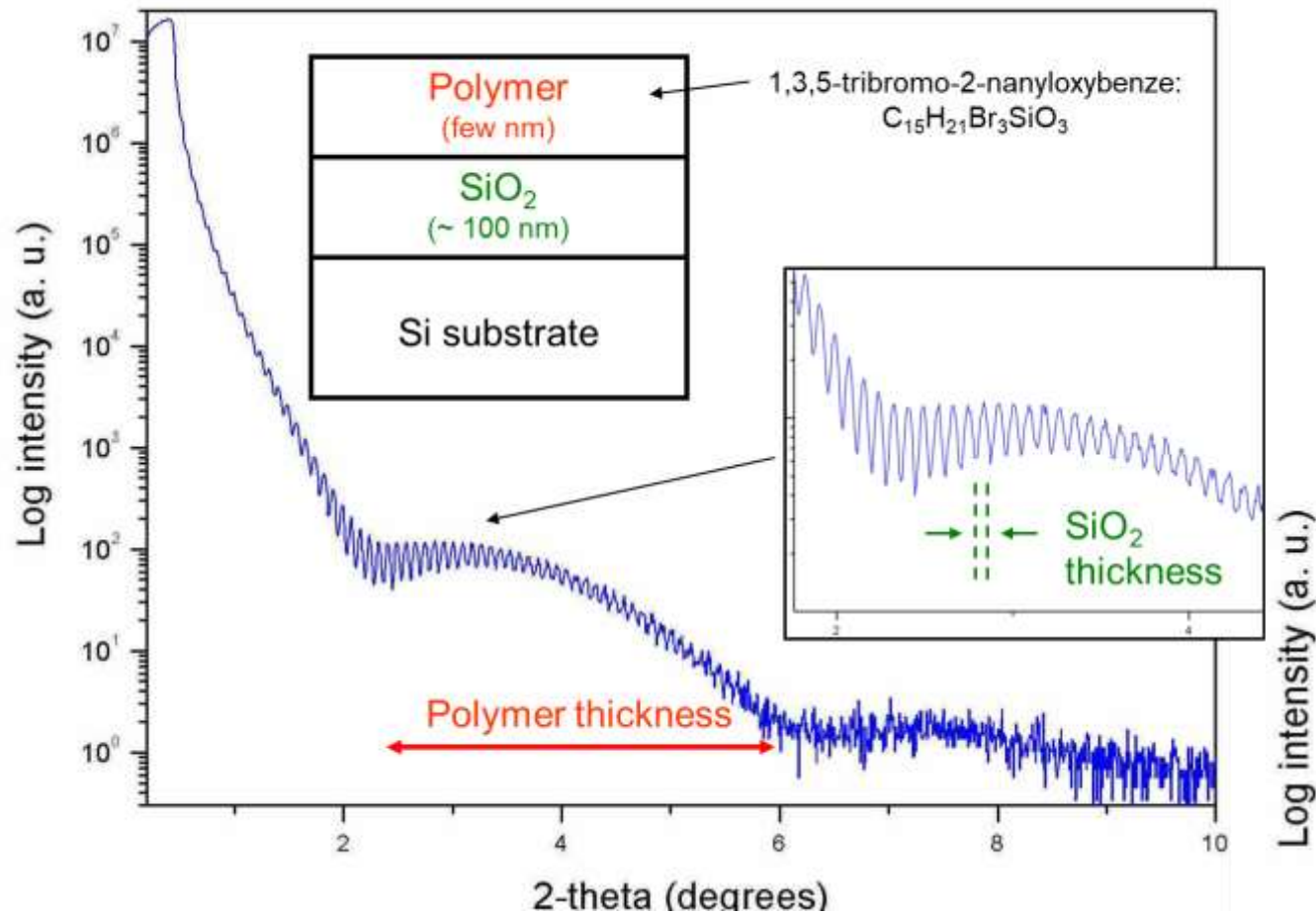


XRR measures *changes in electron density* near surface and over a depth up to $\sim 100-200$ nm: density, porosity, density profile, surface and interface roughness, layer thickness.
Amorphous, crystalline, layered, solids, liquids.

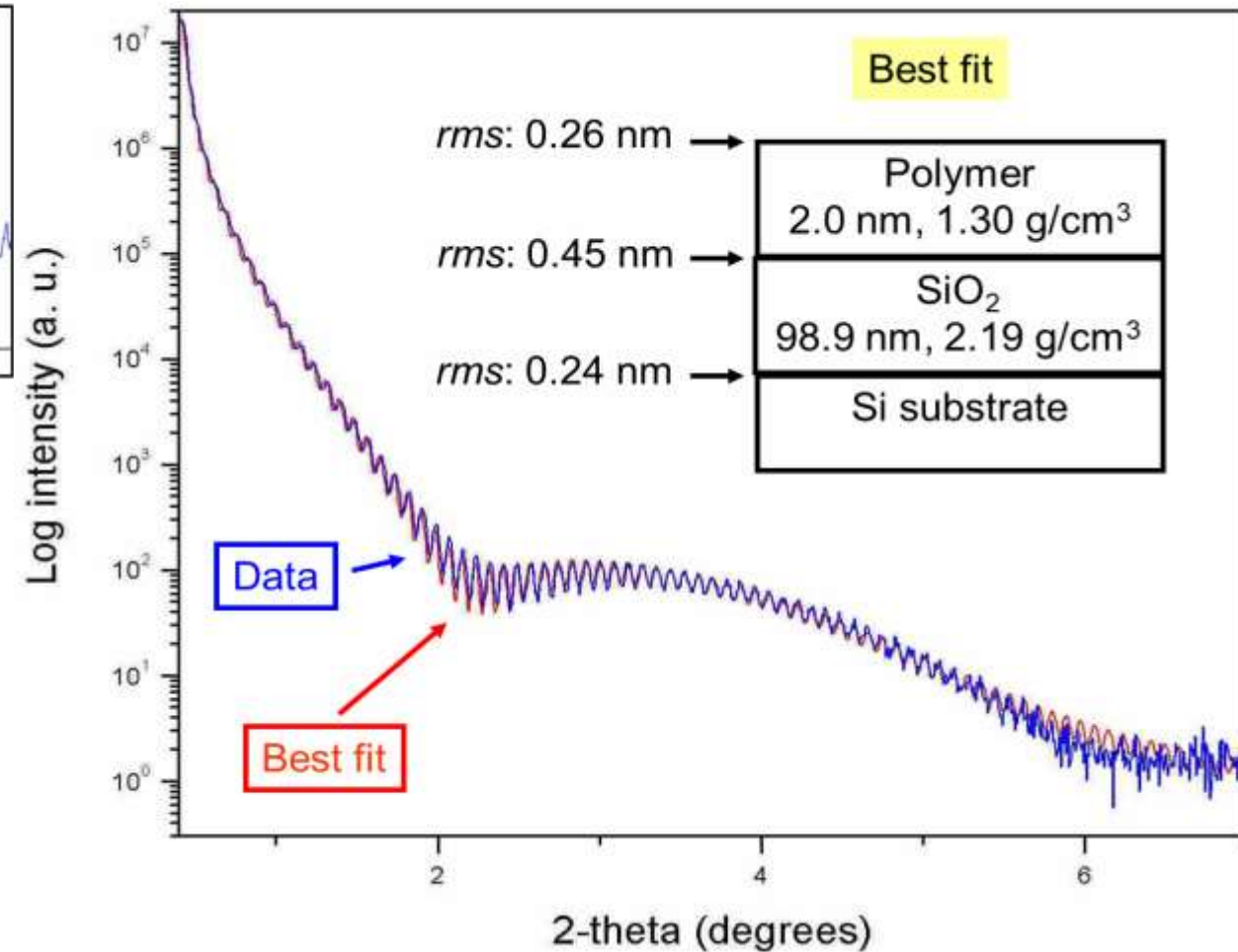


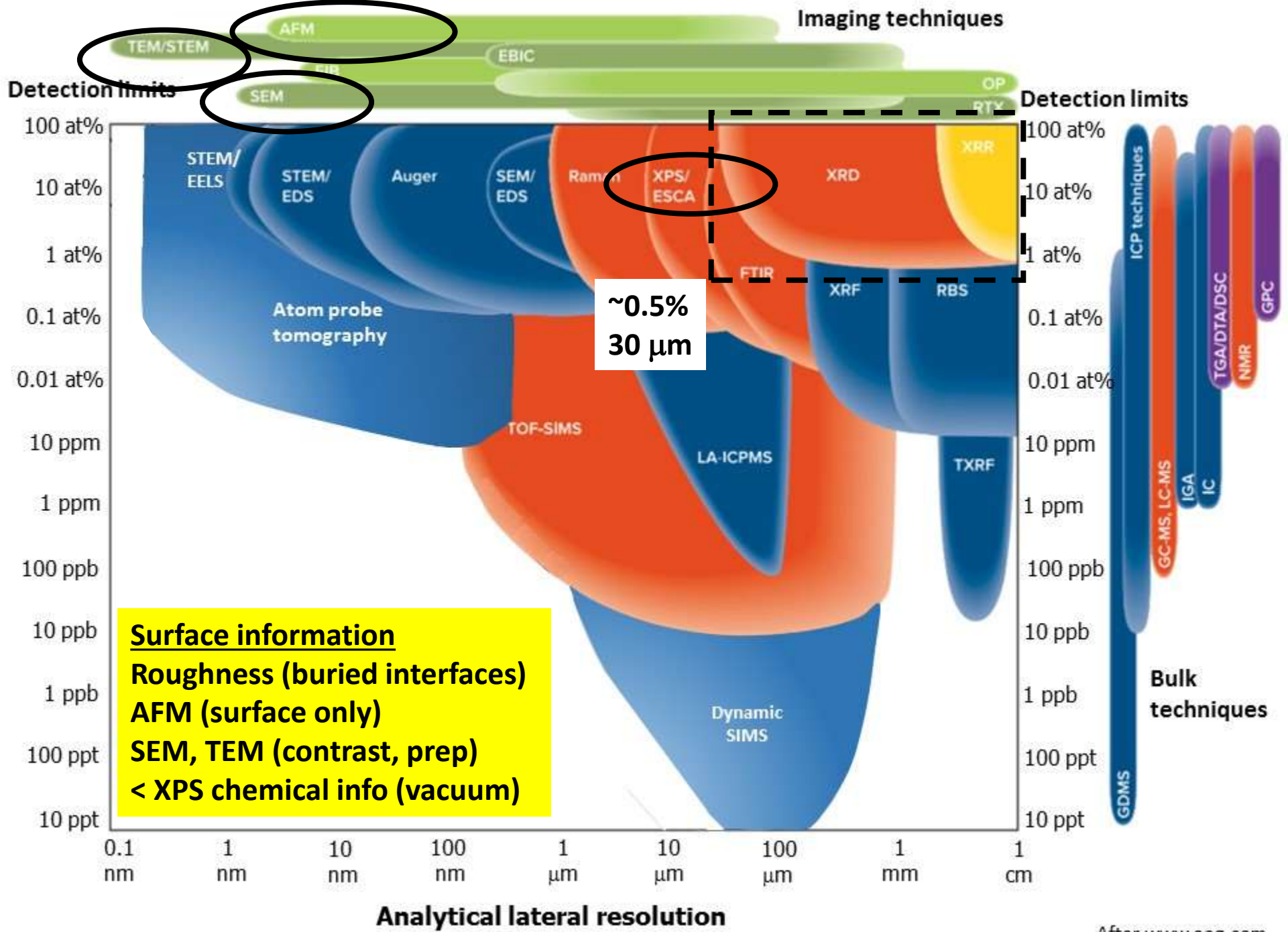
\sim sharp surface and interfaces required for layer thickness determination

X-ray reflectivity of ultra-thin films

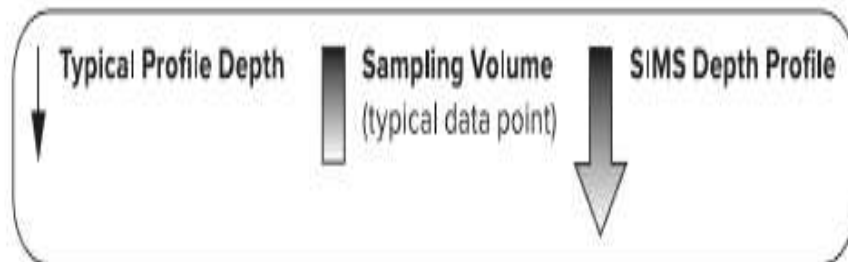
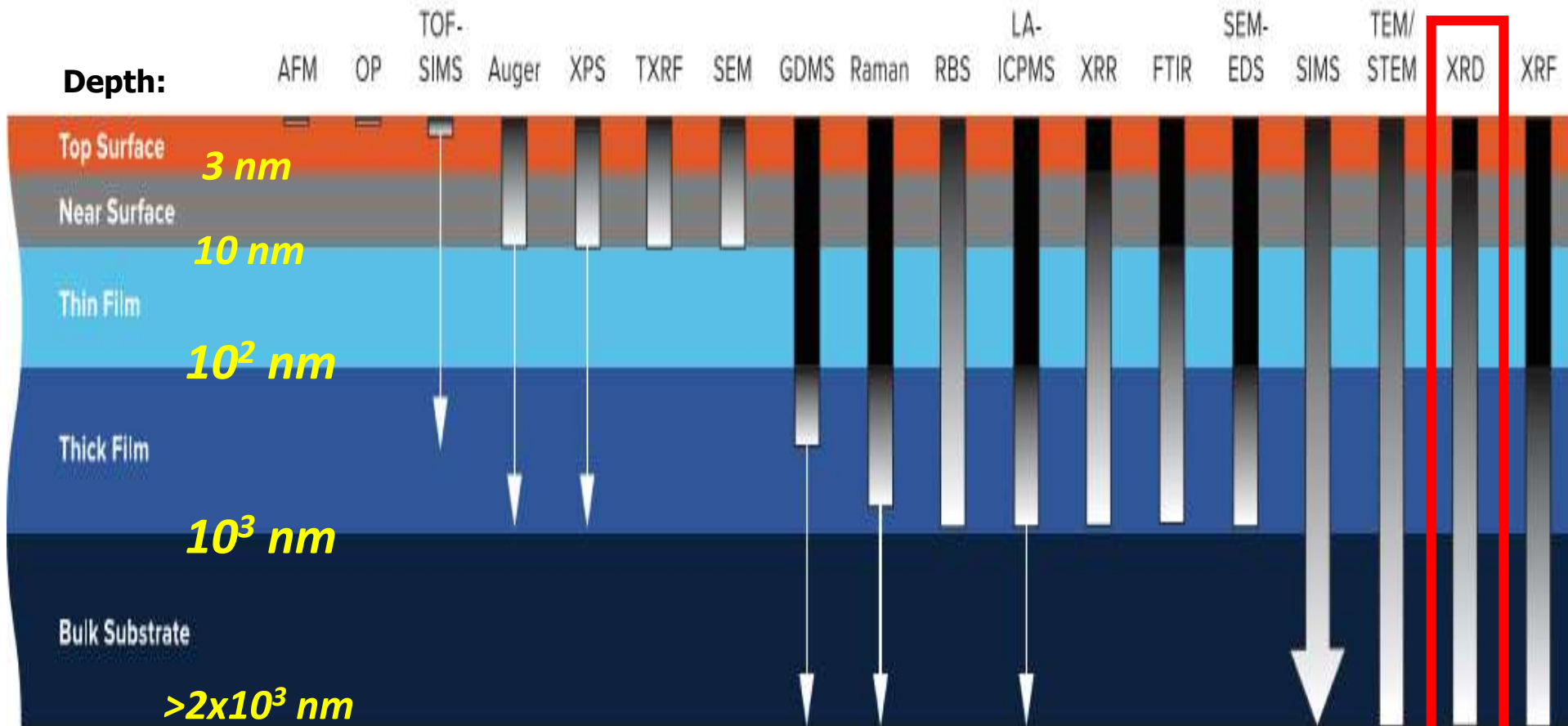


Simulation using Parrat's formalism
and generic algorithm fitting





Typical analysis depth for common analytical techniques



GI-XRD can reduce depth

(+)

Non destructive

No vacuum requirement

Optional sample prep

Crystalline phases identification and quantification

Element, molecules, polymorphs (structural fingerprinting)

Crystallite / grain size: easy to measure (be careful)

Averages over large volume (~ 30 μm x 0.5-2 cm's)

Multiple levels of complexity: simple to complex

Easy integration to in situ HT, LT, pressure, humidity controls

Microdiffraction, pair distribution function, microfocus sources, fast areal detectors



(-)

No localized information:

Areal spatial resolution not better than 100 μm

Depth resolution down to tens of nm only with special techniques

Defects identification and quantification requires simulation and data fitting

No direct info or image of microstructure



X- ray analysis methods

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Based on the book...

“PRACTICAL MATERIALS CHARACTERIZATION”

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